

D. Thin Film Process Technology 분과

O01\_[WA1-D] High-k/Metal Gate

좌장: 이홍섭 교수(경희대학교), 백인환 교수(인하대학교)

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| 초청발표<br>WA1-D-1<br>09:00-09:30 | <p>How to Modulate Threshold Voltage (<math>V_{th}</math>) Using ALD HKMG Gate Stack for Advanced Logic Transistor and DRAM Peripheral Transistor</p> <p>Changhwan Choi<sup>1,2</sup></p> <p><sup>1</sup>Division of Materials Science and Engineering, Hanyang University, <sup>2</sup>Department of Semiconductor Engineering, Hanyang University</p>                                                                                                                                                                                                                                                                                      |
| WA1-D-2<br>09:30-09:45         | <p>A Study on a PECVD-Deposited SiCN Capping Layer in High-k/Metal-Gate</p> <p>Hye-Ri Hong<sup>1</sup>, Woon-San Ko<sup>1</sup>, So-Yeong Park<sup>1</sup>, Seong-Jo Jo<sup>1</sup>, Myeong-Ho Song<sup>2</sup>, and Ga-Won Lee<sup>1</sup></p> <p><sup>1</sup>Chungnam National University, <sup>2</sup>NNFC</p>                                                                                                                                                                                                                                                                                                                            |
| WA1-D-3<br>09:45-10:00         | <p>Leakage Current Reduction in HKMG Stacks through Nitridation Engineering</p> <p>Chinsung Park, Hyungchul Kim, Seungwook Kim, Seungmi Lee, Yeongseok Jeong, Yunhyuck Ji, and Seungwoo Jin</p> <p>R&amp;D Process, R&amp;D Division, SK hynix Inc.</p>                                                                                                                                                                                                                                                                                                                                                                                      |
| WA1-D-4<br>10:00-10:15         | <p>Experimental Investigation of Al-Based Doping for Threshold Voltage Control of GAA pMOS Device</p> <p>Wonjae Choi<sup>1</sup>, Sangkuk Han<sup>2</sup>, Haesoo Jang<sup>1</sup>, Jaewon Chung<sup>1</sup>, Sangmyun Lim<sup>1</sup>, Kyungwook Park<sup>2,3</sup>, Sangwoo Jeong<sup>2</sup>, Soyoung Park<sup>1</sup>, and Changhwan Choi<sup>1,2</sup></p> <p><sup>1</sup>Department of Semiconductor Engineering, Hanyang University, <sup>2</sup>Division of Materials Science and Engineering, Hanyang University, <sup>3</sup>DRAM Process Development Team, Samsung Electronics Co., Ltd.</p>                                      |
| WA1-D-5<br>10:15-10:30         | <p>Tuning the Effective Work Function of TiAlN Gate Electrodes through ALD Aluminum Incorporation</p> <p>Hae-Dam Kim, Gyeong-Min Jeong, and Jin-Seong Park</p> <p>Division of Materials Science and Engineering, Hanyang University</p>                                                                                                                                                                                                                                                                                                                                                                                                      |
| WA1-D-6<br>10:30-10:45         | <p>HfO<sub>2</sub>, ZrO<sub>2</sub>, and La<sub>2</sub>O<sub>3</sub> Films Deposited by Liquid-Injection ALD for High-K Gate Dielectric Applications</p> <p>Ji-Won Jang<sup>1</sup>, Soon-Kyeong Park<sup>1</sup>, Ye-Won Han<sup>3</sup>, Hee-Sung Kang<sup>4</sup>, and Il-Kwon Oh<sup>1,2</sup></p> <p><sup>1</sup>Department of Intelligence Semiconductor Engineering, Ajou University, <sup>2</sup>Department of Electrical and Computer Engineering, Ajou University, <sup>3</sup>Department of Materials Science &amp; Chemical Engineering, Hanyang University ERICA, <sup>4</sup>RPM Team, R&amp;D Innovation Center, MKP Inc.</p> |

K. Memory (Design & Process Technology) 분과

O02\_[WB1-K] NAND Flash

좌장: 심원보 교수(서울과학기술대학교), 김윤 교수(서울시립대학교)

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| 초청발표<br>WB1-K-1<br>09:00-09:30 | Reliability Issues and Modeling of 3D NAND Flash Memory<br>Sangmoo Choi, Kyoungjin Park, Kyoungcheol Kwon, Hyun Heo, Juyeab Lee, and Jumsu Kim<br>SK hynix Inc.                                                                                                                                                                                                                                                                                                                                                                                                                |
| WB1-K-2<br>09:30-09:45         | 밴드갭 엔지니어링 산질화 붕소(Boron Oxynitride, BON) 터널링 층을 이용한 고성능 및 고신뢰성 3D NAND Flash Memory<br>강대현 <sup>1</sup> , 정재중 <sup>1</sup> , 박영근 <sup>1</sup> , 김영준 <sup>2</sup> , 조병진 <sup>1,2</sup><br><sup>1</sup> 한국과학기술원 전기 및 전자공학부, <sup>2</sup> 한국과학기술원 반도체공학대학원                                                                                                                                                                                                                                                                                                                         |
| WB1-K-3<br>09:45-10:00         | A Novel Approach to Enhancing Cell Current in 3D NAND Using Backside Channel Engineering<br>Yeeun Kim <sup>1</sup> , Jaejoong Jeong <sup>2</sup> , Byung Jin Cho <sup>2</sup> , and Jong Kyung Park <sup>1</sup><br><sup>1</sup> Department of Semiconductor Engineering, Seoul National University of Science & Technology, <sup>2</sup> School of Electrical Engineering, KAIST                                                                                                                                                                                              |
| WB1-K-4<br>10:00-10:15         | 저유전율 마카로니 필러 적용을 통한 3D NAND Flash Memory 의 GIDL Erase 특성 향상<br>김민승 <sup>1</sup> , 정재중 <sup>1</sup> , 김승훈 <sup>1</sup> , 강대현 <sup>1</sup> , 유찬미 <sup>2</sup> , 조병진 <sup>1,2</sup><br><sup>1</sup> 한국과학기술원 전기 및 전자공학부, <sup>2</sup> 한국과학기술원 반도체공학대학원                                                                                                                                                                                                                                                                                                                             |
| WB1-K-5<br>10:15-10:30         | Impact of Crystallization on Trap Levels and Charge Storage Characteristics of High-k HfO <sub>2</sub> Charge Trap Layers for 3D NAND Flash Memory Device<br>Dohyun Lee <sup>1</sup> , Yunseo Lim <sup>2</sup> , Jisu Park <sup>1</sup> , Gyumin Hwang <sup>1</sup> , Sangmyun Lim <sup>1</sup> , Seongho Lee <sup>2</sup> , JinYeong Lee <sup>1</sup> , Hoon Pyo <sup>1</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University |
| WB1-K-6<br>10:30-10:45         | 실리콘 질화물 내 저마늄 도입을 통한 CTF 소자의 메모리 특성 개선<br>신건희 <sup>1</sup> , 박영근 <sup>2</sup> , 정재중 <sup>2</sup> , 김희태 <sup>2</sup> , 김승훈 <sup>2</sup> , 강대현 <sup>2</sup> , 박동욱 <sup>2</sup> , 정원묵 <sup>2</sup> , 김민승 <sup>2</sup> , 유찬미 <sup>1</sup> , 이동규 <sup>1</sup> , 조병진 <sup>1,2</sup><br><sup>1</sup> 한국과학기술원 반도체공학대학원, <sup>2</sup> 한국과학기술원 전기 및 전자공학부                                                                                                                                                                                                                                |

D. Thin Film Process Technology 분과

O03\_[WC1-D] Memory Capacitors I

좌장: 이웅규 교수(송실대학교), 문태환 교수(아주대학교)

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| 초청발표<br>WC1-D-1<br>09:00-09:30 | <b>How Can We Stabilize Metastable Rutile TiO<sub>2</sub> Films on Any Substrate?</b><br>Seong Keun Kim <sup>1,2</sup><br><sup>1</sup> Electronic and Hybrid Materials Research Center, KIST, <sup>2</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University                                                                                                                                                                                              |
| WC1-D-2<br>09:30-09:45         | <b>Suppression of Low-k Interfacial Layer in ZrO<sub>2</sub>/TiN Capacitors by Atomic Layer Deposition Using Ligand-Modified Zr Precursor</b><br>Hyeongjun Kim, Seungmin Jo, and Woongkyu Lee<br>Department of Materials Science and Engineering, Soongsil University                                                                                                                                                                                                                  |
| WC1-D-3<br>09:45-10:00         | <b>Sc Doping to Improve the Electrical Properties of TiO<sub>2</sub> Dielectric Thin Films</b><br>Seungwoo Lee <sup>1</sup> , Soomin Yoo <sup>1</sup> , Gaeul Kim <sup>1</sup> , Hansol Oh <sup>2</sup> , Hanbyul Kim <sup>2</sup> , Donghun Shin <sup>2</sup> , Yongjoo Park <sup>2</sup> , and Woojin Jeon <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Kyung Hee University, <sup>2</sup> Advanced Research Development Team, SK Trichem Co., Ltd. |
| WC1-D-4<br>10:00-10:15         | <b>Plasma-Enhanced Atomic Layer Deposition of Stable MoO<sub>2</sub> Thin Films for High-Performance TiO<sub>2</sub>-Based DRAM Capacitors</b><br>Jae Hyeon Lee, Seon Gu Choi, Jeong Min Han, and Jeong Hwan Han<br>Department of Materials Science and Engineering, Seoul National University of Science & Technology                                                                                                                                                                 |
| WC1-D-5<br>10:15-10:30         | <b>Upper-Layer-Induced Crystallization of Metastable Rutile TiO<sub>2</sub></b><br>Jihoon Jeon <sup>1,2</sup> , Jongseo Kim <sup>1,2</sup> , Seungwan Ye <sup>1,2</sup> , and Seong Keun Kim <sup>1,2</sup><br><sup>1</sup> Electronic and Hybrid Materials Research Center, KIST, <sup>2</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University                                                                                                         |
| WC1-D-6<br>10:30-10:45         | <b>Strategy for Bottom-Electrode-Independent Stabilization of Rutile TiO<sub>2</sub> via ALD</b><br>Seungwan Ye <sup>1,2</sup> , Jihoon Jeon <sup>1,2</sup> , Jongseo Kim <sup>1,2</sup> , Minseok Kim <sup>1,2</sup> , and Seong Keun Kim <sup>1,2</sup><br><sup>1</sup> Electronic and Hybrid Materials Research Center, KIST, <sup>2</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University                                                           |

J. Nano-Science & Technology 분과

O04\_[WD1-J] 2차원 나노소재의 성장 및 물성 제어

좌장: 왕건욱 교수(고려대학교), 김준석 교수(홍익대학교)

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| 초청발표<br>WD1-J-1<br>09:00-09:30 | <b>Solution-Processed 2D Materials for Next-Generation Electronics</b><br>Joohoon Kang<br>Department of Chemical and Biomolecular Engineering, Yonsei University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                      |
| WD1-J-2<br>09:30-09:45         | <b>Wafer-Scale Single-Crystal Growth of Bernal-Stacked Boron Nitride</b><br>Jaewon Wang <sup>1</sup> , Hyeonwoo Lee <sup>1</sup> , Jaemin Kim <sup>2</sup> , Haeng Un Yeo <sup>1</sup> , Cheol Hwan Yoon <sup>1</sup> , Min Seok Yoo <sup>3</sup> , Junseop Noh <sup>1</sup> , Sora Jang <sup>1</sup> , Ju-Hyoung Han <sup>1</sup> , Juwon Han <sup>1</sup> , Jaeeun Park <sup>1</sup> , Young Ho Jin <sup>1</sup> , Huijun Han <sup>1</sup> , Kitae Park <sup>1</sup> , Joonki Suh <sup>4</sup> , Tae-Sik Yoon <sup>1</sup> , Seunguk Song <sup>5</sup> , Minsu Seol <sup>3</sup> , Chanyong Hwang <sup>6</sup> , Hyung-Joon Shin <sup>1</sup> , Zonghoon Lee <sup>1</sup> , Changwook Jeong <sup>1</sup> , and Soon-Yong Kwon <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering and Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Center for Multidimensional Carbon Materials, IBS, <sup>3</sup> 2D Device Laboratory, Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd., <sup>4</sup> Department of Chemical and Biomolecular Engineering, KAIST, <sup>5</sup> Department of Energy Science, Sungkyunkwan University, <sup>6</sup> Quantum Technology Institute, KRISS |
| WD1-J-3<br>09:45-10:00         | <b>Probing Nanoscale Structural Perturbation in WS<sub>2</sub> Monolayer via Explainable Artificial Intelligence</b><br>Hyeong Chan Suh <sup>1</sup> , Jaekak Yoo <sup>1</sup> , Kangmo Yeo <sup>2</sup> , Dong Hyeon Kim <sup>1</sup> , Yo Seob Won <sup>3</sup> , Taehoon Kim <sup>1</sup> , Youngwoo Cho <sup>4</sup> , Ki Kang Kim <sup>3</sup> , Seung Mi Lee <sup>5</sup> , Heejun Yang <sup>6</sup> , Dong-Wook Kim <sup>7</sup> , and Mun Seok Jeong <sup>1</sup><br><sup>1</sup> Department of Physics, Hanyang University, <sup>2</sup> Samsung SDI, <sup>3</sup> Department of Energy Science, Sungkyunkwan University, <sup>4</sup> Kim Jaechul Graduate School of Artificial Intelligence, KAIST, <sup>5</sup> KRISS, <sup>6</sup> Department of Physics, KAIST, <sup>7</sup> Department of Physics, Ewha Womans University                                                                                                                                                                                                                                                                                                                                                                                                                              |
| WD1-J-4<br>10:00-10:15         | <b>High-Pressure CVD Growth of 2D Semiconductor with Minimized Defect Density</b><br>Takmo Jeong and Seok Joon Yun<br>Department of Semiconductor Physics and Engineering, University of Ulsan                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                        |
| WD1-J-5<br>10:15-10:30         | <b>Effect of Seed-Layer Morphology on Dielectric Interface and Device Performance in MoS<sub>2</sub> Field-Effect Transistors</b><br>Sumin Hong <sup>1</sup> , Haksoon Jung <sup>2</sup> , Sanghyun Lee <sup>2</sup> , Minho Park <sup>2</sup> , and Jimin Kwon <sup>1,2</sup><br><sup>1</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Department of Electrical Engineering, UNIST                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| WD1-J-6<br>10:30-10:45         | <b>Energy Harvesting Performance Enhancement via Hierarchical MoS<sub>2</sub> Nanostructures in Triboelectric Nanogenerators</b><br>Euna Jung <sup>1,2</sup> , Jeongin Song <sup>1,2</sup> , Taesung Kim <sup>2</sup> , Jae-Hyun Lee <sup>2</sup> , and Jihun Mun <sup>1</sup><br><sup>1</sup> KRISS, <sup>2</sup> Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                            |

E. Compound Semiconductors 분과

O05\_[WE1-E] Ultra Wide Bandgap Power Devices

좌장: 최철종 교수(전북대학교), 문재경 박사(한국전자통신연구원)

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| 초청발표<br>WE1-E-1<br>09:00-09:30 | <b>Diamond Semiconductor: From Single Crystal Wafers to Power Devices</b><br>Taemyung Kwak <sup>1</sup> , Geunho Yoo <sup>1</sup> , Seong-Woo Kim <sup>2</sup> , and Okhyun Nam <sup>1</sup><br><sup>1</sup> Department of Semiconductor Engineering, Tech University of Korea, <sup>2</sup> Orbray Co., Ltd.                                                                                                                                                                                                                                 |
| WE1-E-2<br>09:30-09:45         | <b>Effect of Substrate Off-Angle on the Heteroepitaxial Growth of Twin-Free (111) Diamond on Ir/r-Plane Sapphire</b><br>Seolyoung Oh, Taemyung Kwak, Yoonseok Nam, Hyunsu Ma, Geunho Yoo, and Okhyun Nam<br>Convergence Center for Advanced Nano Semiconductor, Department of Nano-Semiconductor Engineering, Tech University of Korea                                                                                                                                                                                                        |
| WE1-E-3<br>09:45-10:00         | <b>Thermally Stable Al-rich AlGa<sub>N</sub> HEMTs for Extreme Temperature Applications</b><br>Do-Hyeong Yeo <sup>1</sup> , Hyun-Seop Kim <sup>2</sup> , and Ho-Young Cha <sup>1</sup><br><sup>1</sup> School of Electronic and Electrical Engineering, Hongik University, <sup>2</sup> Department of Electrical Engineering, Kunsan National University                                                                                                                                                                                      |
| WE1-E-4<br>10:00-10:15         | <b>Multi-Kilovolt Vertical NiO/Ga<sub>2</sub>O<sub>3</sub> p-n Heterojunction Diodes with Ring-Assisted Junction Termination Extension</b><br>Kanghee Shin <sup>1,2,3</sup> , Ho Jung Jeon <sup>1,2,3</sup> , Jang Hyeok Park <sup>1,2,3</sup> , and You Seung Rim <sup>1,2,3</sup><br><sup>1</sup> Department of Semiconductor Systems Engineering, Sejong University, <sup>2</sup> Department of Convergence Engineering for Intelligent Drone, Sejong University, <sup>3</sup> Institute of Semiconductor and System IC, Sejong University |
| WE1-E-5<br>10:15-10:30         | <b>NPN Gate 구조를 이용한 NiO/<math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Heterojunction Field-Effect Transistor의 게이트 안정성 및 고온 신뢰성 향상 연구</b><br>이태은 <sup>1</sup> , 경신수 <sup>2</sup> , 우솔아 <sup>1,3</sup><br><sup>1</sup> 국립부경대학교 지능로봇학과, <sup>2</sup> PowerCubeSemi, Inc., <sup>3</sup> 국립부경대학교 전자공학과                                                                                                                                                                                                                                            |
| WE1-E-6<br>10:30-10:45         | <b>Characterization of Thermal Transport Properties in NiO/Ga<sub>2</sub>O<sub>3</sub> p-n Junction Diode</b><br>Taeyeon Kim <sup>1</sup> , Ho Jung Jeon <sup>2,3</sup> , Jihyun Kim <sup>1</sup> , You Seung Rim <sup>2,3</sup> , and Jungwan Cho <sup>1</sup><br><sup>1</sup> School of Mechanical Engineering, Sungkyunkwan University, <sup>2</sup> Department of Semiconductor Systems Engineering, Sejong University, <sup>3</sup> Department of Convergence Engineering for Intelligent Drone, Sejong University                       |

K. Memory (Design & Process Technology) 분과

O06\_[WF1-K] IGZO

좌장: 홍윤기 교수(부산대학교), 객준영 교수(이화여자대학교)

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| WF1-K-1<br>09:00-09:15 | <p><b>On-Chip Trainable IGZO Analog CAM for VQ-VAE Acceleration</b></p> <p>Hyeong Jun Seo<sup>1,2,3</sup>, Mingi Kim<sup>1,2,3</sup>, Youngchae Roh<sup>1,2,3</sup>, Kanghyeon Byun<sup>1,2,3</sup>, Changhoon Joe<sup>1,2,3</sup>, Narae Han<sup>1,4</sup>, Sangwook Kim<sup>4</sup>, Sangjun Hong<sup>5</sup>, and Sangbum Kim<sup>1,2,3</sup></p> <p><sup>1</sup>Department of Materials Science and Engineering, Seoul National University, <sup>2</sup>Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup>Research Institute of Advanced Materials, Seoul National University, <sup>4</sup>Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd., <sup>5</sup>Device Solutions, Samsung Electronics Co., Ltd.</p> |
| WF1-K-2<br>09:15-09:30 | <p><b>Turning the Hump into Logic: Ternary MVL via a-IGZO TFTs</b></p> <p>Jeong Yeon Im, So-Jeong Park, Hanbin Lee, Ji Won Park, Seonghyeon Jeong, Youngmin Kim, Dae Hwan Kim, Yoon Jung Lee, and Sung-Jin Choi</p> <p>School of Electronics and Electrical Engineering, Kookmin University</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |
| WF1-K-3<br>09:30-09:45 | <p><b>Back-Gate Biasing Scheme for Robust Random Access in Amorphous InGaZnO 2T0C DRAM Array with Double-Gate Structure</b></p> <p>Seunghun Ji<sup>1</sup>, Junsung Park<sup>2</sup>, Hyunwook Jeong<sup>2</sup>, Eunchong Kim<sup>1</sup>, and Jong-Ho Bae<sup>1</sup></p> <p><sup>1</sup>Department of System Semiconductor Engineering, Yonsei University, <sup>2</sup>School of Electrical Engineering, Kookmin University</p>                                                                                                                                                                                                                                                                                                                                           |
| WF1-K-4<br>09:45-10:00 | <p><b>Correlation between Temperature-Dependent ID-VDS Hysteresis, Schottky Barrier Non-Quasi Static Characteristics, and Trap Distribution in IGZO Vertical Channel Transistors</b></p> <p>Jae Woo Lee<sup>1</sup>, Wonjung Kim<sup>1</sup>, Seong Hoon Jeon<sup>1</sup>, Su Han Noh<sup>1</sup>, Junseok Lee<sup>1</sup>, Changwook Kim<sup>1</sup>, Yoon Jung Lee<sup>1</sup>, Sung-Jin Choi<sup>1</sup>, Yubeen Lim<sup>2</sup>, Min Hee Cho<sup>2</sup>, Pilsang Yun<sup>2</sup>, Daewon Ha<sup>2</sup>, and Dae Hwan Kim<sup>1</sup></p> <p><sup>1</sup>School of Electrical Engineering, Kookmin University, <sup>2</sup>Semiconductor R&amp;D Center, Samsung Electronics Co., Ltd.</p>                                                                              |
| WF1-K-5<br>10:00-10:15 | <p><b>Analog Compute-in-Memory Transformer Using InGaZnO Charge-Trap Flash Memory</b></p> <p>이원주<sup>1</sup>, 이정환<sup>1</sup>, 구민석<sup>2,3</sup>, 김윤<sup>1,3</sup></p> <p><sup>1</sup>서울시립대학교 전자전기컴퓨터공학과, <sup>2</sup>서울시립대학교 첨단융합학부, <sup>3</sup>(주) 아이엠전자</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |
| WF1-K-6<br>10:15-10:30 | <p><b>Enabling Selective and Tunable Weight Updates in All-InGaZnO 3-Transistor 1-Capacitor Synaptic Circuits for On-Chip Training</b></p> <p>Minseung Kang<sup>1,3,4</sup>, Mingi Kim<sup>1,3,4</sup>, Jaehyeon Kang<sup>1,2,3,4</sup>, Jongun Won<sup>1,3,4</sup>, Hyeong Jun Seo<sup>1,3,4</sup>, Changhoon Joe<sup>1,3,4</sup>, Youngchae Roh<sup>1,3,4</sup>, Yeaji Park<sup>1,3,4</sup>, and Sangbum Kim<sup>1,3,4</sup></p> <p><sup>1</sup>Department of Materials Science and Engineering, Seoul National University, <sup>2</sup>Samsung Electronics Co., Ltd., <sup>3</sup>Inter-university Semiconductor Research Center, Seoul National University, <sup>4</sup>Research Institute of Advanced Materials, Seoul National University</p>                          |
| WF1-K-7<br>10:30-10:45 | <p><b>A Study of an OS-Based 2T0C DRAM Architecture for Buffer Using Monolithic 3D Technology</b></p> <p>Jungho Lee and Jae Kyeong Jeong</p> <p>Department of Electronic Engineering, Hanyang University</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |

A. Interconnect & Package 분과

O07\_[WG1-A] Advanced Package I

좌장: 이태익 수석연구원(한국생산기술연구원), 이소연 교수(인하대학교)

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| 초청발표<br>WG1-A-1<br>09:00-09:30 | Single-Suppressor Cu Electrodeposition for Defect-Free TSV Filling<br>Myung Jun Kim<br>School of Chemical Engineering, Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                |
| 초청발표<br>WG1-A-2<br>09:30-10:00 | 3차원 반도체 패키지 접합용 저온 접합 소재 개발 및 신뢰성 연구<br>김병준<br>한국공학대학교 신소재공학과                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| WG1-A-3<br>10:00-10:15         | Accurate Extraction of Ultra-Low Contact Resistivity ( $10^{-12} \Omega \cdot \text{cm}^2$ ) via TSV-Optimized Cu-Cu Hybrid Bonding<br>Kyung Min Shin and Jong Kyung Park<br>Department of Semiconductor Engineering, Seoul National University of Science & Technology                                                                                                                                                                                                                                       |
| WG1-A-4<br>10:15-10:30         | Comparison of Signal Integrity (SI) Characteristics and Implementation of Glass and Silicon Bridge for High-Speed Interfaces<br>Suin Chae <sup>1,2</sup> , Seonwoo Kim <sup>1,3</sup> , Soobin Park <sup>1</sup> , Se-hoon Park <sup>1</sup> , Jaemyung Lim <sup>2</sup> , and Jein Yu <sup>1</sup><br><sup>1</sup> ICT Device Packaging Researcher Center, KETI, <sup>2</sup> Department of Electronic Engineering, Hanyang University, <sup>3</sup> School of Chemical Engineering, Sungkyunkwan University |
| WG1-A-5<br>10:30-10:45         | Novel Rinse for Fabrication of Fan-Out RDL Interposer with Embedded Bridge<br>Seonwoo Kim <sup>1,2</sup> , Suin Chae <sup>1,3</sup> , Soobin Park <sup>1</sup> , Jein Yu <sup>1</sup> , Sungjune Park <sup>2</sup> , and Se-hoon Park <sup>1</sup><br><sup>1</sup> ICT Device Packaging Research Center, KETI, <sup>2</sup> School of Chemical Engineering, Sungkyunkwan University, <sup>3</sup> Department of Electronic Engineering, Hanyang University                                                    |

G. Device & Process Modeling, Simulation and Reliability 분과

O08\_[WH1-G] Device & Process Modeling, Simulation and Reliability I

좌장: 정창욱 교수(UNIST), 김현우 교수(건국대학교)

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| WH1-G-1<br>09:00-09:15 | <b>Investigation of Bias-Dependent Off-State Leakage Current in Split-Gate VDMOS</b><br>Sung-Su Yoon, Jieun Lee, Jong Min Kim, Young Chul Kim, and Hyun Chul Nah<br>Technology Enabling Center, DB HiTek                                                                                                                                                                   |
| WH1-G-2<br>09:15-09:30 | <b>Beyond the Perfect-Metal Assumption: A 3D Phase Field Simulation Framework with Thomas-Fermi Electrode Screening for FTJs</b><br>Seokwon Lee and Mincheol Shin<br>School of Electrical Engineering, KAIST                                                                                                                                                               |
| WH1-G-3<br>09:30-09:45 | <b>Accelerating Simulation of General Gate-All-Around Transistors via a Quasi-1D Model</b><br>Gyubeen Kim <sup>1</sup> , Kwang-Woon Lee <sup>2</sup> , and Sung-Min Hong <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, GIST, <sup>2</sup> Department of Electrical Engineering and Computer Science, GIST                                        |
| WH1-G-4<br>09:45-10:00 | <b>High Performance Bi-Directional SCR with PWELL Cut-out Structure</b><br>Youngsang Son, Jongmin Kim, Youngchul Kim, and Hyunchul Nah<br>DB HiTek                                                                                                                                                                                                                         |
| WH1-G-5<br>10:00-10:15 | <b>Semi-Classical Monte-Carlo Simulation of Quantum Confinement Effects in Si Fin and Nanosheet with Different Surface Orientations</b><br>Uiho Lee, Jae Yeon Kim, and Jiwon Chang<br>Department of System Semiconductor Engineering, Yonsei University                                                                                                                    |
| WH1-G-6<br>10:15-10:30 | <b>A Voxel-Based Semiconductor Process Emulator, AngstromCraft</b><br>Sung-Min Hong<br>Department of Electrical Engineering and Computer Science, GIST                                                                                                                                                                                                                     |
| WH1-G-7<br>10:30-10:45 | <b>Invertible Encryption-Decryption Framework Using Threshold Switching-Based Probabilistic Bits</b><br>Jihyun Kim <sup>1</sup> , Hyeonsik Choi <sup>1</sup> , and Jiyong Woo <sup>1,2</sup><br><sup>1</sup> School of Electronic and Electrical Engineering, Kyungpook National University, <sup>2</sup> School of Electronics Engineering, Kyungpook National University |

F. Silicon and Group-IV Devices and Integration Technology 분과

O09\_[W11-F] Advanced CMOS Applications

좌장: 김경록 교수(UNIST), 조성재 교수(이화여자대학교)

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| W11-F-1<br>09:00-09:15 | <b>Metal-Gate-Induced Stress Effects in GAAFET-Based CMOS Inverters</b><br>Subin Lim <sup>1</sup> , Jaehyuk Lim <sup>2</sup> , and Changhwan Shin <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, College of Engineering, Korea University, <sup>2</sup> Research Institute of Semiconductor Technology, Korea University                                                                                                                                                                                                   |
| W11-F-2<br>09:15-09:30 | <b>Si CMOS-Compatible Ternary CMOS Technology Utilizing Intrinsic Drain-Side Resistance for Low-Power Multi-Value Logic Applications</b><br>Minsu Lim <sup>1</sup> and Jiwon Chang <sup>2</sup><br><sup>1</sup> School of Materials Science and Engineering, Yonsei University, <sup>2</sup> School of System Semiconductor Engineering, Yonsei University                                                                                                                                                                                 |
| W11-F-3<br>09:30-09:45 | <b>Multi-Level Cell Physically Unclonable Function (PUF) based on Dual Physical Parameters in Silicon MOSFETs</b><br>Sang-Min Kang <sup>1</sup> , Da-Eun Bang <sup>1</sup> , Dol Sohn <sup>1</sup> , Hyo-Jun Park <sup>1</sup> , Eui-Cheol Yun <sup>1</sup> , Min-Woo Kim <sup>1</sup> , Moon-Seok Kim <sup>2</sup> , and Jun-Young Park <sup>1</sup><br><sup>1</sup> School of Semiconductor Engineering, Chungbuk National University, <sup>2</sup> Department of Semiconductor System Engineering, Chungnam National University         |
| W11-F-4<br>09:45-10:00 | <b>Multi-State Probabilistic Computing Using Floating-Body MOSFETs based on the Potts Model for Solving Complex Combinatorial Optimization Problems</b><br>Sunwoo Cheong <sup>1,2</sup> , Soo Hyung Lee <sup>1,2</sup> , Janguk Han <sup>1,2</sup> , and Cheol Seong Hwang <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University                                                               |
| W11-F-5<br>10:00-10:15 | <b>A Study on Temporal Noise Reduction in 200Mp Pixel CMOS Image Sensors</b><br>Daehyung Lee, Hyunki Ko, Nakyung Lee, Seungjoon Lee, Kyoungun Chang, Minkyung Kim, Kisang Yoon, Seungyeon Lee, Seunghwan Lee, Hyungchae Kim, DongHyun Kim, Jungbin Yun, and Kyungho Lee<br>Pixel Development Team, System LSI Division, Samsung Electronics Co., Ltd.                                                                                                                                                                                      |
| W11-F-6<br>10:15-10:30 | <b>Efficient Phase Modulation in a Graphene-Integrated MOS Optical Phase Shifter</b><br>Gijun Ju <sup>1,2</sup> , Kyunghwan Kim <sup>1</sup> , Sunghyun Hwang <sup>1</sup> , Kyul Ko <sup>1</sup> , Yujeong Kang <sup>1</sup> , Dae-Hwan Ahn <sup>1</sup> , Donghee Park <sup>1</sup> , In-Ho Lee <sup>1</sup> , Yong-Won Song <sup>1</sup> , Younghyun Kim <sup>2</sup> , and Jae-Hoon Han <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Department of Photonics and Nanoelectronics, Hanyang University |
| W11-F-7<br>10:30-10:45 | <b>CMOS 공정 기반 Single-Photon Avalanche Diodes의 항복전압 및 노이즈 온도 의존성에 대한 분석</b><br>Doyoon Eom <sup>1,2</sup> , Eunsung Park <sup>1</sup> , Hyun-Seung Choi <sup>1,2</sup> , Hyo-Sung Park <sup>1</sup> , Joo-Hyun Kim <sup>1,2</sup> , Seyoung Yook <sup>1</sup> , Doo-Hee Son <sup>1</sup> , Woo-Young Choi <sup>1</sup> , and Myung-Jae Lee <sup>1</sup><br><sup>1</sup> Department of Electrical and Electronic Engineering, Yonsei University, <sup>2</sup> Post-Silicon Semiconductor Institute, KIST                                      |

H. Display and Imaging Technologies 분과

O10\_[WJ1-H] Thin Film Transistors for Displays I

좌장: 최창순 선임연구원(KIST), 최소연 교수(한밭대학교)

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| WJ1-H-1<br>09:00-09:15         | <p>Monolithic 3D-Integrated <math>\mu</math>LEDoS Display Using AlInP/GaInP MQW Epitaxial Layers with High Internal Quantum Efficiency and Low Size Dependence</p> <p>Juhyuk Park<sup>1</sup>, Woojin Baek<sup>1</sup>, Hyunsu Kim<sup>1</sup>, Dae-Myeong Geum<sup>2</sup>, and Sanghyeon Kim<sup>1</sup></p> <p><sup>1</sup>School of Electrical Engineering, KAIST, <sup>2</sup>Department of Electrical &amp; Computer Engineering, Inha University</p> |
| WJ1-H-2<br>09:15-09:30         | <p>Improvement of Hydrogen Resistance and Reliability in IGZO TFTs Through Nitrogen Incorporation into Al<sub>2</sub>O<sub>3</sub></p> <p>Sang-Hyun Kim<sup>1</sup>, YuJin Yang<sup>2</sup>, and Jin-Seong Park<sup>1</sup></p> <p><sup>1</sup>Department of Display Science and Engineering, Hanyang University, <sup>2</sup>Department of Semiconductor Engineering, Hanyang University</p>                                                               |
| WJ1-H-3<br>09:30-09:45         | <p>Active-Matrix Electrochromic Monopixel Array on a Silicon Transistor Backplane</p> <p>Jae Min Jeon<sup>1</sup>, Hyo Eun Jeong<sup>2</sup>, Jun Seo Lee<sup>1</sup>, and Young Min Song<sup>2</sup></p> <p><sup>1</sup>School of Electrical Engineering and Computer Science, GIST, <sup>2</sup>School of Electrical Engineering, KAIST</p>                                                                                                               |
| WJ1-H-4<br>09:45-10:00         | <p>Conformal Transfer Printing Technology on Complex Surfaces Using Shape Deformable Stamp</p> <p>Hyeon Ji Yang<sup>1</sup>, Wonseok Yang<sup>2</sup>, and Yei Hwan Jung<sup>1,2</sup></p> <p><sup>1</sup>Department of AI Semiconductor Engineering, Hanyang University, <sup>2</sup>Department of Electronic Engineering, Hanyang University</p>                                                                                                          |
| 초청발표<br>WJ1-H-5<br>10:00-10:30 | <p>Toward Next-Generation Active-Matrix QLEDs: Optimized TFT-QLED Designs and QD Patterning Strategies</p> <p>Geun Woo Baek</p> <p>Department of Electronic Engineering, Hanbat National University</p>                                                                                                                                                                                                                                                     |

D. Thin Film Process Technology 분과

O11\_[WC2-D] Memory Capacitors II

좌장: 김성근 책임(KIST), 이웅규 교수(송실대학교)

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| 초청발표<br>WC2-D-1<br>10:55-11:25 | <b>Interfacial Layer Engineering for Enhanced Properties of Scaled Memory Capacitor Materials</b><br>Dae Seon Kwon<br>Department of Chemical and Biological Engineering, Sookmyung Women's University                                                                                                                                                                                                                                                                                                                                                                                                                                                |
| WC2-D-2<br>11:25-11:40         | <b>In-Situ Multimodal STEM Analysis of Interfacial Dead Layer in High-<math>\kappa</math> Oxide Thin Film Capacitors</b><br>이기용 <sup>1</sup> , Yaolong Xing <sup>2</sup> , 변진호 <sup>1</sup> , 정명호 <sup>3</sup> , 서진솔 <sup>4</sup> , 방정일 <sup>3</sup> , 이재호 <sup>3</sup> , 이주호 <sup>3</sup> , 김해룡 <sup>3</sup> , 이은하 <sup>3</sup> , 오상호 <sup>1</sup><br><sup>1</sup> 한국에너지공과대학교 에너지공학부, <sup>2</sup> Department Structure and Nano-/Micromechanics of Materials, Max Planck Institute for Sustainable Materials, <sup>3</sup> 삼성전자 종합기술원, <sup>4</sup> 삼성전자 DS 부문                                                                                     |
| WC2-D-3<br>11:40-11:55         | <b>High-Performance Dynamic Random Access Memory Capacitor with an Equivalent Oxide Thickness of 0.31 nm via Stepwise Cycling in Y-Doped Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Thin Films</b><br>Jonghoon Shin <sup>1,2</sup> , Tae Kyun Kim <sup>1,2</sup> , Heewon Paik <sup>1,2</sup> , Haewon Song <sup>1,2</sup> , and Cheol Seong Hwang <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University                                                                                              |
| WC2-D-4<br>11:55-12:10         | <b>Achieving Higher-<math>\kappa</math> and Enhanced Reliability near the Morphotropic Phase Boundary in Hf<sub>1-x</sub>Zr<sub>x</sub>O<sub>2</sub> by Interfacial Nitride Metal Layer for DRAM Cell Capacitor</b><br>Jaewon Chung <sup>1</sup> , Sangkuk Han <sup>2</sup> , Wonjae Choi <sup>1</sup> , Haesoo Jang <sup>1</sup> , Kyungwook Park <sup>2</sup> , Sangmyun Lim <sup>1</sup> , Soyoung Park <sup>1</sup> , Sangwoo Jeong <sup>2</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University |
| WC2-D-5<br>12:10-12:25         | <b>Enhancement of Fatigue Endurance in Ferroelectric Hf<sub>x</sub>Zr<sub>1-x</sub>O<sub>2</sub> DRAM Capacitors through Remote Plasma ALD</b><br>Ji Won Kim, In Kook Hwang, Byung Wook Kim, Young Woon Jang, Hyeon Wu Nam, Min Kyun Kang, and Chang Bun Yoon<br>Department of Advanced Materials Engineering, Tech University of Korea                                                                                                                                                                                                                                                                                                              |

J. Nano-Science & Technology 분과

O12\_[WD2-J] 2D 반도체 기반 트랜지스터 및 디바이스

좌장: 이철호 교수(서울대학교), 강주훈 교수(연세대학교)

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| 초청발표<br>WD2-J-1<br>10:55-11:25 | <b>2D Material-Based Ferroelectric Source Gated Transistor</b><br>Joon-Seok Kim<br>School of Electronics and Electrical Engineering, Hongik University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                       |
| WD2-J-2<br>11:25-11:40         | <b>P-Type Doping of Multilayer WSe<sub>2</sub> Transistors via Iodination</b><br>Hojun Kim, Gunwon Seo, Seongmin Lee, Danbi Lee, Jeongbin Lee, and Min Sup Choi<br>Department of Materials Science and Engineering, Chungnam National University                                                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| WD2-J-3<br>11:40-11:55         | <b>Polarity Engineering in a Single MoTe<sub>2</sub> Device for Homogeneous Complementary Circuit Applications</b><br>Hyeonchang Son <sup>1</sup> and Dong-Ho Kang <sup>1,2</sup><br><sup>1</sup> Department of Electrical Engineering and Computer Science, GIST, <sup>2</sup> Department of Semiconductor Engineering, GIST                                                                                                                                                                                                                                                                                                                                                                                                |
| WD2-J-4<br>11:55-12:10         | <b>Vertically Stacked NMOS Inverter based on Multi-layer WS<sub>2</sub> Formed via Multiple Wet-Transfers of Monolayer WS<sub>2</sub></b><br>Jiwon Ma <sup>1</sup> , Dae Kyu Lee <sup>2</sup> , Eunyeong Yang <sup>1</sup> , Joon Young Kwak <sup>3</sup> , and Jiwon Chang <sup>1,4</sup><br><sup>1</sup> Department of Materials Science and Engineering, Yonsei University, <sup>2</sup> KIST, <sup>3</sup> Division of Electronic and Semiconductor Engineering, Ewha Womans University, <sup>4</sup> Department of System Semiconductor Engineering, Yonsei University                                                                                                                                                  |
| WD2-J-5<br>12:10-12:25         | <b>A Three-Dimensional Nanogap for High-Performance MoS<sub>2</sub> Gate-All-Around Transistors</b><br>Junwoo Kim, Hyesu Ryu, Minjin Kim, and Sang Hyun Lee<br>School of Chemical Engineering, Chonnam National University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                   |
| WD2-J-6<br>12:25-12:40         | <b>Charged Impurity-Scattering-Free Transport in Large-Area MoS<sub>2</sub> FETs by Diffusion-Mediated Modulation Doping</b><br>Jiwoo Yang <sup>1,2</sup> , Yongtaek Hong <sup>2</sup> , Takhee Lee <sup>3,4</sup> , Kyungjune Cho <sup>5,6</sup> , and Seungjun Chung <sup>1</sup><br><sup>1</sup> School of Electrical and Engineering, Korea University, <sup>2</sup> Department of Electrical and Computer Engineering, Seoul National University, <sup>3</sup> Department of Physics and Astronomy, Seoul National University, <sup>4</sup> Institute of Applied Physics, Seoul National University, <sup>5</sup> Electronic and Hybrid Materials Research Center, KIST, <sup>6</sup> Convergence Research Center, KIST |

E. Compound Semiconductors 분과

O13\_[WE2-E] Wide Bandgap Power Devices

좌장: 이형석 기술총괄(한국전자통신연구원), 김현섭 교수(국립군산대학교)

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| WE2-E-1<br>10:55-11:10 | <p>Normally-off Al/HfO<sub>2</sub>/Al-Gated Diamond Field Effect Transistor on a Hetero-Epitaxially Grown Diamond Substrate</p> <p>Yoonseok Nam<sup>1</sup>, Taemyung Kwak<sup>1</sup>, Hyunsu Ma<sup>1</sup>, Seolyoung Oh<sup>1</sup>, Geunho Yoo<sup>1</sup>, Seong-Woo Kim<sup>2</sup>, and Okhyun Nam<sup>1</sup></p> <p><sup>1</sup>Convergence Center for Advanced Nano Semiconductor, Department of Nano-Semiconductor Engineering, Tech University of Korea, <sup>2</sup>Orbray Co., Ltd.</p>                                                                                                                                                                                                                                                               |
| WE2-E-2<br>11:10-11:25 | <p>High-Temperature Reverse Bias Reliability of Edge Termination Structures in 4H-SiC Power Devices</p> <p>정승완<sup>1</sup>, 김상엽<sup>1</sup>, 석오균<sup>2</sup></p> <p><sup>1</sup>부산대학교 전기전자공학과, <sup>2</sup>부산대학교 전기전자공학부</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                         |
| WE2-E-3<br>11:25-11:40 | <p>Enhancement-Mode Al-Rich AlGa<sub>N</sub> Channel HEMTs Realized by Superlattice and Gate Recess Design</p> <p>Jaejin Heo, Joocheol Jeong, Shyam Mohan, Hyogeun Cho, Mingoo Jo, Minyeong Kim, and Okhyun Nam</p> <p>Convergence Center for Advanced Nano Semiconductor, Department of Nano-Semiconductor Engineering, Tech University of Korea</p>                                                                                                                                                                                                                                                                                                                                                                                                                |
| WE2-E-4<br>11:40-11:55 | <p>상온 스퍼터링 증착 방식의 Boron Nitride를 활용한 p-GaN/AlGa<sub>N</sub>/Ga<sub>N</sub> 소자 특성 향상 연구</p> <p>Jun-Hyeok Yim, JinHyeok Pyo, MyeongSu Chae, SangYeon Pak, Hyungtak Kim, and Ho-Young Cha</p> <p>School of Electrical and Electronic Engineering, Hongik University</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| WE2-E-5<br>11:55-12:10 | <p>Diode-Embedded E-mode P-GaN/AlGa<sub>N</sub>/Ga<sub>N</sub> HEMT</p> <p>Min-Ji Cho, Jun-Hyeok Lim, and Ho-Young Cha</p> <p>School of Electronic and Electrical Engineering, Hongik University</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| WE2-E-6<br>12:10-12:25 | <p>Vertical GaN-Based Heterojunction Bipolar Transistors with an Al-Doped ZnO Collector</p> <p>Sooyoung Kim<sup>1,2</sup>, Go-eun Bang<sup>3</sup>, Chang-yong Kim<sup>3</sup>, Taenam Kwon<sup>1</sup>, Jongseob Kim<sup>4</sup>, Kyoung-Kook Kim<sup>3</sup>, Dong Yeong Kim<sup>5</sup>, and Jaehee Cho<sup>1</sup></p> <p><sup>1</sup>School of Semiconductor and Chemical Engineering, Jeonbuk National University, <sup>2</sup>Semiconductor Process Technology Research Center, Semiconductor Physics Research Center, Jeonbuk National University, <sup>3</sup>Department of Semiconductor Engineering, Tech University of Korea, <sup>4</sup>Samsung Electronics Co., Ltd., <sup>5</sup>Major of Semiconductor Engineering, Pukyong National University</p> |
| WE2-E-7<br>12:25-12:40 | <p>Thermal Management Solutions for GaN HEMTs through Electro-Thermal Modeling</p> <p>Jisu Kim, Changhwan Song, Jungwon Choi, Hyeonjin Nam, and Jungwan Cho</p> <p>School of Mechanical Engineering, Sungkyunkwan University</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |

V. Quantum Technology 분과

O14\_[WF2-V] Quantum Technology I

좌장: 주정진 본부장(ETRI), 최태영 교수(이화여자대학교)

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| 초청발표<br>WF2-V-1<br>10:55-11:25 | Trapped Ion-Based Quantum Computing<br>Taeyoung Choi<br>Department of Physics, Ewha Womans University                                                        |
| 초청발표<br>WF2-V-2<br>11:25-11:55 | A Software-Defined Quantum Processor Using Neutral-Atom Arrays<br>김동규<br>한국과학기술원 물리학과                                                                        |
| 초청발표<br>WF2-V-3<br>11:55-12:25 | Full-Wave 전자기 수치해석 기반의 양자 광학 현상 모델링<br>Dong-Yeop Na<br>Department of Electrical Engineering, POSTECH                                                         |
| WF2-V-4<br>12:25-12:40         | Observation of PT-Symmetric Transitions in a Trapped $^{40}\text{Ca}^+$ Ion<br>Youngil Moon and Moonjoo Lee<br>Department of Electrical Engineering, POSTECH |

A. Interconnect & Package 분과

O15\_[WG2-A] Advanced Package II

좌장: 김명준 교수(성균관대학교), 이태익 수석연구원(한국생산기술연구원)

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| 초청발표<br>WG2-A-1<br>10:55-11:25 | <b>Comparative Study of Adhesion Energy in Symmetric and Asymmetric Substrate Bonding</b><br>Ah-Young Park <sup>1,2</sup> and Hakyung Jeong <sup>3</sup><br><sup>1</sup> Department of Materials Science and Engineering, University of Seoul, <sup>2</sup> Center for Semiconductor Research, University of Seoul, <sup>3</sup> Semiconductor Manufacturing Research Center, KIMM                                                                                                                                                                                                                                                                |
| WG2-A-2<br>11:25-11:40         | <b>Plasma Activated SiO<sub>2</sub> and SiCN Dielectrics and Bonding Characteristics</b><br>Sunbum Kim <sup>1</sup> , Kyoungyeon Min <sup>2</sup> , Dugkyu Han <sup>1</sup> , Sehyeon Choi <sup>1</sup> , Jaeho Lee <sup>1</sup> , Kang Baek Seo <sup>2</sup> , Ahra Jo <sup>3</sup> , Juno Kim <sup>3</sup> , Moonkeun Kim <sup>3</sup> , Euisun Choi <sup>3</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University, <sup>3</sup> Advanced Process Development Lap, Samsung Electronics Co., Ltd. |
| WG2-A-3<br>11:40-11:55         | <b>Impact of Surface Topography on Cu/Dielectric Hybrid Bonding: A Finite Element Analysis Study</b><br>Yoonho Choi <sup>1</sup> , So-Yeon Park <sup>1</sup> , Minjae Park <sup>1</sup> , Seung-Ho Seo <sup>2</sup> , Sarah Eunkyung Kim <sup>3</sup> , and Won-Jun Lee <sup>1</sup><br><sup>1</sup> Department of Nanotechnology and Advanced Materials Engineering, Sejong University, <sup>2</sup> GO Element Co., Ltd., <sup>3</sup> Department of Semiconductor Engineering, Seoul National University of Science & Technology                                                                                                               |
| WG2-A-4<br>11:55-12:10         | <b>Cu-Contamination Free Hybrid Bonding via MoS<sub>2</sub> Passivation Layer</b><br>Hyunbin Choi <sup>1</sup> , Sihoon Son <sup>2,3</sup> , Dongho Lee <sup>4</sup> , Geonwook Kim <sup>4</sup> , and Taesung Kim <sup>1,2,3,4</sup><br><sup>1</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University, <sup>2</sup> SKKU Advanced Institute of Nano Technology, Sungkyunkwan University, <sup>3</sup> Department of Nano Science and Technology, Sungkyunkwan University, <sup>4</sup> School of Mechanical Engineering, Sungkyunkwan University                                                                     |
| WG2-A-5<br>12:10-12:25         | <b>Impact of Misalignment and Dishing on Cu-Cu Hybrid Bonding Reliability</b><br>Sang-Hoon Kim <sup>1</sup> , Changhyeon Kim <sup>2</sup> , Jihun Kim <sup>2</sup> , Sunwoo Han <sup>2</sup> , Dae-Won Lee <sup>2</sup> , Hae Ri Kim <sup>4</sup> , Yeoun Soo Kim <sup>4</sup> , Ji Ho Kang <sup>4</sup> , and Eun-Ho Lee <sup>1,2,3</sup><br><sup>1</sup> Department of Smart Fab. Technology, Sungkyunkwan University, <sup>2</sup> Department of Mechanical Engineering, Sungkyunkwan University, <sup>3</sup> Department of Intelligent Robotics, Sungkyunkwan University, <sup>4</sup> WF Bonding, SK hynix Inc.                             |
| WG2-A-6<br>12:25-12:40         | <b>Epoxy-Based Reducing Polymer Composites for Low-Temperature Cu/Polymer Hybrid Bonding Processes</b><br>Dong Keon An, Chansu Jeon, and Kyung Min Kim<br>Department of Materials Science and Engineering, KAIST                                                                                                                                                                                                                                                                                                                                                                                                                                  |

G. Device & Process Modeling, Simulation and Reliability 분과

O16\_[WH2-G] Device & Process Modeling, Simulation and Reliability II

좌장: 김현우 교수(건국대학교), 전종욱 교수(성균관대학교)

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| 초청발표<br>WH2-G-1<br>10:55-11:25 | Quantum-Tunneling-Driven Nonradiative Carrier Trapping at Si/SiO <sub>2</sub> Interfaces: A First-Principles Study<br>Yongjin Shin<br>Department of Semiconductor Convergence Engineering, Dankook University                                                                                                                                                                                                                                                                                                                                                                                      |
| WH2-G-2<br>11:25-11:40         | Spatial Trap Profiles in the Charge Trap Layer of 3-D NAND Flash Cell Using a Positive-Bias Induced Trap Extraction (P-BITE) Method<br>Seungjae Kim <sup>1</sup> , Donghyun Go <sup>2</sup> , Donghwi Kim <sup>2</sup> , Daehan Won <sup>1</sup> , and Jeong-Soo Lee <sup>1,2</sup><br><sup>1</sup> Graduate School of Semiconductor Technology, POSTECH, <sup>2</sup> Department of Electrical Engineering, POSTECH                                                                                                                                                                               |
| WH2-G-3<br>11:40-11:55         | Dynamic Source-resistance in RF GaN HEMTs and Its Impact on the g <sub>m</sub> Non-linearity<br>Su-Min Choi <sup>1</sup> , Wan-Soo Park <sup>1</sup> , Min-Gyu Song <sup>1</sup> , Se-Hun Kim <sup>1</sup> , Ji-In Byeon <sup>1</sup> , Seung-Woo Son <sup>1</sup> , In-Geun Lee <sup>1</sup> , Ho-Kyun Ahn <sup>2</sup> , Dong-Hee Shin <sup>3</sup> , Young-Kyun Noh <sup>3</sup> , Jae-Hak Lee <sup>1</sup> , Kyounghoon Yang <sup>4</sup> , and Dae-Hyun Kim <sup>1</sup><br><sup>1</sup> Kyungpook National University, <sup>2</sup> ETRI, <sup>3</sup> IWWorks Co., Ltd., <sup>4</sup> KAIST |
| WH2-G-4<br>11:55-12:10         | Accuracy Test of Numerical Methods for Generalization of Scharfetter-Gummel Scheme<br>Ji-Young Kim and Sung-Min Hong<br>Department of Electrical Engineering and Computer Science, GIST                                                                                                                                                                                                                                                                                                                                                                                                            |
| WH2-G-5<br>12:10-12:25         | Investigation of Threshold Voltage Instability in E-Mode GaN HEMTs through TCAD Simulations<br>Geon-Tae Jang, Nakwon Yu, Jongmin Kim, Youngchul Kim, and Hyunchul Nah<br>Technology Enabling Center, DB HiTek                                                                                                                                                                                                                                                                                                                                                                                      |
| WH2-G-6<br>12:25-12:40         | Characterization of Well Proximity Effect and TCAD Calibration for CIS Pixel Implant<br>Kyeongjin Park, Jongmin Kim, Youngchul Kim, and Hyunchul Nah<br>Korea Tech. Enabling Center, DB HiTek Co. Ltd                                                                                                                                                                                                                                                                                                                                                                                              |

F. Silicon and Group-IV Devices and Integration Technology 분과

O17\_[W12-F] Special Topics: Device Reliability/Annealing Process

좌장: 김상완 교수(서강대학교), 김경록 교수(UNIST)

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| 초청발표<br>W12-F-1<br>10:55-11:25 | Introduction to Rad-hardened Semiconductor R&D and Test Infra for Aero-space Application<br>Chang Goo Kang, Jeong Min Park, Su Jin Kim, and Yongsu Lee<br>Advanced Radiation Technology Institute, KAERI                                                                                                                                                                                                                                                                                                                                                                                            |
| 초청발표<br>W12-F-2<br>11:25-11:55 | RGB Continuous-Wave Laser Annealing for Low Thermal Budget CMOS Integration: Junction Activation, Silicidation and Ferroelectric HZO Crystallization<br>Hyeon Jun Hwang<br>Department of Semiconductor Engineering, Mokpo National University                                                                                                                                                                                                                                                                                                                                                       |
| W12-F-3<br>11:55-12:10         | Comparative Study of Multiple High-Pressure Rapid Deuterium Annealing for MOSFET Performance Enhancement<br>Min-Woo Kim, Hyo-Jun Park, Eui-Cheol Yun, Sang-Min Kang, Da-Eun Bang, Dol Sohn, and Jun-Young Park<br>School of Semiconductor Engineering, Chungbuk National University                                                                                                                                                                                                                                                                                                                 |
| W12-F-4<br>12:10-12:25         | Process Optimization for Highly Activated Ultra-Shallow Junction Formation with Continuous Wave Laser Annealing<br>Gunryeol Cho, Sanguk Lee, Yonghwan Ahn, Minchan Kim, Sunmin Yeou, Jaeseong Pyo, Jitae Yoo, and Rock-Hyun Baek<br>Department of Electrical Engineering, POSTECH                                                                                                                                                                                                                                                                                                                   |
| W12-F-5<br>12:25-12:40         | Mitigating BTI Degradation in HKMG Transistors via Oxygen Reservoir Layer Engineering<br>Kyungwook Park <sup>1,3</sup> , Sangkuk Han <sup>1</sup> , Wonjae Choi <sup>2</sup> , Haesoo Jang <sup>2</sup> , Jaewon Chung <sup>2</sup> , Sangmyun Lim <sup>2</sup> , Sangwoo Jeong <sup>1</sup> , Soyoung Park <sup>2</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University, <sup>3</sup> DRAM Process Development Team, Samsung Electronics Co., Ltd. |

H. Display and Imaging Technologies 분과

O18\_[WJ2-H] Photodiodes and Image Sensors

좌장: 백근우 교수(한밭대학교), 최창순 선임연구원(KIST)

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| 초청발표<br>WJ1-H-1<br>10:55-11:25 | Wide Bandgap Semiconductor Based Photomemory Application<br>Ramit Kumar Mondal, Yoon-Ho Kim, and Sang-Hyeon Kim<br>School of Electrical and Electronic Engineering, Nanyang Technological University                                                                                                                                                    |
| WJ2-H-2<br>11:25-11:40         | Single-Band Guided-Mode Resonance InGaAs Photodetector for Multispectral Polarization Sensing<br>Junho Jang <sup>1</sup> , Il-Suk Kang <sup>2</sup> , Yeon-Wha Oh <sup>2</sup> , Sanghee Jung <sup>2</sup> , Huijae Cho <sup>2</sup> , and SangHyeon Kim <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, KAIST, <sup>2</sup> NNFC        |
| WJ2-H-3<br>11:40-11:55         | Hyperspectral Imaging via Air-Gap Cavity Tunable Filter<br>Nayeon Kim <sup>1,2</sup> , Sunghyun Hwang <sup>1</sup> , Eui-Hyoun Ryu <sup>1</sup> , Ji-Hwan Son <sup>1</sup> , Nayoung Kim <sup>1</sup> , and In-Ho Lee <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> School of Electrical Engineering, Korea University |
| WJ2-H-4<br>11:55-12:10         | Ultra Low Noise Global Shutter CMOS Image Sensor with High Density MIM Capacitor<br>Junha Kang, Yoonjay Han, Taemin Kim, Jonguk Kim, Suji Hwang, Jihye Jeong, Jungsan Kim, Sangjin Choi, Yongsoon Park, Daekun Ahn, Jae-Kyu Lee, and Jonghyun Go<br>Semiconductor R&D Center, Samsung Electronics Co., Ltd.                                             |
| WJ2-H-5<br>12:10-12:25         | Pixel-like TEG Design for Accurate FD-Leakage Prediction in Global-Shutter CIS Sensors<br>Surim Lee, Jaehoon Jeon, Haeyong Park, Jeong-soon Kang, Sangyoon Kim, Jaehyun Kim, Taehyung Kim, Woochan Lee, Seung-Sik Kim, Jae-Kyu Lee, and Jonghyun Go<br>Semiconductor R&D Center, Samsung Electronics Co., Ltd.                                          |
| WJ2-H-6<br>12:25-12:40         | 최첨단 High CRA CIS의 Gr Gb Difference 원인 분석<br>강정우 <sup>1</sup> , 황제혁 <sup>1</sup> , 박민영 <sup>3</sup> , 정재오 <sup>3</sup> , 추성민 <sup>3</sup> , 김동수 <sup>3</sup> , 이지원 <sup>1,2</sup><br><sup>1</sup> 포항공과대학교 반도체대학원, <sup>2</sup> 포항공과대학교 반도체공학과, <sup>3</sup> 삼성전자 MX사업부                                                                                   |

M. RF and Wireless Design 분과

O19\_[WA3-M] RF and Wireless Design

좌장: 권구덕 교수(강원대학교), 김주성 교수(이화여자대학교)

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| 초청발표<br>WA3-M-1<br>16:00-16:30 | <b>Low Noise and Broadband Cryo-CMOS Receiver for Superconducting Multi-qubits Read-out</b><br>Jusung Kim <sup>1</sup> , Hyeonsik Ahn <sup>2</sup> , Juhui Jeong <sup>3</sup> , and Junghwan Han <sup>3</sup><br><sup>1</sup> Division of Electronic and Semiconductor Engineering, Ewha Womans University, <sup>2</sup> Department of Electronics Engineering, Hanbat National University, <sup>3</sup> Department of Radio and Information Communication Engineering, Chungnam National University                                                                                                                                                                                                                                                                                                          |
| WA3-M-2<br>16:30-16:45         | <b>Channel-Selection LNA with Complex Pole <i>N</i>-Path Feedforward Blocker Cancellation for Advanced 5G NR FDD RX</b><br>Hyeonjun Kim, Sengjun Jo, and Kuduck Kwon<br>Department of Electronic Engineering, Kangwon National University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| WA3-M-3<br>16:45-17:00         | <b>HM3D Integrated RF Platform with III-V HEMTs on Si CMOS for Next-Generation Wireless Communication Systems</b><br>Jaeyong Jeong <sup>1</sup> , Jeong-Taek Lim <sup>2</sup> , Yoon-Je Suh <sup>1</sup> , Nahyun Rheem <sup>1</sup> , Chan Jik Lee <sup>1</sup> , Bong Ho Kim <sup>3</sup> , Joon Pyo Kim <sup>3</sup> , Jongmin Kim <sup>4</sup> , Jongwon Lee <sup>5</sup> , Choul-Young Kim <sup>2</sup> , and Sanghyeon Kim <sup>1,6</sup><br><sup>1</sup> School of Electrical Engineering, KAIST, <sup>2</sup> Department of Electronics Engineering, Chungnam National University, <sup>3</sup> Samsung Electronics Co., Ltd., <sup>4</sup> KANC, <sup>5</sup> Department of Semiconductor Convergence, Chungnam National University, <sup>6</sup> Graduate School of Semiconductor Technology, KAIST |
| 초청발표<br>WA3-M-4<br>17:00-17:30 | <b>A Fully Integrated IEEE 802.15.4/4z-Compliant IR-UWB System-on-Chip RF Transceiver Supporting Precision Positioning and Channels 5 to 12</b><br>Sinyoung Kim, Hyun-Gi Seok, and Hyun-Chul Park<br>System LSI Division, Samsung Electronics Co., Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                       |

K. Memory (Design & Process Technology) 분과

O20\_[WB3-K] Advanced Memory

좌장: 강명곤 교수(서울시립대학교), 백승재 마스터(삼성전자)

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| 초청발표<br>WB3-K-1<br>16:00-16:30 | AI-Driven Device and Process Modeling Platforms for Next-Generation Semiconductor Development<br>Hyunbo Cho<br>Alsemy Inc.                                                                                                                                                                                                                                                                                                                                                       |
| WB3-K-2<br>16:30-16:45         | Block-Diagonal Hadamard Matrices Based Dynamic Transfer Algorithm for Volatile Processing-In-Memory Based Cross-Point Arrays<br>Jinho Byun <sup>1</sup> , Sengkun Kim <sup>2</sup> , Jeonghoon Son <sup>1</sup> , and Seyoung Kim <sup>1,3</sup><br><sup>1</sup> Department of Electrical Engineering, POSTECH, <sup>2</sup> Department of Materials Science and Engineering, POSTECH, <sup>3</sup> Graduate School of Semiconductor Technology, POSTECH                         |
| WB3-K-3<br>16:45-17:00         | Self-Rectifying Characteristics in RRAM Using Semiconducting CNT Selector Layer<br>Chan-Hyeok Nam <sup>1</sup> , Beomseu Je <sup>1</sup> , Beomjeon Jung <sup>1</sup> , Ju Han Ryu <sup>2</sup> , Yeongmyeong Cho <sup>2</sup> , Sang Min Park <sup>2</sup> , Goeun Heo <sup>2</sup> , Younglae <b>첼 회</b><br><sup>1</sup> Department of Electro <b>첼 회</b> University, <sup>2</sup> Department of Electronic and Semiconductor Engineering, Gangneung-Wonju National University |
| WB3-K-4<br>17:00-17:15         | A Configurable Processing-in-Memory Evaluation Framework for Large Language Model Inference<br>Minki Choi, Juhyeon Lee, and Wonbo Shim<br>Department of Electrical and Information Engineering, Seoul National University of Science & Technology                                                                                                                                                                                                                                |
| WB3-K-5<br>17:15-17:30         | A Partially-Unrolled DFE Architecture for Low-Power, Low-Area High-Speed DSP Receivers<br>Seung Yun Lee and Jaeha Kim<br>Department of Electrical and Computer Engineering, Seoul National University                                                                                                                                                                                                                                                                            |

I. MEMS & Sensors Systems 분과

O21\_[WJ3-I] MEMS and Sensor System I

좌장: 박윤석 교수(경희대학교), 최준환 교수(단국대학교)

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| 초청발표<br>WJ3-I-1<br>16:00–16:30 | <b>Electromechanical and Electrochemical Energy Harvesting from Ambient Moisture</b><br>Jiaming Zhou, Eunjong Kim, and Dong-Myeong Shin<br>Department of Mechanical Engineering, The University of Hong Kong                                                                                                                                                                                                                                                                                                                                                                                               |
| WJ3-I-2<br>16:30–16:45         | <b>Radiation Hardness of Graphene Gas Sensor</b><br>Jaeyeon Oh <sup>1,2</sup> , Jongin Park <sup>1</sup> , and Yeonhoo Kim <sup>1</sup><br><sup>1</sup> Strategic Technology Research Institute, KRISS, <sup>2</sup> Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                                                                                            |
| WJ3-I-3<br>16:45–17:00         | <b>High-Sensitivity Pressure Sensors based on 3D Hierarchical MoS<sub>2</sub> with Wide Dynamic Range</b><br>Jeongin Song <sup>1,2</sup> , Se Min Hwang <sup>1,3</sup> , Min Sup Choi <sup>3</sup> , Sang Woo Kang <sup>1,4</sup> , Taesung Kim <sup>2</sup> , and Jihun Mun <sup>1</sup><br><sup>1</sup> Semiconductor and Display Metrology Group, KRISS, <sup>2</sup> School of Mechanical Engineering, Sungkyunkwan University, <sup>3</sup> Department of Materials Science and Engineering, Chungnam National University, <sup>4</sup> Measurement Engineering, University of Science and Technology |
| 초청발표<br>WJ3-I-4<br>17:00–17:30 | <b>On-Device AI Sensors: Gaussian Transistors and Light-Driven Spikes for Deepfake Detection</b><br>Hocheon Yoo<br>Department of Electronic Engineering, Hanyang University                                                                                                                                                                                                                                                                                                                                                                                                                                |

R. Semiconductor Software 분과

O22\_[WD3-R] R & O 분과 통합 세션 (부제: Semiconductor Software)

좌장: 강동현 교수(동국대학교), 최웅 교수(숙명여자대학교)

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| 초청발표<br>WD3-R-1<br>16:00-16:30 | High Accuracy Reverse Engineering Tool for Xilinx FPGAs<br>Soyeon Choi<br>Department of Semiconductor System Engineering, Hanbat National University                                  |
| 초청발표<br>WD3-R-2<br>16:30-17:00 | Toward 100M IOPS SSD in the AI Era<br>Eyye Hyun Nam<br>FADU Inc.                                                                                                                      |
| WD3-R-3<br>17:00-17:15         | Bottleneck Analysis of On-Device Large Language Model Inference under Out-of-Core Execution<br>Seunghun Oh and Jisung Park<br>Department of Computer Science and Engineering, POSTECH |
| WD3-R-4<br>17:15-17:30         | eBPF를 활용한 Linux 커널 I/O 스택의 계층별 지연 시간 분석<br>김유리 <sup>1</sup> , 이찬용 <sup>2</sup> , 강동현 <sup>1</sup><br><sup>1</sup> 동국대학교 컴퓨터·AI학부, <sup>2</sup> 동국대학교 일반대학원 컴퓨터·AI학과                   |

E. Compound Semiconductors 분과

O23\_[WE3-E] High Speed Devices and Circuits

좌장: 김형탁 교수(홍익대학교), 고유민 실장(한국나노기술원)

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| <div>WE3-E-1</div> <div>16:00–16:15</div> | <div><b><math>f_T = 815</math> GHz <math>\text{In}_{0.8}\text{Ga}_{0.2}\text{As}/\text{In}_{0.52}\text{Al}_{0.48}\text{As}</math> QW HEMTs with <math>L_g = 23</math> nm</b></div> <div>Seung-Woo Son<sup>1</sup>, Min-Seo Yu<sup>1</sup>, Sang-Pyeong Son<sup>1</sup>, In-Geun Lee<sup>1</sup>, Kyoungsoon Yang<sup>2</sup>, Jae-Hak Lee<sup>1</sup>, and Dae-Hyun Kim<sup>1</sup></div> <div><sup>1</sup>School of Electronic and Electrical Engineering, Kyungpook National University, <sup>2</sup>KAIST</div>                                                                                                                                                                           |
| <div>WE3-E-2</div> <div>16:15–16:30</div> | <div><b>Effect of a Wider Bandgap Al-Rich InAlAs Layer on Suppressing Gate Leakage in Low-Noise InP HEMTs</b></div> <div>Juwon Seo<sup>1,2</sup>, Won Jun Lee<sup>1,3</sup>, Il Ki Han<sup>1</sup>, DaeHwan Ahn<sup>4</sup>, Jae-Hoon Han<sup>4</sup>, Mun Seok Jeong<sup>2</sup>, and JoonHyun Kang<sup>1</sup></div> <div><sup>1</sup>Nanophotonic System Research Center, KIST, <sup>2</sup>Department of Physics, Hanyang University, <sup>3</sup>School of Electrical Engineering, Korea University, <sup>4</sup>Center for Quantum Technology, KIST</div>                                                                                                                              |
| <div>WE3-E-3</div> <div>16:30–16:45</div> | <div><b>InAlGa<sub>N</sub>/Al<sub>N</sub>/Ga<sub>N</sub> High-electron Mobility Transistors with Selective <math>n^+</math> Ga<sub>N</sub> S/D Regrowth and <math>f_T &gt; 250</math> GHz</b></div> <div>Wan-Soo Park<sup>1</sup>, Su-Min Choi<sup>1</sup>, Min-Gyu Song<sup>1</sup>, Se-Hun Kim<sup>1</sup>, Ji-In Byeon<sup>1</sup>, Seung-Woo Son<sup>1</sup>, In-Geun Lee<sup>1</sup>, Ho-Kyun Ahn<sup>2</sup>, Dong-Hee Shin<sup>3</sup>, Young-Kyun Noh<sup>3</sup>, Jae-Hak Lee<sup>1</sup>, Kyoungsoon Yang<sup>4</sup>, and Dae-Hyun Kim<sup>1</sup></div> <div><sup>1</sup>Kyungpook National University, <sup>2</sup>ETRI, <sup>3</sup>IWWorks Co., Ltd., <sup>4</sup>KAIST</div> |
| <div>WE3-E-4</div> <div>16:45–17:00</div> | <div><b>Heterogeneous 3D Integrated RF Platform on CMOS via Die-to-Wafer Bonding Technology</b></div> <div>Jaeyong Jeong<sup>1</sup>, Chan Jik Lee<sup>1</sup>, Yoon-Je Suh<sup>1</sup>, Nahyun Rheem<sup>1</sup>, Bong Ho Kim<sup>1,2</sup>, Joon Pyo Kim<sup>1,2</sup>, Juhyuk Park<sup>1</sup>, and Sanghyeon Kim<sup>1,3</sup></div> <div><sup>1</sup>School of Electrical Engineering, KAIST, <sup>2</sup>Samsung Electronics Co., Ltd., <sup>3</sup>Graduate School of Semiconductor Technology, KAIST</div>                                                                                                                                                                           |
| <div>WE3-E-5</div> <div>17:00–17:15</div> | <div><b>Heterogeneous InGaAs/InP Biristor Oscillators for Fast, Power-Efficient Ising Machine Hardware</b></div> <div>이현준<sup>1</sup>, 김준표<sup>2,3</sup>, 김상현<sup>1,2</sup></div> <div><sup>1</sup>KAIST 반도체공학대학원, <sup>2</sup>KAIST 전기 및 전자공학부, <sup>3</sup>삼성전자 반도체연구소</div>                                                                                                                                                                                                                                                                                                                                                                                                               |

C. Material Growth & Characterization 분과

O24\_[WF3-C] Functional Membranes, Sensing, and Advanced Characterization

좌장: 김태헌 책임박사(KIST), 손창희 교수(UNIST)

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| 초청발표<br>WF3-C-1<br>16:00–16:30 | <b>Freestanding Single-crystalline Membranes in Chemical Sensor Application</b><br>Jun Min Suh <sup>1,2</sup><br><sup>1</sup> School of Transdisciplinary Innovations, Seoul National University, <sup>2</sup> Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                                                                           |
| WF3-C-2<br>16:30–16:45         | <b>Epitaxial Growth of Wurtzite BeO on Corundum <math>\alpha</math>-Ga<sub>2</sub>O<sub>3</sub> via Plasma-Enhanced Atomic Layer Deposition for Wide-Bandgap Power Devices</b><br>Jonghyun Bae <sup>1,2</sup> , Dohwan Jung <sup>1</sup> , Haekyun Bong <sup>1,2</sup> , Hyeong-Yun Kim <sup>3</sup> , Ji-Hyeon Park <sup>3</sup> , Dae-Woo Jeon <sup>3</sup> , and Jungwoo Oh <sup>1,2</sup><br><sup>1</sup> School of Integrated Technology, Yonsei University, <sup>2</sup> BK21 Graduate Program in Intelligent Semiconductor Technology, Yonsei University, <sup>3</sup> KICET |
| WF3-C-3<br>16:45–17:00         | <b>High Thermal Conductivity of Sub-100 nm BeO Thin Films</b><br>Jihyun Kim <sup>1</sup> , Jonghyun Bae <sup>2,3</sup> , Jisu Kim <sup>1</sup> , Dohwan Jung <sup>2</sup> , Dongyun Seo <sup>1</sup> , Jungwoo Oh <sup>2,3</sup> , and Jungwan Cho <sup>1</sup><br><sup>1</sup> School of Mechanical Engineering, Sungkyunkwan University, <sup>2</sup> School of Integrated Technology, Yonsei University, <sup>3</sup> BK21 Graduate Program in Intelligent Semiconductor Technology, Yonsei University                                                                           |
| WF3-C-4<br>17:00–17:15         | <b>Deep Learning Analysis of 4D-STEM Reveals 3D Polarization and Switching in Ferroelectric Capacitors</b><br>Jinho Byun <sup>1</sup> , Keeyong Lee <sup>1</sup> , Jeongil Bang <sup>2</sup> , Jaeho Lee <sup>2</sup> , Jooho Lee <sup>2</sup> , Haeryoung Kim <sup>2</sup> , Geun Ho Gu <sup>1</sup> , and Sang Ho Oh <sup>1</sup><br><sup>1</sup> Department of Energy Engineering, KENTECH, <sup>2</sup> Thin Film TU, Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd.                                                                                   |
| WF3-C-5<br>17:15–17:30         | <b>Direct Synthesis of Surface Functional Group-free Molybdenum Carbide MXene Thin Films by Chemical Vapor Deposition for Nitrogen Reduction Reaction</b><br>Junhyeok No <sup>1</sup> , Taemin Ahn <sup>2</sup> , Tae Hwan Kim <sup>3</sup> , and Hee Cheul Choi <sup>1,4</sup><br><sup>1</sup> Division of Advanced Materials Science, POSTECH, <sup>2</sup> Pohang Accelerator Laboratory, POSTECH, <sup>3</sup> Department of Physics, POSTECH, <sup>4</sup> Department of Chemistry, POSTECH                                                                                    |

S. Chip Design Contest 분과

O25\_[WG3-S] Chip Design Contest

좌장: 조경록 교수(충북대학교), 양종렬 교수(건국대학교)

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| WG3-S-1<br>16:00-16:15 | <p>An 850μW, 2-to-5GHz Jitter-Filtering and Instant-Toggling Injection-Locked Quadrature-Clock Generator for Low-Power Clock Distribution in HBM Interfaces</p> <p>Jeongbeom Seo<sup>1</sup>, Yuhwan Shin<sup>2</sup>, and Jaehyoun Choi<sup>1</sup></p> <p><sup>1</sup>Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup>Electrical Engineering, KAIST</p> |
| WG3-S-2<br>16:15-16:30 | <p>A 0.4-VDDQ 11.5-Gb/s/pin Transmitter with Switched-Coupling Charge-Pump Crosstalk Cancellation Achieving Eye-Margin Recovery for Ultra-Dense Die-to-Die Interfaces</p> <p>Yoochang Kim<sup>1</sup> and Young-Ha Hwang<sup>1,2</sup></p> <p><sup>1</sup>Department of Intelligent Semiconductors, Soongsil University, <sup>2</sup>School of Electronic Engineering, Soongsil University</p>      |
| WG3-S-3<br>16:30-16:45 | <p>Small-Area, High-Speed, and High Uniformity Source Driver IC for OLED-on-Silicon (OLEDoS) Displays</p> <p>Jung Hwan Oh, Wi Man Yoo, Dong Kun Lee, and Jong Seok Kim</p> <p>Department of Electronics and Electrical Engineering, Hanyang University ERICA</p>                                                                                                                                    |
| WG3-S-4<br>16:45-17:00 | <p>An Energy-Efficient Multi-Cell Battery Charger with Simultaneous Charging and Balancing</p> <p>Seongil Yeo and Kunhee Cho</p> <p>Department of Semiconductor Convergence Engineering, Sungkyunkwan University</p>                                                                                                                                                                                |

G. Device & Process Modeling, Simulation and Reliability 분과

O26\_[WH3-G] Device & Process Modeling, Simulation and Reliability III

좌장: 권용우 교수(홍익대학교), 김병조 교수(UNIST)

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| 초청발표<br>WH3-G-1<br>16:00–16:30 | <b>Bridging Atomistic Kinetics and Fluid Dynamics: A Multiscale Simulations from DFT Integrated Transient CFD for Industrial-Scale Spatial ALD</b><br>Hwanyeol Park <sup>1,2</sup><br><sup>1</sup> Department of Display Materials Engineering, Soonchunhyang University, <sup>2</sup> Department of Electronic Materials, Devices, and Equipment Engineering, Soonchunhyang University |
| WH3-G-2<br>16:30–16:45         | <b>Impact of Power Cycling Test on the Electrical Characteristics of p-GaN HEMTs</b><br>Taehyeon Kim <sup>1,2</sup> , Kihyun Kim <sup>1</sup> , Sungsik Lee <sup>2</sup> , and Inho Kang <sup>1</sup><br><sup>1</sup> Power SoC Research Center, KERI, <sup>2</sup> Department of Electronic Engineering, Pusan National University                                                     |
| WH3-G-3<br>16:45–17:00         | <b>Analysis of Quasi-Bound-State Tunneling in AlGaIn/AlIn/GaN HEMTs by NEGF-Based Quantum Transport Approach</b><br>Heonseok Oh and Mincheol Shin<br>School of Electrical Engineering, KAIST                                                                                                                                                                                            |
| WH3-G-4<br>17:00–17:15         | <b>TCAD Framework for Predicting Breakdown Voltage, Photon Detection Probability, and Dark Count Rate in Single-Photon Avalanche Diodes</b><br>Nakwon Yu, Jongmin Kim, Youngchul Kim, Ju-Hwan Jung, Sanghwan Kim, Man-Lyun Ha, and Hyunchul Nah<br>Technology Enabling Center, DB HiTek                                                                                                 |
| WH3-G-5<br>17:15–17:30         | <b>Investigation of Cell-to-Cell Analysis Methodology for ESD Protection Devices Using TCAD Simulation</b><br>Jehoon Lee, Jongmin Kim, and Youngchul Kim<br>Technology Development Department, DB HiTek                                                                                                                                                                                 |

F. Silicon and Group-IV Devices and Integration Technology 분과

O27\_[W13-F] Memory and Logic Devices for AI

좌장: 정규원 교수(서울대학교), 김시현 교수(서강대학교)

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| <div>W13-F-1</div> <div>16:00–16:15</div> | <div>Hopfield Neural Networks Using Vertical NAND Flash Memory for Large-Scale In-Memory Associative Computing</div> <div>Jin Ho Chang<sup>1,2</sup>, Jae Seung Woo<sup>1,2</sup>, Suk-Kang Sung<sup>3</sup>, Ki-Whan Song<sup>4</sup>, and Woo Young Choi<sup>1,2</sup></div> <div><sup>1</sup>Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup>Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup>Advanced Flash Technology Team, Samsung Electronics Co., Ltd., <sup>4</sup>Flash Design Team, Samsung Electronics Co., Ltd.</div> |
| <div>W13-F-2</div> <div>16:15–16:30</div> | <div>Automatic Training of Reconfigurable Analog Logic Circuit via LTSPICE-Python Co-Simulation towards Accuracy Maximization</div> <div>Joeun Lee<sup>1,2</sup> and Seongjae Cho<sup>1,2</sup></div> <div><sup>1</sup>Division of Electronics and Semiconductor Engineering, Ewha Womans University, <sup>2</sup>Institute for Multiscale Matter and Systems (IMMS), Ewha Womans University</div>                                                                                                                                                                                                                 |
| <div>W13-F-3</div> <div>16:30–16:45</div> | <div>Comparative Analysis of Channel Materials and Device Architectures in 2T0C DRAM</div> <div>Jimin Son and Changhwan Shin</div> <div>School of Electrical Engineering, College of Engineering, Korea University</div>                                                                                                                                                                                                                                                                                                                                                                                           |
| <div>W13-F-4</div> <div>16:45–17:00</div> | <div>Bonding Pressure Annealing Technique to Improve Reliability of FeRAM</div> <div>Myeongjae Choi<sup>1</sup>, Chaeho Kwon<sup>2</sup>, Jeongheon Cho<sup>2</sup>, and Changhwan Shin<sup>3</sup></div> <div><sup>1</sup>Department of Semiconductor System Engineering, Korea University, <sup>2</sup>Department of Semiconductor Engineering, Korea University, <sup>3</sup>School of Electrical Engineering, College of Engineering, Korea University</div>                                                                                                                                                   |
| <div>W13-F-5</div> <div>17:00–17:15</div> | <div>Analysis on High-Frequency Capacitance Characteristics of Si-Compatible Dual-Layer RRAM Designed for Low-Power Applications</div> <div>Euni Ko<sup>1,2</sup>, Soomin Kim<sup>1,2</sup>, and Seongjae Cho<sup>1,2</sup></div> <div><sup>1</sup>Department of Semiconductor Engineering, Ewha Womans University, <sup>2</sup>Institute for Multiscale Matter and Systems (IMMS), Ewha Womans University</div>                                                                                                                                                                                                   |
| <div>W13-F-6</div> <div>17:15–17:30</div> | <div>Via-embedded Self-rectifying Memristor based on 180nm CMOS Process</div> <div>Solji Park<sup>1</sup>, Gapseop Sim<sup>2</sup>, Won-Chul Lee<sup>2</sup>, Woo-Suk Sul<sup>2</sup>, Kyung Min Kim<sup>3</sup>, and Jongwon Lee<sup>1</sup></div> <div><sup>1</sup>Chungnam National University, <sup>2</sup>NNFC, <sup>3</sup>KAIST</div>                                                                                                                                                                                                                                                                       |

T. AI 분과

O28\_[WJ3-T] Artificial Intelligence II

좌장: 박정우 교수(성균관대학교), 김병수 센터장(KETI)

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| 초청발표<br>WJ3-T-1<br>16:00-16:30 | Ultra-low Power LLM Processor with Binary/Ternary Quantization<br>Sangyeob Kim<br>School of Integrated Technology, Yonsei University                                                                                                                                            |
| WJ3-T-2<br>16:30-16:45         | Deep Q-Network 기반 온-디바이스 자율주행로봇 경로 도출 시스템<br>권은혜, 백돈규<br>충북대학교 반도체공학부                                                                                                                                                                                                           |
| WJ3-T-3<br>16:45-17:00         | Compute-in-Memory 구조 기반 근전도 신호 획득 및 손동작 분류 System-on-Chip<br>홍준성 <sup>1,3</sup> , 유희재 <sup>1,3</sup> , 구민석 <sup>2,3,4</sup> , 김윤 <sup>1,3,4</sup><br><sup>1</sup> 서울시립대학교 전자전기컴퓨터공학과, <sup>2</sup> 서울시립대학교 첨단융합학부, <sup>3</sup> 서울시립대 반도체 연구센터(UOS-FAB), <sup>4</sup> 주식회사 IM전자 |
| WJ3-T-4<br>17:00-17:15         | BF16-to-BFP Conversion Architecture for Systolic Array Computation<br>Jihyeon Hwang, Taehong Min, Jungwoo Park, and Seung Eun Lee<br>Department of Electronic Engineering, Seoul National University of Science & Technology                                                    |
| WJ3-T-5<br>17:15-17:30         | Low-Latency and Resource-Optimized LeNet-5 Accelerator Using FPGA<br>DongHwan Yoon, JoonSeok Kim, and Seokhyeong Kang<br>Graduate School of Semiconductor Technology, POSTECH                                                                                                   |

D. Thin Film Process Technology 분과

O29\_[TA1-D] Emerging Devices I

좌장: 최병준 교수(서울과학기술대학교)

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| 초청발표<br>TA1-D-1<br>09:00-09:30 | <b>Resistive Switching Materials and Devices for Information Processing</b><br>Kyung Seok Woo <sup>1,2</sup><br><sup>1</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Department of Materials Science and Engineering, UNIST                                                                                                                                                                                               |
| TA1-D-2<br>09:30-09:45         | <b>Li Doped NbO<sub>x</sub> Self-Rectifying Memristors for Crossbar Array Neuromorphic Architectures</b><br>Jeong Hyeon Son and Hong-Sub Lee<br>Department of Materials Science and Engineering, Kyung Hee University                                                                                                                                                                                                                                                     |
| TA1-D-3<br>09:45-10:00         | <b>Two-Stack 2k-Level Crossbar Array based on Alkali-Ion Al:TiO<sub>2</sub> Memristors</b><br>Dae Hee Han and Hong Sub Lee<br>Department of Advanced Materials Engineering, Kyung Hee University                                                                                                                                                                                                                                                                          |
| TA1-D-4<br>10:00-10:15         | <b>Tuning Switching Dynamics in ZnO Transistors with TiO<sub>2</sub> Memristor Gates for Neuromorphic Computing</b><br>Yun Seo Shin and Hong Sub Lee<br>Department of Advanced Materials Engineering, Kyung Hee University                                                                                                                                                                                                                                                |
| TA1-D-5<br>10:15-10:30         | <b>Li-well ZnO Memtransistors Cross-bar Array for Neuromorphic Applications</b><br>Hyun Sik Kim, Ki Hoon Son, and Hong Sub Lee<br>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University                                                                                                                                                                                                                                      |
| TA1-D-6<br>10:30-10:45         | <b>Analysis of Switching Characteristics and Thermal Stability in 2DEG-Based Conductive-Bridge Random Access Memory</b><br>In Su Oh <sup>1,2</sup> , Ju Young Sung <sup>1,2</sup> , Chae Hyun Lee <sup>1,2</sup> , Ye Bin Lim <sup>1,2</sup> , Sang Hyeok Lee <sup>1,2</sup> , Yun Won Song <sup>1,2</sup> , and Sang Woon Lee <sup>1,2</sup><br><sup>1</sup> Department of Energy Systems Research, Ajou University, <sup>2</sup> Department of Physics, Ajou University |

B. Patterning (Lithography & Etch Technology) 분과

O30\_[TB1-B] Patterning (Lithography)

좌장: 정현담 교수(전남대학교), 김명웅 교수(인하대학교)

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| 초청발표<br>TB1-B-1<br>09:00-09:30 | Eco-Friendly Water-Processable Dual-Tone Photoresists Containing Photoreversible Functional Groups for Advanced Lithography<br>Hyun-Jin Kim <sup>1</sup> , Min-Jung Park <sup>1</sup> , Gayoung Kim <sup>2</sup> , Jin-Kyun Lee <sup>2</sup> , and Jae-Hak Choi <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Chungnam National University, <sup>2</sup> Program in Environment and Polymer Engineering, Inha University                                                                                                                                                                                                                                                                 |
| TB1-B-2<br>09:30-09:45         | 이미징 성능 및 Best Focus Shift 완화를 위한 High-NA EUV 마스크용 Bilayer 흡수체 구조 연구<br>이승호 <sup>1,2</sup> , 정동민 <sup>1,2</sup> , 김연수 <sup>1,2</sup> , 이태호 <sup>2</sup> , 안진호 <sup>1,2</sup><br><sup>1</sup> 한양대학교 신소재공학과, <sup>2</sup> 극한스케일·극한물성-이종집적 한계극복 반도체 기술 연구센터                                                                                                                                                                                                                                                                                                                                                                                                                                                                  |
| TB1-B-3<br>09:45-10:00         | Simulation of Extreme Ultraviolet Mask for Defect Inspection and Repair<br>Sang-Kon Kim<br>Hongik University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| TB1-B-4<br>10:00-10:15         | Grain Size에 따른 EUV 펄리클의 기계적 및 광학적 특성 변화<br>김원진 <sup>1,2</sup> , 강영우 <sup>1,2</sup> , 이태호 <sup>1,2</sup> , 박영욱 <sup>2</sup> , 안진호 <sup>1,2</sup><br><sup>1</sup> 한양대학교 신소재공학과, <sup>2</sup> 극한스케일·극한물성-이종집적 한계극복 반도체 기술 연구센터                                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |
| TB1-B-5<br>10:15-10:30         | A Methodology of Emissivity Measurement for Radiatively Complex CNT and Porous-Structured Pellicles<br>Jiho Kim <sup>1</sup> , Youngchan Kim <sup>3</sup> , Hyun Don Kim <sup>3</sup> , Hyeongjoon Lim <sup>3</sup> , Hyuk Jin Kim <sup>1</sup> , Geonhwa Kim <sup>1</sup> , Boknam Chae <sup>1</sup> , Eunjip Choi <sup>3</sup> , and Sangsul Lee <sup>1,2</sup><br><sup>1</sup> Pohang Accelerator Laboratory, POSTECH, <sup>2</sup> Department of Semiconductor Engineering, POSTECH, <sup>3</sup> Department of Physics, University of Seoul                                                                                                                                                                         |
| TB1-B-6<br>10:30-10:45         | Gap-filling Stencil Lithography Utilizing Protective Layer for Precise Patterning of 2D Transition-metal Dichalcogenide Electronics<br>Jaemin Myoung <sup>1,2,3</sup> , Taehyeon Kim <sup>1,2,3</sup> , Seunghun Lee <sup>4</sup> , Jeonghwan Kim <sup>4</sup> , Taesung Kim <sup>5</sup> , and Jihun Mun <sup>1</sup><br><sup>1</sup> Strategic Technology Research Institute, KRISS, <sup>2</sup> SKKU Advanced Institute of Nano Technology, Sungkyunkwan University, <sup>3</sup> Department of Nano Science and Technology, Sungkyunkwan University, <sup>4</sup> Department of Materials Science & Engineering, Hanbat National University, <sup>5</sup> School of Mechanical Engineering, Sungkyunkwan University |

D. Thin Film Process Technology 분과

O31\_[TC1-D] Ferroelectrics I

좌장: 임태용 교수(세종대학교), 박민혁 교수(서울대학교)

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| 초청발표<br>TC1-D-1<br>09:00–09:30 | <b>Advanced Synchrotron-Based X-ray Diffraction Characterization of Ferroelectric HfO<sub>2</sub> for Emerging Memory Applications</b><br>Younghwan Lee <sup>1</sup> and Min Hyuk Park <sup>2</sup><br><sup>1</sup> School of Materials Science and Engineering, Chonnam National University, <sup>2</sup> Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                    |
| TC1-D-2<br>09:30–09:45         | <b>Antiferroelectric Shift of Hf<sub>0.2</sub>Zr<sub>0.8</sub>O<sub>2</sub> Thin Film Capacitors via NbC Low-Work Function Transition Metal Electrodes</b><br>Kwan Hyun Park <sup>1</sup> , Chae Hyun Park <sup>2</sup> , Soo Hyun Kim <sup>2</sup> , and Min Hyuk Park <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Department of Materials Science and Engineering, UNIST                                                                                                                                                                     |
| TC1-D-3<br>09:45–10:00         | <b>A Study on the Role of O<sub>2</sub> Plasma-Controlled TiOx Interfacial Layer for Reliability Enhancement of HZO Ferroelectric Capacitors</b><br>So Yeong Park, Woon San Ko, Hye Ri Hong, Seong Jo Jo, and Ga Won Lee<br>School of Electronics Engineering, Chungnam National University                                                                                                                                                                                                                                                                                                                              |
| TC1-D-4<br>10:00–10:15         | <b>Stable Ferroelectric Properties in 3 nm Hafnium-Zirconium-Oxide Thin Films by Shifting the Composition Window</b><br>Gunho Kim <sup>1</sup> , Hyo-Bae Kim <sup>1</sup> , Wonwoo Kho <sup>2</sup> , Hye Won Cho <sup>1</sup> , Hyung-Seok Lee <sup>1</sup> , Seung-Eon Ahn <sup>3</sup> , and Ji-Hoon Ahn <sup>1</sup><br><sup>1</sup> Department of Materials Science & Chemical Engineering, Hanyang University, <sup>2</sup> Department of IT·Semiconductor Convergence Engineering, Tech University of Korea, <sup>3</sup> Department of Nano & Semiconductor Engineering, Tech University of Korea                |
| TC1-D-5<br>10:15–10:30         | <b>Polarization Characteristics of Nano-Laminated Thick Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> with Al<sub>2</sub>O<sub>3</sub> Interlayer</b><br>Yu-Jeong Kang <sup>1,2</sup> , Kyul Ko <sup>1</sup> , Woo-Young Choi <sup>2</sup> , and Jae-Hoon Han <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Department of Electrical and Electronic Engineering, Yonsei University                                                                                                                                                                                                      |
| TC1-D-6<br>10:30–10:45         | <b>Enhanced Thermal Robustness of Hf<sub>x</sub>Zr<sub>1-x</sub>O<sub>2</sub> through Lanthanum Oxygen Diffusion Interlayer</b><br>Jihoon Choi <sup>1</sup> , KyungSoo Park <sup>2</sup> , HyeonCheol Jeong <sup>1</sup> , SangMyum Lim <sup>1</sup> , TaeSuk Kim <sup>2</sup> , GyuMin Hwang <sup>1</sup> , YeonWoo Choi <sup>1</sup> , JinYeong Lee <sup>1</sup> , YoonSeok Lee <sup>1</sup> , YeJun Park <sup>1</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University |

K. Memory (Design & Process Technology) 분과

O32\_[TD1-K] NAND Flash

좌장: 박종경 교수(서울과학기술대학교), 전종욱 교수(성균관대학교)

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| 초청발표<br>TD1-K-1<br>09:00-09:30 | Evolution of Device Technology for Next Generation VNAND<br>Kibong Moon<br>Flash TD Team, Semiconductor R&D Center, Samsung Electronics Co., Ltd.                                                                                                                                                                                                                                                                              |
| TD1-K-2<br>09:30-09:45         | Implementation of n-Shot STDP Pulse Scheme for Flash Memory Array-Based Low-Power SNN<br>Jaewon Kim <sup>1</sup> , Jangsaeng Kim <sup>1,2</sup> , and Jong-Ho Bae <sup>3</sup><br><sup>1</sup> Department of Electrical and Electronic Engineering, Sogang University, <sup>2</sup> Department of System Semiconductor Engineering, Sogang University, <sup>3</sup> Department of Semiconductor Engineering, Yonsei University |
| TD1-K-3<br>09:45-10:00         | Improved Surrogate Learning of Threshold-Voltage Distribution in 3D NAND Flash Using Ensemble-Driven MLP Optimization<br>Hyeon Seo Yun and Jong Kyung Park<br>Department of Semiconductor Engineering, Seoul National University of Science & Technology                                                                                                                                                                       |
| TD1-K-4<br>10:00-10:15         | Low-Power, Area-Efficient NAND-AND Hybrid Flash MCAM for High-Density In-Memory Search<br>Seoung Youl Lee <sup>1,2</sup> , Sung Yun Woo <sup>3</sup> , and Dongseok Kwon <sup>2</sup><br><sup>1</sup> Department of Electrical and Electronic Engineering, Inha University, <sup>2</sup> Department of Semiconductor Engineering, GIST, <sup>3</sup> School of Electronics Engineering, Kyungpook National University          |
| TD1-K-5<br>10:15-10:30         | 고성능 낸드 플래시 메모리를 위한 iCVD 공정 기반 다결정 실리콘 채널 내 불소 도핑 기술 개발<br>박영근 <sup>1</sup> , 박정익 <sup>2</sup> , 정재중 <sup>1</sup> , 장성진 <sup>3</sup> , 박세준 <sup>4</sup> , 임성갑 <sup>2</sup> , 조병진 <sup>1</sup><br><sup>1</sup> 한국과학기술원 전기 및 전자공학부, <sup>2</sup> 한국과학기술원 생명화학공학과, <sup>3</sup> 나노종합기술원, <sup>4</sup> 삼성전자                                                                                                                         |
| TD1-K-6<br>10:30-10:45         | Analog Compute-In-Memory based on Flash Memory Cells for Hopfield Neural Networks<br>Yoosung Jeon <sup>1,2</sup> and Dongseok Kwon <sup>2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Soongsil University, <sup>2</sup> Department of Semiconductor Engineering, GIST                                                                                                                               |

J. Nano-Science & Technology 분과

O33\_[TE1-J] 공정·계면·재료공학 기반 나노전자

좌장: 김태욱 교수(전북대학교), 조준현 교수(전북대학교)

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| 초청발표<br>TE1-J-1<br>09:00-09:30 | <b>Topological van der Waals Contacts for 2D Materials</b><br>Soheil Ghods <sup>1,2</sup> , Hochan Jang <sup>1,2</sup> , Ji-Yun Moon <sup>2,3,4</sup> , and Jae-Hyun Lee <sup>1,2</sup><br><sup>1</sup> Department of Electrical and Computer Engineering, Sungkyunkwan University, <sup>2</sup> Center for Stacked van der Waals Semiconductors, Sungkyunkwan University, <sup>3</sup> Department of Mechanical Engineering and Materials Science, <sup>4</sup> Institute of Materials Science and Engineering, Washington University                                                                                                                                                                          |
| TE1-J-2<br>09:30-09:45         | <b>Study on the Effects of Formation Temperature of Alkanethiol Self-Assembled Monolayers on their Electrical Properties</b><br>Hyemin Lee <sup>1</sup> , Haeri Kim <sup>2</sup> , Donguk Kim <sup>1</sup> , Jongwoo Nam <sup>1</sup> , Minwoo Song <sup>1</sup> , Hyun Sun Sung <sup>2</sup> , Jaegeun Noh <sup>2</sup> , and Takhee Lee <sup>1</sup><br><sup>1</sup> Department of Physics and Astronomy, Seoul National University, <sup>2</sup> Department of Chemistry, Hanyang University                                                                                                                                                                                                                 |
| TE1-J-3<br>09:45-10:00         | <b>Passivation of Indium Selenide: Suppressing Polymer-Induced Doping through Redox Activation</b><br>Jieun Jo <sup>1</sup> , Chan Kwon <sup>1</sup> , Hyeon Jung Park <sup>1</sup> , Chaewon Lee <sup>1</sup> , Haneul Kim <sup>1</sup> , Taehoon Kim <sup>1</sup> , Ga Hyun Cho <sup>1</sup> , Seungho Bang <sup>1</sup> , Dae Young Park <sup>2</sup> , and Mun Seok Jeong <sup>1</sup><br><sup>1</sup> Hanyang University, <sup>2</sup> Sungkyunkwan University                                                                                                                                                                                                                                             |
| TE1-J-4<br>10:00-10:15         | <b>Phase-Engineered Amorphous-Tellurium Trioxide: An Emerging p-Type Channel Material</b><br>Seungho Bang <sup>1</sup> , Chaewon Lee <sup>1</sup> , Deogkyu Choi <sup>1</sup> , Dae Young Park <sup>1</sup> , Dong Hyeon Kim <sup>1</sup> , Dohyeon Lee <sup>1</sup> , Dong-Joon Yi <sup>1,2</sup> , Jungeun Song <sup>3</sup> , Seok Joon Yun <sup>4</sup> , Dong-Wook Kim <sup>3</sup> , and Mun Seok Jeong <sup>1</sup><br><sup>1</sup> Department of Physics, Hanyang University, <sup>2</sup> Department of Electronics Engineering, Hanyang University, <sup>3</sup> Department of Physics, Ewha Womans University, <sup>4</sup> Department of Semiconductor Physics and Engineering, University of Ulsan |
| TE1-J-5<br>10:15-10:30         | <b>Uniform Sub-60 mV/dec Super-Steep Subthreshold Swing Achieved in Chip-Scale Graphene/IGZO Cold Source FET Array</b><br>Seyoung Oh <sup>1,2</sup> , Jonghun Jeon <sup>1</sup> , Jaeyoung Yoon <sup>1</sup> , and Byungjin Cho <sup>1,2</sup><br><sup>1</sup> Department of Advanced Materials Engineering, Chungbuk National University, <sup>2</sup> Department of Urban, Energy, and Environmental Engineering, Chungbuk National University                                                                                                                                                                                                                                                                |
| TE1-J-6<br>10:30-10:45         | <b>Capacitance-Voltage Characterization as a Diagnostic Tool for Dielectric Selection in VCMA Devices</b><br>Ji-Hyeon Yun <sup>1,2</sup> , Kyumin Sim <sup>3</sup> , Yeon-Su Park <sup>4</sup> , In-Kook Hwang <sup>1</sup> , Sang Ho Lim <sup>2</sup> , Byong-Guk Park <sup>4</sup> , Hamin Park <sup>3</sup> , and Seung-heon Chris Baek <sup>1</sup><br><sup>1</sup> Center for Semiconductor Technology, KIST, <sup>2</sup> Department of Materials Science and Engineering, Korea University, <sup>3</sup> Department of Electronic Engineering, Kwangwoon University, <sup>4</sup> Department of Materials Science and Engineering, KAIST                                                                 |

K. Memory (Design & Process Technology) 분과

O34\_[TF1-K] Ferroelectric

좌장: 심원보 교수(서울과학기술대학교), 구민석 교수(서울시립대학교)

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| TF1-K-1<br>09:00–09:15 | <b>Memory Window Expansion in <math>\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2</math> MFS FeFETs Enabled by <math>\text{ZrO}_2</math> Interlayer</b><br>Eunjin Kim and Jiyong Woo<br>School of Electronic and Electrical Engineering, Kyungpook National University                                                                                                                                                                                                                                                                                                                                                                                                                                         |
| TF1-K-2<br>09:15–09:30 | <b>Domain-Engineered <math>\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2</math> Ferroelectric Tunnel Junction with Oxygen Vacancy Suppression for Enhanced Endurance</b><br>Hyojin Yang, Seongho Park, Minwoo Kim, Dae Hwan Kim, Sung-Jin Choi, and Yoon Jung Lee<br>School of Electrical Engineering, Kookmin University                                                                                                                                                                                                                                                                                                                                                                                      |
| TF1-K-3<br>09:30–09:45 | <b>AI 메모리 구현을 위한 고성능 강유전체 소자 기술 특허 출원 동향</b><br>한상국, 정재훈, 김희태<br>지식재산청 반도체심사추진단                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                           |
| TF1-K-4<br>09:45–10:00 | <b>Effect of Electrode Work-Function Asymmetry on Built-in Fields in Ferroelectric ALD-HZO Thin Films</b><br>Hoyoung Kim, Gwanghyeon Jang, Seongbin Lee, Hyeonhong Min, Yechan Kim, Soohyeok Park, Geonhwi Kim, Yejin Han, Han-Don Um, and Si Joon Kim<br>Kangwon National University                                                                                                                                                                                                                                                                                                                                                                                                                     |
| TF1-K-5<br>10:00–10:15 | <b>Dual-Gate HZO Ferroelectric Field-Effect Transistor with Gd-Doped <math>\text{HfO}_2</math> Top-Gate Insulator</b><br>Jin Yeong Lee <sup>1</sup> , KyungSoo Park <sup>2</sup> , HyeonCheol Jeong <sup>1</sup> , SangMyum Lim <sup>1</sup> , TaeSuk Kim <sup>2</sup> , GyuMin Hwang <sup>1</sup> , YeonWoo Choi <sup>1</sup> , Jihoon Choi <sup>1</sup> , YoonSeok Lee <sup>1</sup> , YeJun Park <sup>1</sup> , Hanbyul Kim <sup>3</sup> , Yongjoo Park <sup>3</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Semiconductor Engineering, Hanyang University, <sup>2</sup> Department of Materials Science and Engineering, Hanyang University, <sup>3</sup> SK Trichem Co., Ltd. |
| TF1-K-6<br>10:15–10:30 | <b>HfLaO 박막을 이용한 하프니아 기반 FeFET의 Disturbance 특성 완화</b><br>김승훈 <sup>1</sup> , 유찬미 <sup>2</sup> , 박영근 <sup>1</sup> , 정원묵 <sup>1</sup> , 이동규 <sup>2</sup> , 조병진 <sup>1,2</sup><br><sup>1</sup> 한국과학기술원 전기 및 전자공학부, <sup>2</sup> 한국과학기술원 반도체공학대학원                                                                                                                                                                                                                                                                                                                                                                                                                                                              |
| TF1-K-7<br>10:30–10:45 | <b>Impact of Ferroelectric/Insulator Interface Traps on the Memory Characteristics of Metal-Ferroelectric-Insulator-Semiconductor FeFET</b><br>Seok-Hoon Jeong <sup>1</sup> , Ha-Neul Lee <sup>2</sup> , Sujong Kim <sup>2</sup> , Eunhong Kim <sup>1</sup> , Hwanjin Kim <sup>2</sup> , Haesung Kim <sup>3</sup> , Hyojin Yang <sup>2</sup> , and Jong-Ho Bae <sup>1</sup><br><sup>1</sup> Department of System Semiconductor Engineering, Yonsei University, <sup>2</sup> School of Electrical Engineering, Kookmin University, <sup>3</sup> Birck Nanotechnology Center, Purdue University                                                                                                             |

C. Material Growth & Characterization 분과

O35\_[TG1-C] Ferroelectricity and Complex Oxides

좌장: 서준민 교수(서울대학교), 엄기태 교수(가천대학교)

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| 초청발표<br>TG1-C-1<br>09:00-09:30 | Optical Spectroscopic Characterization of High $\kappa$ and Ferroelectric Oxides<br>Changhee Sohn<br>Department of Physics, UNIST                                                                                                                                                                                                                                                                     |
| TG1-C-2<br>09:30-09:45         | Kinetic Control of Cation Stoichiometry in Infinite-Layer Cuprate by Pulsed Laser Deposition<br>Jaewoo Lee <sup>1,2</sup> , Jiwon Lee <sup>1,2</sup> , Hyungmok Lee <sup>1,2</sup> , and Woo Jin Kim <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Pusan National University, <sup>2</sup> Institute of Materials Technology, Pusan National University             |
| TG1-C-3<br>09:45-10:00         | Epitaxial Stabilization of van der Waals-Layered $\alpha$ -MoO <sub>3</sub> Thin Films<br>Hyeondong Do <sup>1,2</sup> , Donghoon Shin <sup>1</sup> , and Woo Jin Kim <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Pusan National University, <sup>2</sup> Institute of Materials Technology, Pusan National University                                             |
| TG1-C-4<br>10:00-10:15         | In-situ TEM Study on Structural and Defect Responses of Hf1/2Zr1/2O <sub>2</sub> under Heating and Biasing Conditions<br>Jeehun Jeong <sup>1</sup> , Heechan Bang <sup>2</sup> , Minchan Seong <sup>1</sup> , Keeyong Lee <sup>1</sup> , Chan-Ho Yang <sup>2</sup> , and Sang Ho Oh <sup>1</sup><br><sup>1</sup> Department of Energy Engineering, KENTECH, <sup>2</sup> Department of Physics, KAIST |
| 초청발표<br>TG1-C-5<br>10:15-10:45 | Sub-Unit-Cell-Segmented Ferroelectricity in Brownmillerite Oxides by Phonon Decoupling<br>Si-Young Choi <sup>1,2,3</sup><br><sup>1</sup> Department of Materials Science and Engineering, POSTECH, <sup>2</sup> Department of Semiconductor Engineering, POSTECH, <sup>3</sup> Center for Van der Waals Quantum Solids, IBS                                                                           |

G. Device & Process Modeling, Simulation and Reliability 분과

O36\_[TH1-G] Device & Process Modeling, Simulation and Reliability IV

좌장: 이재현 교수(부산대학교), 홍성민 교수(GIST)

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| 초청발표<br>TH1-G-1<br>09:00-09:30 | Quantum Simulations for Advanced Logic Devices and Interconnects<br>Yeonghun Lee<br>Department of Electronics Engineering, Incheon National University                                                                                                                                                                                                                                                                                                                                                                                                                        |
| TH1-G-2<br>09:30-09:45         | Component Based Quantification of Trap Formation in MOS Devices under Total Ionized Dose Stress<br>Jung Woo Moon <sup>1,2</sup> , Jemin Kim <sup>1</sup> , Kwanhun Lee <sup>1</sup> , Byungjin Ma <sup>1</sup> , and Youngbin Lee <sup>1</sup><br><sup>1</sup> Reliability Technology Research Center, KETI, <sup>2</sup> Department of Chemical and Biomolecular Engineering, Yonsei University                                                                                                                                                                              |
| TH1-G-3<br>09:45-10:00         | Temperature-Dependent Characterization and SPICE-Based Compact Modeling of a Dual-Gate Feedback Field-Effect Transistors<br>Jaewon-Lee and Min-Woo Kwon<br>Department of Electronic Engineering, Seoul National University of Science & Technology                                                                                                                                                                                                                                                                                                                            |
| TH1-G-4<br>10:00-10:15         | Introduction to Hybrid ESD Model Using HSPICE and Verilog-A<br>Dongseok Han, Seungchan Yun, Minsu Choi, Bongsik Sihn, Inho Hwang, Gyeongsun Park, Suk Yun, and Il-sup Jin<br>Future Technology Group, SK Keyfoundry Co., Ltd                                                                                                                                                                                                                                                                                                                                                  |
| TH1-G-5<br>10:15-10:30         | Charge Pumping-Based Characterization of Interface Trap Density and Reliability of FeFETs for Cryogenic Operation<br>Sangmyun Lim <sup>1</sup> , Kyungsoo Park <sup>2</sup> , Sangkuk Han <sup>2</sup> , HyeonCheol Jeong <sup>1</sup> , Jihoon Choi <sup>1</sup> , Taesuk Kim <sup>2</sup> , Haesoo Jang <sup>1</sup> , Jaewon Chung <sup>1</sup> , Wonjae Choi <sup>1</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University |
| TH1-G-6<br>10:30-10:45         | Reliability Comparison of BJTs with Different Emitter Areas under Electrical Stress Conditions<br>Ju-Han Lee, Ju-Yong Shin, Yu-Bin Kim, and Hi-Deok Lee<br>Department of Electronics Engineering, Chungnam National University                                                                                                                                                                                                                                                                                                                                                |

F. Silicon and Group–IV Devices and Integration Technology 분과

O37\_[TI1–F] Ferroelectric Device Technology

좌장: 이병훈 교수(POSTECH), 황현준 교수(목포대학교)

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| TI1–F–1<br>09:00–09:15 | <b>Fatigue and Recovery Mechanism of HfZrO<sub>2</sub>/Ge MF(I)S Capacitors under Low Operating Voltage</b><br>Jai–Youn Jeong <sup>1,2</sup> , Kyul Ko <sup>1</sup> , Changhwan Shin <sup>2</sup> , and Jae–Hoon Han <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Device and Circuit Laboratory, Korea University                                                                                                                                                         |
| TI1–F–2<br>09:15–09:30 | <b>Oxygen Vacancy Engineering of ITO Interfacial Layer for Enhanced Reliability in Ferroelectric Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Capacitors</b><br>Haevin Choi and Changhwan Shin<br>School of Electrical Engineering, College of Engineering, Korea University                                                                                                                                                                                                                               |
| TI1–F–3<br>09:30–09:45 | <b>Improved Ferroelectricity in W/Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>/W Capacitor With WO<sub>x</sub> Interlayer</b><br>Juneyup Cho and Changhwan Shin<br>School of Electrical Engineering, College of Engineering, Korea University                                                                                                                                                                                                                                                              |
| TI1–F–4<br>09:45–10:00 | <b>Capacitance Wake up in Morphotropic Phase Boundary Enabled by Bilayer Hf<sub>x</sub>Zr<sub>1–x</sub>O<sub>2</sub> Capacitors</b><br>Junseok Kim and Changhwan Shin<br>School of Electrical Engineering, College of Engineering, Korea University                                                                                                                                                                                                                                                         |
| TI1–F–5<br>10:00–10:15 | <b>The Strategy to Enhance “On” State Current of Ferroelectric Tunnel Junction Satisfying Self–Rectifying Property</b><br>Hui Seong Shin, Sehee Kim, and Changhwan Shin<br>School of Electrical Engineering, College of Engineering, Korea University                                                                                                                                                                                                                                                       |
| TI1–F–6<br>10:15–10:30 | <b>Hf–Free Ferroelectric Capacitor with ZrO<sub>2</sub>/Oxide Semiconductor for Low–Power Non–Volatile Operation</b><br>Changwoo Han <sup>1</sup> , Hyeonjung Park <sup>2</sup> , Inhyeok Choi <sup>3</sup> , and Changhwan Shin <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, College of Engineering, Korea University, <sup>2</sup> Department of Electrical and Computer Engineering, Sungkyunkwan University, <sup>3</sup> Department of Physics, College of Science, Korea University |
| TI1–F–7<br>10:30–10:45 | <b>The Role of IGZO Interlayer as an Oxygen Reservoir Layer for Enhanced Ferroelectric Capacitor Endurance</b><br>Donghyeon Kim and Changhwan Shin<br>School of Electrical Engineering, College of Engineering, Korea University                                                                                                                                                                                                                                                                            |

I. MEMS & Sensors Systems 분과

O38\_[TJ1-I] MEMS and Sensor System II

좌장: 상민규 교수(가천대학교), 유호천 교수(한양대학교)

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| TJ1-I-1<br>09:00-09:15         | <b>Wireless Multi-Sensing System for Real-Time Battery Safety Management</b><br>Junghoon Lee <sup>1</sup> , Hyejun Kim <sup>1</sup> , Seongu Kim <sup>1</sup> , Yeonjae Yang <sup>1</sup> , Jinsu Park <sup>1</sup> , Sangkyu Lee <sup>2</sup> , and Jeonghyun Kim <sup>1</sup><br><sup>1</sup> Department of Electronic Convergence Engineering, Kwangwoon University, <sup>2</sup> Department of Energy Science & Engineering, Kunsan National University                 |
| TJ1-I-2<br>09:15-09:30         | <b>Development of a Ferroelectric Ga-HfO<sub>2</sub> Thin Film via Co-Sputtering for Vibration and Temperature Sensor</b><br>Minsoo Kim <sup>1</sup> , Junmo Kim <sup>1</sup> , Minje Lee <sup>1</sup> , Donghyeon Bae <sup>1</sup> , and Hyeongtak Seo <sup>1,2</sup><br><sup>1</sup> Department of Energy Systems Research, Ajou University, <sup>2</sup> Department of Materials Science and Engineering, Ajou University                                                |
| TJ1-I-3<br>09:30-09:45         | <b>Solution-Processable and Photo-Patternable Electronic Materials for Transient Electronics</b><br>Sungkeun Han <sup>1</sup> and Suk-Won Hwang <sup>1,2,3</sup><br><sup>1</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University, <sup>2</sup> Center for Biomaterials, Biomedical Research Institute, KIST, <sup>3</sup> Department of Integrative Energy Engineering, Korea University                                                     |
| TJ1-I-4<br>09:45-10:00         | <b>Magneto-Encephaloscope: A Minimal-Invasive and Magnetically Controllable Neural Interface</b><br>Jeongmin Yoo <sup>1</sup> , Sang Hoon Park <sup>2</sup> , Ji Won Lee <sup>2</sup> , Gyuri Shin <sup>1</sup> , Yeonhee Heo <sup>1</sup> , Ki Jun Yu <sup>2</sup> , and Yoonseok Park <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Kyung Hee University, <sup>2</sup> School of Electrical and Electronic Engineering, Yonsei University |
| TJ1-I-5<br>10:00-10:15         | <b>Wearable Ring Sensor for Enhanced Accuracy and Comfort in Blood Pressure Monitoring</b><br>Seongu Kim, Lurong Yang, Hyejun Kim, Junghoon Lee, Yeonjae Yang, Jinsu Park, and Jeonghyun Kim<br>Department of Electronic Convergence Engineering, Kwangwoon University                                                                                                                                                                                                      |
| 초청발표<br>TJ1-I-6<br>10:15-10:45 | <b>Acoustic Impedance Mismatching for Ultrasound-driven Triboelectric Generator</b><br>Hong-Joon Yoon <sup>1,2</sup><br><sup>1</sup> Department of Electronic Engineering, Gachon University, <sup>2</sup> Department of Semiconductor Engineering, Gachon University                                                                                                                                                                                                       |

D. Thin Film Process Technology 분과

O39\_[TC2-D] Ferroelectrics II

좌장: 이홍섭 교수(경희대학교), 유찬영 교수(홍익대학교)

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| TC2-D-1<br>10:55-11:10 | <b>Enhancement of Polarization Characteristics in HZO-Based FeCAP Using a Dual Insertion Layer Structure</b><br>Dongchan Seo <sup>1</sup> , Taehyung Kim <sup>1</sup> , Kiwon Yoon <sup>2</sup> , and Jinsub Park <sup>1,2</sup><br><sup>1</sup> Department of Electronic Engineering, Hanyang University, <sup>2</sup> Department of AI Semiconductor Engineering, Hanyang University                                                                                                                                                                                                                                                                                              |
| TC2-D-2<br>11:10-11:25 | <b>Enhanced Ferroelectricity in Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Thin Films via Ar Plasma Surface Treatment</b><br>Jeonggwang Lee <sup>1</sup> , Jaewook Lee <sup>1</sup> , Hyun Woo Jeong <sup>1</sup> , Hyojun Choi <sup>1</sup> , Young Yong Kim <sup>2</sup> , and Min Hyuk Park <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Pohang Accelerator Laboratory, POSTECH                                                                                                                                                                                                                      |
| TC2-D-3<br>11:25-11:40 | <b>Nanolaminate-Driven Ferroelectric Enhancement in Ultrathin (Hf,Zr)O<sub>2</sub> with Quantitative Strain Analysis</b><br>Jaewook Lee, Hyun Woo Jeong, Yong Hyeon Cho, and Min Hyuk Park<br>Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                                                                                                                                                                                            |
| TC2-D-4<br>11:40-11:55 | <b>Lowering Effective Dielectric Constant of Ferroelectric Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Film with an Ultra-Thin Al<sub>2</sub>O<sub>3</sub> Intermediate Layer</b><br>Jinyoung Park <sup>1</sup> , Hyunjae Park <sup>2</sup> , Hyunmin Kwun <sup>2</sup> , Eunseok Hyun <sup>2</sup> , Jaehyeong Jo <sup>2</sup> , Jiwan Kim <sup>2</sup> , Wonho Song <sup>3</sup> , Junhyung Kim <sup>4</sup> , and Kibog Park <sup>1,5</sup><br><sup>1</sup> Semiconductor R&D Center, Samsung Electronics Co., Ltd., <sup>2</sup> Department of Physics, UNIST, <sup>3</sup> LG Display Co., Ltd., <sup>4</sup> ETRI, <sup>5</sup> Department of Electrical Engineering, UNIST |
| TC2-D-5<br>11:55-12:10 | <b>Role of Nitrogen Content in Determining the Reliability of Symmetric MoN<sub>x</sub>-Based Ferroelectric Capacitors</b><br>Hyojun Choi, Ju Yong Park, Jaewook Lee, Hyun Woo Jeong, Dong In Han, Sun Young Lee, Kun Yang, and Min Hyuk Park<br>Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                                                                                                                                         |
| TC2-D-6<br>12:10-12:25 | <b>In Situ Analysis of Wake-Up Induced Phase Transition and In-Plane Strain Modulation in Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Thin Films via Grazing Incidence Synchrotron X-Ray Diffraction</b><br>Hyun Woo Jeong <sup>1</sup> , Younghwan Lee <sup>2</sup> , and Min Hyuk Park <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> School of Materials Science and Engineering, Chonnam National University                                                                                                                                                                                           |
| TC2-D-7<br>12:25-12:40 | <b>잔류 분극 구동 기반 IGZO FeTFT의 계면 트랩 정량화 연구</b><br>조성조, 박소영, 고운산, 홍혜리, 이가원<br>충남대학교 전자공학과                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                               |

E. Compound Semiconductors 분과

O40\_[TD3-E] Optical and Other Device Technologies

좌장: 허준석 교수(아주대학교), 황완식 교수(한국항공대학교)

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| TD3-E-1<br>10:55-11:10 | <b>InGaAs/InP Phototransistor Heterogeneously Integrated on Si Photonics Platform</b><br>Kyunghwan Kim <sup>1</sup> , Yuna Lee <sup>1</sup> , Sanghyeon Kim <sup>2,3</sup> , and Jae-Hoon Han <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> School of Electrical Engineering, KAIST, <sup>3</sup> Graduate School of Semiconductor Technology, KAIST                                                                                                                                                                                                                                                                                                                                                                                                                                                  |
| TD3-E-2<br>11:10-11:25 | <b>III-V/Ins./Si Waveguide-integrated High-Speed Mach-Zehnder Optical Modulator for Co-packaged Optics</b><br>Donggil Kang <sup>1</sup> , Shin Hyung Lee <sup>1</sup> , Jae-Hoon Han <sup>2</sup> , Jongmin Kim <sup>3</sup> , Seok-Geun Ahn <sup>4</sup> , Minhyuk Jung <sup>4</sup> , Hyun-Chul Jung <sup>4</sup> , and SangHyeon Kim <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, KAIST, <sup>2</sup> KIST, <sup>3</sup> KANC, <sup>4</sup> Samsung Electronics Co., Ltd.                                                                                                                                                                                                                                                                                                                                         |
| TD3-E-3<br>11:25-11:40 | <b>Monolithic Growth of High-Quality InSb on On-Axis (001) Silicon for Mid-Wavelength Infrared Photodetector Applications</b><br>Kenneth Duque <sup>1,2</sup> , Tsimafei Laryn <sup>1,2</sup> , Seungwan Woo <sup>1,3,4</sup> , Eunkyo Ju <sup>1,5</sup> , Eungbeom Yeon <sup>1,5</sup> , Yeonhwa Kim <sup>1,5</sup> , In-Hwan Lee <sup>5</sup> , Won Jun Choi <sup>1</sup> , and Daehwan Jung <sup>1,2</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Division of Nanoscience and Technology, KIST School at University of Science and Technology, <sup>3</sup> Department of Materials Science and Engineering, Seoul National University, <sup>4</sup> Research Institute of Advanced Materials, Seoul National University, <sup>5</sup> Department of Materials Science and Engineering, Korea University |
| TD3-E-4<br>11:40-11:55 | <b>Monolithically Integrated InGaAs/InAsSb Ultra-Broadband Infrared Detector Covering 0.8 - 5.5 Micron Wavelengths</b><br>Seungwan Woo <sup>1,2</sup> , Eungbeom Yeon <sup>1</sup> , Ho Won Jang <sup>2</sup> , Daehwan Jung <sup>1</sup> , and Won Jun Choi <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                                                                                                                                                                                                 |
| TD3-E-5<br>11:55-12:10 | <b>중적외선 검출을 위한 유연 기판 위 T2SL 광검출기 Array 제작</b><br>한재훈<br>한국과학기술연구원 양자기술연구단                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |
| TD3-E-6<br>12:10-12:25 | <b>Improved Specific Contact Resistivity in Amorphous IGZO via Sub-Nanometer SiO<sub>2</sub> Interlayer Engineering</b><br>So Young Lim <sup>1</sup> , Taewon Hwang <sup>1</sup> , Sangwoo Lee <sup>2</sup> , and Jin-Seong Park <sup>1</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Tokyo Electron Korea Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                                                |
| TD3-E-7<br>12:25-12:40 | <b>Al-Doped NiO/<math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> P-N Heterojunction Diodes for Enhanced Electrical and Thermal Characteristics</b><br>Ho Jung Jeon <sup>1,2,3</sup> and You Seung Rim <sup>1,2,3</sup><br><sup>1</sup> Department of Semiconductor Systems Engineering, Sejong University, <sup>2</sup> Department of Convergence Engineering for Intelligent Drone, Sejong University, <sup>3</sup> Institute of Semiconductor and System IC, Sejong University                                                                                                                                                                                                                                                                                                                                                         |

J. Nano-Science & Technology 분과

O41\_[TE2-J] 광전자·포토닉 디바이스 및 센서

좌장: 이철호 교수(서울대학교), 이재현 교수(성균관대학교)

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| 초청발표<br>TE2-J-1<br>10:55-11:25 | <b>Interfacial Engineering in Layered Magnetic Semiconductor CrSBr</b><br>Junhyeon Jo<br>Division of Advanced Materials Engineering, Jeonbuk National University                                                                                                                                                                                                                                                                                                                                                                        |
| TE2-J-2<br>11:25-11:40         | <b>Metal-Silicon-Metal Hot-Carrier Avalanche Photodetector for High-Responsivity SWIR Detection</b><br>Ji-Hwan Son <sup>1,2</sup> , Eui-Hyoun Ryu <sup>1</sup> , Sunghyun Hwang <sup>1</sup> , Nayeon Kim <sup>1</sup> , Nayoung Kim <sup>1</sup> , Myung-Jae Lee <sup>3</sup> , Jae-Hoon Han <sup>1</sup> , and In-Ho Lee <sup>1</sup><br>Center for Quantum Technology, KIST, <sup>2</sup> Department of Micro/Nano Systems, Korea University,<br><sup>3</sup> Department of Electrical and Electronic Engineering, Yonsei University |
| TE2-J-3<br>11:40-11:55         | <b>Focused-Beam-Induced Asymmetric Guided-Mode Resonance for Compact Optical Sensors</b><br>Yeong Hwan Ko<br>Kongju National University                                                                                                                                                                                                                                                                                                                                                                                                 |
| TE2-J-4<br>11:55-12:10         | <b>A Transfer-Free Solution-Processed MoS<sub>2</sub> Based mmWave Switches with <math>f_{co} \sim 94</math> THz for Radiofrequency Circuit Application</b><br>Changwoo Pyo <sup>1</sup> , Sungmoon Park <sup>1</sup> , and Myungsoo Kim <sup>1,2</sup><br><sup>1</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Department of Electrical Engineering, UNIST                                                                                                                             |
| TE2-J-5<br>12:10-12:25         | <b>Enabling Frequency-Agile Reconfigurable X-Band Filters with VO<sub>x</sub>-Based Non-Volatile RF Switches</b><br>Dabin Seo <sup>1</sup> , Dahyeon Kim <sup>2</sup> , and Myungsoo Kim <sup>1,2</sup><br><sup>1</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Department of Electrical and Computer Engineering, UNIST                                                                                                                                                                |
| TE2-J-6<br>12:25-12:40         | <b>A Flexible and Thermally Stable Polymer-Based Analogue Switch for Millimeter-Wave Systems</b><br>Sungmoon Park <sup>1</sup> , Changwoo Pyo <sup>1</sup> , Ji Ho Yu <sup>2</sup> , Min Ju Kim <sup>2</sup> , and Myungsoo Kim <sup>1</sup><br><sup>1</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Department of Foundry Engineering, Dankook University                                                                                                                              |

K. Memory (Design & Process Technology) 분과

O42\_[TF2-K] DRAM

좌장: 정두석 교수(한양대학교), 전종욱 교수(성균관대학교)

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| 초청발표<br>TF2-K-1<br>10:55-11:25 | Scaling Challenges and Emerging Solutions for DRAM Cell Transistors Beyond Sub 10 nm Node<br>Seol-Min Yi, Seon Soon Kim, Young-man Cho, and Seon Yong Cha<br>R&D, SK hynix Inc.                                                                                                                                                                                                                                                                                                                                                    |
| TF2-K-2<br>11:25-11:40         | Surrounding Poly-Si Capacitor-Implemented 2T DRAM Cell for Retention Improvement and Coupling Effect Suppression<br>Seonghwan Kong and Wonbo Shim<br>Department of Electrical and Information Engineering, Seoul National University of Science & Technology                                                                                                                                                                                                                                                                       |
| TF2-K-3<br>11:40-11:55         | Optimizing Novel 3D-Stackable 2T0C DRAM Cell Design through TCAD Simulation and Its Experimental Verification<br>Yongwoo Ryu <sup>2</sup> , Gyuheon Bae <sup>2</sup> , Youngjoon Lee <sup>3</sup> , Dae Hwan Kang <sup>1,2</sup> , and Changwook Jeong <sup>3</sup><br><sup>1</sup> Department of Semiconductor Engineering, POSTECH, <sup>2</sup> Graduate School of Semiconductor Technology, POSTECH, <sup>3</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST                                    |
| TF2-K-4<br>11:55-12:10         | A Split-Gate 2T0C Gain Cell Suppressing Cell-Level and Array-Level Issues<br>Jeong-Min Lee <sup>1</sup> , Seung-Yoon Lee <sup>2</sup> , Seong-Jun Byun <sup>1</sup> , and Joon-Kyu Han <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Department of Electronic Engineering, Sogang University                                                                                                                                                               |
| TF2-K-5<br>12:10-12:25         | Investigation of Low-Frequency Noise Characteristics in Charge-Trap-Based DRAM Devices<br>Hyokyung Kim <sup>1</sup> , Hyeongyu Kim <sup>1</sup> , Yoojin Seol <sup>1</sup> , Jeongmin Son <sup>1</sup> , and Kihyun Kim <sup>1,2</sup><br><sup>1</sup> Department of Electronics and Information Engineering, Jeonbuk National University, <sup>2</sup> Division of Electronic Engineering, Jeonbuk National University                                                                                                            |
| TF2-K-6<br>12:25-12:40         | TCAD-SPICE 혼합모드 기반 소자-특성 반영 DRAM 센스앰프 기본 회로 동작 특성 평가<br>박제원 <sup>1</sup> , 김건 <sup>1</sup> , 김동영 <sup>1</sup> , 김수연 <sup>1</sup> , 김신욱 <sup>1</sup> , 강륜 <sup>1</sup> , 김소원 <sup>1</sup> , 임채혁 <sup>1</sup> , 윤정현 <sup>1</sup> , 서현아 <sup>1</sup> , 이혜린 <sup>1</sup> , 이주원 <sup>1</sup> , 최우진 <sup>2</sup> , 김어진 <sup>2</sup> , 정민우 <sup>2</sup> , 이명진 <sup>2</sup><br><sup>1</sup> 전남대학교 지능전자컴퓨터공학과, <sup>2</sup> 전남대학교 전자컴퓨터공학부                                                                                                  |
| TF2-K-7<br>12:40-12:55         | Memristor-Based Artificial Sensory Nervous System for Neuro-Inspired Robotics<br>See-On Park <sup>1</sup> , Hakcheon Jeong <sup>2</sup> , Seokho Seo <sup>2</sup> , Youna Kwon <sup>3</sup> , Jongwon Lee <sup>4</sup> , and Shinhyun Choi <sup>1,2</sup><br><sup>1</sup> Information and Electronics Research Institute, KAIST, <sup>2</sup> School of Electrical Engineering, KAIST, <sup>3</sup> Nano Convergence Technology Division, NNFC, <sup>4</sup> Department of Semiconductor Convergence, Chungnam National University |

C. Material Growth & Characterization 분과

O43\_[TG2-C] BEOL & Semiconductor Integration Technologies

좌장: 최시영 교수(POSTECH), 송승욱 교수(성균관대학교)

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| 초청발표<br>TG2-C-1<br>10:55-11:25 | <b>BEOL-Compatible Monolithic Integration of Property-Tunable Complex Oxide Single Crystals on Si for Advancing the More-than-Moore Paradigm</b><br>Seung-Hyub Baek<br>Electronic and Hybrid Materials Research Center, KIST                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                         |
| TG2-C-2<br>11:25-11:40         | <b>Additive Manufacturing and Densification of SiC-Based Components for Semiconductor Processing Equipment</b><br>Youngsuk Jung, Ji-Won Oh, and Shinhu Cho<br>MADDE Inc.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| TG2-C-3<br>11:40-11:55         | <b>Record-low Threading Dislocation Density of GaSb on Si Buffer Template via Optimized Multiple Defect Filter Layers</b><br>Eungbeom Yeon <sup>1,2</sup> , Seungwan Woo <sup>1</sup> , In-Hwan Lee <sup>2</sup> , Daehwan Jung <sup>1</sup> , and Won Jun Choi <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Department of Materials Science and Engineering, Korea University                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| TG2-C-4<br>11:55-12:10         | <b>Thermal Atomic Layer Deposition of TiN Using Metal Organic Precursors with N<sub>2</sub>H<sub>4</sub> Reactant</b><br>최윤서, 박혜원, 이한보람<br>인천대학교 신소재공학과                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |
| TG2-C-5<br>12:10-12:25         | <b>Tunable Dielectric Trap Engineering of SiN<sub>x</sub> for Operating Voltage Modulation in Charge Trap Flash Memory</b><br>Hanyeol Ahn <sup>1</sup> , Minseon Gu <sup>1</sup> , Hyun Don Kim <sup>1,2</sup> , Seungchul Choi <sup>1</sup> , Hyun Su Park <sup>1</sup> , Sangwoo Nam <sup>1,2</sup> , Kyu-Myung Lee <sup>3</sup> , Yongsup Park <sup>3</sup> , Jinwoo Byun <sup>5</sup> , Gukhyon Yon <sup>5</sup> , E.J. Choi <sup>1</sup> , Young Jun Chang <sup>1,4</sup> , and Moonsup Han <sup>1</sup><br><sup>1</sup> Department of Physics, University of Seoul, <sup>2</sup> Department of Smart Cities, University of Seoul, <sup>3</sup> Department of Physics, Kyung Hee University, <sup>4</sup> Department of Intelligent Semiconductor, University of Seoul, <sup>5</sup> Advanced Process Development Team, Semiconductor R&D Center, Samsung Electronics Co., Ltd. |
| TG2-C-6<br>12:25-12:40         | <b>Epitaxial Growth of 775 nm Al<sub>0.1</sub>Ga<sub>0.9</sub>As and In<sub>0.1</sub>Al<sub>0.2</sub>Ga<sub>0.7</sub>As Quantum Well Laser Diodes for Quantum Photonic Applications</b><br>Tsimafei Laryn <sup>1,2</sup> , Yeonhwa Kim <sup>1,3</sup> , Kenneth Duque <sup>1,2</sup> , Won Jun Choi <sup>1</sup> , and Daehwan Jung <sup>1,2</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Division of Nanoscience and Technology, KIST School at University of Science and Technology, <sup>3</sup> Department of Materials Science and Engineering, Korea University                                                                                                                                                                                                                                                                                     |

T. AI 분과

O44\_[TH2-T] Artificial Intelligence I

좌장: 김병수 센터장(KETI), 이재학 팀장(KETI)

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| 초청발표<br>TH2-T-1<br>10:55-11:25 | Development Direction of Server PIM Platform for Large Language Models<br>Kyu Hyun Choi and Jae Hyung Ko<br>SoC Platform Research Center, KETI                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| TH2-T-2<br>11:25-11:40         | Real-Time Prediction of 3D-to-2D Surface Transition during GaN Epitaxial Growth Using an In Situ RHEED-Based Transformer Model<br>Jun Suk Chang, Hyeong Yeon Lee, and Hong Kyun Noh<br>AI Manufacturing Division, IVWorks Co., Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                        |
| TH2-T-3<br>11:40-11:55         | Timestep-wise Token Merging for Efficient Spiking Transformer<br>Minyeong An and Jongsun Park<br>Department of Electrical Engineering, Korea University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| TH2-T-4<br>11:55-12:10         | Artificial Neural Logic Operators for Energy-Efficient Dendritic Computing<br>Unhyeon Kang <sup>1,2</sup> , Seungmin Oh <sup>1,3</sup> , Jingyeong Hwang <sup>1,2</sup> , Jiin Bang <sup>1,4</sup> , Kyungmin Lee <sup>1,5</sup> , Hakseung Rhee <sup>1,6</sup> ,<br>Younghyun Lee <sup>1</sup> , Jooyoung Bae <sup>1</sup> , and Suyoun Lee <sup>1</sup><br><sup>1</sup> Center for Semiconductor Technology, KIST, <sup>2</sup> Department of Materials Science and Engineering, Seoul National University, <sup>3</sup> Department of Physics and Astronomy, Seoul National University, <sup>4</sup> Division of Nanoscience and Technology, University of Science and Technology, <sup>5</sup> School of Electrical Engineering, Korea University, <sup>6</sup> Department of Materials Science and Engineering, KAIST |
| TH2-T-5<br>12:10-12:25         | 신경망회로를 활용한 PID 기반 피드백 제어를 위한 시스템 온 칩 구성<br>유동우 <sup>1</sup> , 백돈규 <sup>2</sup><br><sup>1</sup> 충북대학교 반도체공학전공, <sup>2</sup> 충북대학교 반도체공학부                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| TH2-T-6<br>12:25-12:40         | DeepSCF: Physics-Inspired Neural Networks for Efficient Self-Consistent Charge Density Prediction<br>Minsu Jeong, Ryong-Gyu Lee, and Yong-Hoon Kim<br>School of Electrical Engineering, KAIST                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |

Q. Metrology, Inspection, Analysis, and Yield Enhancement 분과

O45\_[TI2-Q] Metrology, Inspection, Analysis, and Yield Enhancement I

좌장: 제갈원 박사(한국표준과학연구원), 손영훈 마스터(삼성전자)

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| 초청발표<br>TI2-Q-1<br>10:55-11:25 | AI-Enhanced Pulsed Thermography for Surface Micro-Crack Inspection in Epoxy Molding Compounds of Semiconductor Packages<br>Jinsung Rho<br>Department of Mechanical Engineering, Hanbat National University                                             |
| 초청발표<br>TI2-Q-2<br>11:25-11:55 | 초고속 레이저 기반 화학기상증착을 이용한 3차원 유리 구조 표면 전도성 회로 형성 기술<br>한승희, 허준석, 위찬웅<br>전남대학교 기계공학과                                                                                                                                                                       |
| TI2-Q-3<br>11:55-12:10         | 이중모드 열반사 현미경을 이용한 마이크로 전자소자의 정상 및 과도열 특성 분석<br>정찬배, 김동욱, 정문경, 김동목, 장기수<br>한국기초과학지원연구원 연구장비개발부                                                                                                                                                          |
| TI2-Q-4<br>12:10-12:25         | 열특성 기반 첨단반도체 패키징용 TGV 비파괴 고장분석 기술 제안<br>마병진, 백주희, 이영빈, 최성순, 이규석, 김제민<br>한국전자기술연구원                                                                                                                                                                      |
| TI2-Q-5<br>12:25-12:40         | Tip-Enhanced Nano-Spectroscopy and Imaging for Applications in Semiconductor Metrology and Inspection<br>Kyoung-Duck Park <sup>1,2</sup><br><sup>1</sup> Department of Physics, POSTECH, <sup>2</sup> Department of Semiconductor Engineering, POSTECH |

H. Display and Imaging Technologies 분과

O46\_[TJ2-H] Semiconductor Photonics for Displays and Imagers

좌장: 정예환 교수(한양대학교), 노정균 교수(부산대학교)

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| <div>초청발표<br/>TJ2-H-1<br/>10:55-11:25</div> | <div>Next-generation III-V Semiconductor Infrared Photodetectors for Thermal Imaging Sensors<br/>Daehwan Jung<sup>1,2</sup>, Seungwan Woo<sup>1</sup>, Kenneth Duque<sup>1</sup>, Tsimafei Laryn<sup>1,2</sup>, Eungbeom Yeon<sup>1</sup>, Yeonhwa Kim<sup>1</sup>, and Won Jun Choi<sup>1</sup><br/><sup>1</sup>Center for Quantum Technology, KIST, <sup>2</sup>Division of Nanoscience and Technology, KIST School, University of Science and Technology</div> |
| <div>초청발표<br/>TJ2-H-2<br/>11:25-11:55</div> | <div>Photonic-Integrated Circuits and On-Chip Light Sources for Scalable Quantum Computing Technologies<br/>남동욱<sup>1,2</sup><br/><sup>1</sup>한국과학기술원 기계공학과, <sup>2</sup>한국과학기술원 양자대학원</div>                                                                                                                                                                                                                                                                      |
| <div>TJ2-H-3<br/>11:55-12:10</div>          | <div>Analyzing Dark Count Rate and Photon Detection Probability Characteristics of Single Photon Avalanche Diode without Hydrogen Annealing Process<br/>김상환, 정주환, 이한규, 유현, 윤찬수, 이경재, 하만륜, 이상기<br/>Technology CIS Process Development Team, DB HiTek</div>                                                                                                                                                                                                         |
| <div>TJ2-H-4<br/>12:10-12:25</div>          | <div>A 10μm-Pitch Stand-Alone SPAD with 30.3% PDE at 940nm, Utilizing a Dual Epitaxial Growth Process and Full-BDTI with 2x2 Microlens Integration<br/>Juhwan Jung, Sang Hwan Kim, Chansoo Yoon, Hyun Yoo, Gyeong Jae Lee, Man Lyun Ha, and Sang Gi Lee<br/>CIS Process Development Team, DB HiTek</div>                                                                                                                                                          |
| <div>TJ2-H-5<br/>12:25-12:40</div>          | <div>Full Well Capacity Modeling of Vertical Pinned Photodiode with Realistic Photodiode Doping<br/>박지원<sup>1</sup>, 이지원<sup>1,2</sup><br/><sup>1</sup>포항공과대학교 반도체대학원, <sup>2</sup>포항공과대학교 반도체공학과</div>                                                                                                                                                                                                                                                           |

D. Thin Film Process Technology 분과

O47\_[TA3-D] Emerging Devices II

좌장: 문태환 교수(아주대학교), 권대선 교수(숙명여자대학교)

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| TA3-D-1<br>14:00–14:15 | <b>Atomic Layer Deposition of <math>\text{Ge}_x\text{Se}_y\text{Te}_z</math> Thin Films for Selector-only Memory</b><br>Hyun Wook Kim, Ju Hwan Park, Se Hwan Jeon, Tae Jun Yang, Yoon Jae Hong, Dong Hyun Kim, and Byung Joon Choi<br>Department of Materials Science and Engineering, Seoul National University of Science & Technology                                                                                                                                                                                                                                                                                                                                                                                        |
| TA3-D-2<br>14:15–14:30 | <b>Study on the Atomic-Layer-Deposited In-Te Films for Vertical Selector Only Memory Applications</b><br>Myeong Hwan You <sup>2</sup> , Beom Joo Kim <sup>2,3</sup> , and Dae Hwan Kang <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, POSTECH, <sup>2</sup> Graduate School of Semiconductor Technology, POSTECH, <sup>3</sup> Department of Materials Science and Engineering, Chonnam National University                                                                                                                                                                                                                                                                                           |
| TA3-D-3<br>14:30–14:45 | <b>Ultrathin Monatomic Antimony Films by Sacrificial Atomic Layer Deposition for Phase Change Memory</b><br>Sangmin Jeon <sup>1,2</sup> , Gwangsik Jeon <sup>1,2</sup> , Seunghwan Lee <sup>1,2</sup> , Jeong Woo Jeon <sup>1,2</sup> , Wonho Choi <sup>1,2</sup> , Byongwoo Park <sup>1,2</sup> , Sungjin Kim <sup>1,2</sup> , Junwoo Park <sup>1,2</sup> , Chanyoung Yoo <sup>3</sup> , Hyejin Jang <sup>1,2</sup> , and Cheol Seong Hwang <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup> Department of Materials Science and Engineering, Hongik University |
| TA3-D-4<br>14:45–15:00 | <b>Atomic Layer Deposition of <math>\text{Sb}_2\text{Te}_3/\text{MnTe}</math> Superlattice Film for Vertical Phase Change Memory</b><br>Gwangsik Jeon <sup>1,2</sup> , Wonho Choi <sup>1,2</sup> , Byongwoo Park <sup>1,2</sup> , Sangmin Jeon <sup>1,2</sup> , Sungjin Kim <sup>1,2</sup> , Junwoo Park <sup>1,2</sup> , Chanyoung Yoo <sup>3</sup> , and Cheol Seong Hwang <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup> Department of Materials Science and Engineering, Hongik University                                                                 |
| TA3-D-5<br>15:00–15:15 | <b>Multilayer Bi-GeSeTe SOM for Window-Margin Enlargement and Array-Level Reproducibility</b><br>Jae Jun Lee, Eun Taek Yu, Geon Woo Cheon, and Min Kyu Yang<br>Artificial Intelligence Semiconductor Process Lab, Sahmyook University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                           |
| TA3-D-6<br>15:15–15:30 | <b>Enhanced Read Margin and Multilevel Switching Characteristics in W/GeAsSeTe/W Selector-Only Memory via Bi Doping</b><br>Min Kyung Lee <sup>1</sup> , Ji Soo Han <sup>2</sup> , Dong Hyun Lee <sup>2</sup> , Se Eun Jeong <sup>2</sup> , Hee Sang Park <sup>2</sup> , Changhwan Shin <sup>1</sup> , and Min Kyu Yang <sup>2</sup><br><sup>1</sup> School of Electrical Engineering, Korea University, <sup>2</sup> Artificial Intelligence Semiconductor Process Lab, Sahmyook University                                                                                                                                                                                                                                     |
| TA3-D-7<br>15:30–15:45 | <b>Sn-Doped GSST Selector-Only Memory for Robust BNN Inference</b><br>Hyun Kyu Seo <sup>1,2</sup> , Na Young Kim <sup>1</sup> , Ji Won Song <sup>1</sup> , Jae-Seung Jeong <sup>1</sup> , Min Hyuk Park <sup>2</sup> , and Min Kyu Yang <sup>1</sup><br><sup>1</sup> Artificial Intelligence Semiconductor Process Lab, Sahmyook University, <sup>2</sup> Department of Materials Science and Engineering, Seoul National University                                                                                                                                                                                                                                                                                            |

B. Patterning (Lithography & Etch Technology) 분과

O48\_[TB2-B] Patterning and Etch Materials

좌장: 김창구 교수(아주대학교), 채희엽 교수(성균관대학교)

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| 초청발표<br>TB2-B-1<br>14:00-14:30 | Innovation of Patterning Materials in Semiconductor Technology<br>Seongjun Park<br>Department of System Semiconductor Engineering, College of Engineering, Yonsei University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                  |
| TB2-B-2<br>14:30-14:45         | Effect of H <sub>2</sub> O Addition on Fluorocarbon Layer Formation on SiO <sub>2</sub> and Si <sub>3</sub> N <sub>4</sub> Films in C <sub>4</sub> F <sub>8</sub> Plasmas<br>Haegeon Jung <sup>1,2</sup> , Hakseung Lee <sup>1,2</sup> , Daeun Hong <sup>3</sup> , Kangwoo Lee <sup>3</sup> , Minsung Jeon <sup>4</sup> , and Heeyeop Chae <sup>1,4</sup><br><sup>1</sup> Department of Semiconductor and Display Engineering, Sungkyunkwan University, <sup>2</sup> Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd., <sup>3</sup> School of Chemical Engineering, Sungkyunkwan University, <sup>4</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University |
| TB2-B-3<br>14:45-15:00         | 정전척(Electrostatic Chuck)의 주파수 응답 특성과 반도체 식각 공정(Etch Process)의 영향성 연구<br>오병욱, 송완수, 강창진, 이윤영<br>PSK(주) 연구개발본부                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                   |
| TB2-B-4<br>15:00-15:15         | Metal Seasoning 및 OES 장기 모니터링을 통한 Plasma Etch 설비의 Aging 방법론<br>유하늘 <sup>1</sup> , 임재용 <sup>1</sup> , 김수정 <sup>1</sup> , 이현기 <sup>1</sup> , 최두원 <sup>2</sup> , 서봉임 <sup>2</sup> , 이원석 <sup>2</sup> , 조성민 <sup>1</sup> , 금의석 <sup>1</sup><br><sup>1</sup> 삼성전자 Digital Twin센터, <sup>2</sup> 삼성전자 메모리제조기술센터                                                                                                                                                                                                                                                                                                                                                                                                      |
| TB2-B-5<br>15:15-15:30         | Coupling between Diffusion and Surface Reaction in Atomic Layer Etching<br>Sangheon Lee<br>Department of Chemical Engineering and Materials Science, Ewha Womans University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                   |
| TB2-B-6<br>15:30-15:45         | CF <sub>4</sub> /Ar/O <sub>2</sub> 분위기에서 높은 물리화학적 플라즈마 식각 저항성을 지닌 고엔트로피 산화물 세라믹<br>마호진<br>경기대학교 신소재화학공학부 신소재공학전공                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                              |

D. Thin Film Process Technology 분과

O49\_[TC3-D] Thin Film Transistors I

좌장: 안지훈 교수(한양대학교), 최병준 교수(서울과학기술대학교)

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| TC3-D-1<br>14:00–14:15 | <b>Impact of Deposition and Annealing Conditions on Reliability and Performance in BEOL-Compatible Monolithic 3D IGZO Transistors</b><br>Min-Joe Lee, Ji-Won Kang, and Sung-Min Yoon<br>Kyung Hee University                                                                                                                                                                                                                                                                                                                                                                                                                    |
| TC3-D-2<br>14:15–14:30 | <b>Investigation for W Contact on IGZO TFT via Deuterium Annealing for Suppressed Oxygen Diffusion</b><br>Woosub Byun <sup>1</sup> , Tae-Hyun Kil <sup>2</sup> , Hwanyeol Park <sup>3</sup> , Junyoung Park <sup>2,4</sup> , and Dae-Myeong Geum <sup>1</sup><br><sup>1</sup> Department of Electrical and Computer Engineering, Inha University, <sup>2</sup> ParkLab Semiconductor Inc, <sup>3</sup> Department of Display Materials Engineering, Soonchunhyang University, <sup>4</sup> School of Electronics Engineering, Chungbuk National University                                                                      |
| TC3-D-3<br>14:30–14:45 | <b>Source/Drain Overlap Length Dependence on the Electrical Performance of a-IGZO TFTs with Ti-Electrodes</b><br>Junhui Park <sup>1</sup> , Jaewook Yoo <sup>1</sup> , Hongseung Lee <sup>1</sup> , Seongbin Lim <sup>1</sup> , Minah Park <sup>1</sup> , Seohyeon Park <sup>1</sup> , Sojin Jung <sup>1</sup> , Sieun Lee <sup>1</sup> , Donghyeon Lee <sup>1</sup> , Soohyun Lim <sup>1</sup> , Dongsun Shin <sup>1</sup> , Kiyoun Lee <sup>3</sup> , Sung Hun Jin <sup>2</sup> , and Hagyoul Bae <sup>1</sup><br><sup>1</sup> Jeonbuk National University, <sup>2</sup> Kyung Hee University, <sup>3</sup> Hongik University |
| TC3-D-4<br>14:45–15:00 | <b>Correlation of Hydrogen and Oxygen Composition with Transition Region Voltage in Oxide TFTs</b><br>Junseok Lee <sup>1</sup> , Soohong Eo <sup>1</sup> , Jae Woo Lee <sup>1</sup> , Changwook Kim <sup>1</sup> , Sung-Jin Choi <sup>1</sup> , Yoon Jung Lee <sup>1</sup> , Jaeman Jang <sup>2</sup> , Ju Heyuck Baek <sup>2</sup> , Byung Du Ahn <sup>2</sup> , Jong Uk Bae <sup>2</sup> , Soo Young Yoon <sup>2</sup> , and Dae Hwan Kim <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, Kookmin University, <sup>2</sup> R&D Center, LG Display Co., Ltd.                                                    |
| TC3-D-5<br>15:00–15:15 | <b>Revealing Local Heterogeneity in a-IGZO through 4D-STEM and EELS</b><br>Daeyeong Kim, Keeyong Lee, Jinho Byun, Geun Ho Gu, and Sang Ho Oh<br>Department of Energy Engineering, KENTECH                                                                                                                                                                                                                                                                                                                                                                                                                                       |
| TC3-D-6<br>15:15–15:30 | <b>Controllable Subthreshold Swing in Driving Oxide TFTs Enabled by Sn Delta Layer</b><br>Jae Young Lee <sup>1</sup> and Jae Kyeong Jeong <sup>2</sup><br><sup>1</sup> Department of Artificial Intelligence Semiconductor Engineering, Hanyang University, <sup>2</sup> Department of Electronic Engineering, Hanyang University                                                                                                                                                                                                                                                                                               |
| TC3-D-7<br>15:30–15:45 | <b>Electrical Pulse Signal for Enhancement of Electrical Performances in In<sub>2</sub>O<sub>3</sub> TFTs</b><br>Dongsun Shin <sup>1</sup> , Jaewook Yoo <sup>1</sup> , Hongseung Lee <sup>1</sup> , Sojin Jung <sup>1</sup> , Seongbin Lim <sup>1</sup> , Seohyeon Park <sup>1</sup> , Minah Park <sup>1</sup> , Donghyeon Lee <sup>1</sup> , Soohyun Lim <sup>1</sup> , Sieun Lee <sup>1</sup> , Junhui Park <sup>1</sup> , Kiyoun Lee <sup>2</sup> , and Hagyoul Bae <sup>1</sup><br><sup>1</sup> Jeonbuk National University, <sup>2</sup> Hongik University                                                                |

K. Memory (Design & Process Technology) 분과

O50\_[TD3-K] Adv. Memory & Ferroelectric

좌장: 강대웅 교수(서울대학교), 조우영 교수(KAIST)

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| 초청발표<br>TD3-K-1<br>14:00–14:30 | <b>Next Generation NAND Technology</b><br>Wanki Kim<br>Semiconductor Research and Development, Samsung Electronics Co., Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                           |
| TD3-K-2<br>14:30–14:45         | <b>Ferroelectric Memcapacitor Crossbar Array with NAND Flash Structure for In-Memory Computing</b><br>Hwiho Hwang <sup>1,2</sup> , Sangwook Youn <sup>1,2</sup> , and Hyungjin Kim <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, <sup>2</sup> Hanyang University, Department of Semiconductor Engineering, Hanyang University                                                                                                                                                                                                                                                                                          |
| TD3-K-3<br>14:45–15:00         | <b>BEOL-Compatible FeTFTs With Ultra-Thin 3 nm HZO / 3 nm Oxide Semiconductor Stack (Physical) Enabling Low-Voltage Operation for Next-Generation Non-Volatile Memory</b><br>Kyungsoo Park <sup>1</sup> , Minhyuk Kim <sup>1</sup> , Duho Kim <sup>1</sup> , Jihoon Choi <sup>2</sup> , Yeonwoo Choi <sup>2</sup> , Jin Yeong Lee <sup>2</sup> , Taesuk Kim <sup>1</sup> , Hyeoncheol Jeong <sup>2</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University                                               |
| TD3-K-4<br>15:00–15:15         | <b>후면 강유전체 기반 이중 게이트 소자를 이용한 Read Disturbance 현상을 억제할 수 있는 AND-type 어레이 구조</b><br>정재중 <sup>1</sup> , 박영근 <sup>1</sup> , 김예은 <sup>2</sup> , 김영권 <sup>3</sup> , 정원묵 <sup>4</sup> , 유찬미 <sup>4</sup> , 김승훈 <sup>1</sup> , 김영준 <sup>4</sup> , 강대현 <sup>1</sup> , 장병철 <sup>3</sup> , 박종경 <sup>2</sup> , 조병진 <sup>1,4</sup><br><sup>1</sup> 한국과학기술원 전기및전자공학부, <sup>2</sup> 서울과학기술대학교 지능형반도체공학과, <sup>3</sup> 경북대학교 전자전기공학부, <sup>4</sup> 한국과학기술원 반도체공학대학원                                                                                                                                                                                                    |
| TD3-K-5<br>15:15–15:30         | <b>Towards Artificial Intelligence Hardware with Monolithic 3D Integrated Ferroelectric Transistors</b><br>Geonwook Kim <sup>1</sup> , Hyunho Seok <sup>2</sup> , Sihoon Son <sup>3</sup> , Hyunbin Choi <sup>4</sup> , Jinhyoung Lee <sup>1</sup> , Dongho Lee <sup>1</sup> , Seowoo Son <sup>3</sup> , and Taesung Kim <sup>1,3,4</sup><br><sup>1</sup> School of Mechanical Engineering, Sungkyunkwan University, <sup>2</sup> Research Laboratory of Electronics, MIT, <sup>3</sup> SKKU Advanced Institute of Nano Technology, Sungkyunkwan University, <sup>4</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University |
| TD3-K-6<br>15:30–15:45         | <b>Vertical Ferroelectric Tunnel Junctions with Composition-Tuned Oxide Semiconductors for Enhanced TER and Self-Rectifying Behavior</b><br>Yeonwoo Choi <sup>1</sup> , Kyungsoo Park <sup>2</sup> , Jin Yeong Lee <sup>1</sup> , Taesuk Kim <sup>2</sup> , Sang Myun Lim <sup>1</sup> , Jihoon Choi <sup>1</sup> , Hyeoncheol Jeong <sup>1</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University                                                                                                      |

P. Device for Energy (Solar Cell, Power Device, Battery, etc.) 분과

O51\_[TE3-P] Electrochemical Energy Device

좌장: 주종훈 교수(GIST), 김선동 박사(한국에너지기술연구원)

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| 초청발표<br>TE3-P-1<br>14:00–14:30 | <b>Solid Oxide Electrolysis Cells for Clean Hydrogen Production</b><br>Sun-Dong Kim <sup>1,2</sup><br><sup>1</sup> High Temperature Electrolysis Laboratory, Korea Institute of Energy Research, <sup>2</sup> National Hydrogen Hub Laboratory for SOEC                                                                                                                                                                                                                                                                                                                                                                               |
| TE3-P-2<br>14:30–14:45         | <b>Dual Synergistic Effects of SOCs ALD CeO<sub>2</sub> Infiltration PrOx@LSCF Oxygen Electrode for Enhanced Catalyst Activity and Stability</b><br>Woojin Park, Hyongjune Kim, and Jihwan An<br>Department of Mechanical Engineering, POSTECH                                                                                                                                                                                                                                                                                                                                                                                        |
| TE3-P-3<br>14:45–15:00         | <b>Composition-Controlled Cathode Protective Layer via Powder-Atomic Layer Deposition for All-Solid-State Batteries</b><br>Kyu Moon Kwon <sup>1</sup> , Dae Ho Kim <sup>1</sup> , Ha Yeon Kwon <sup>1</sup> , Joungwon Park <sup>2</sup> , Kyoung Hwan Kim <sup>2</sup> , Hwi-Yeol Park <sup>2</sup> , Hyo Rang Kang <sup>1,3</sup> , and Tae Joo Park <sup>1,4</sup><br><sup>1</sup> Department of Materials Science & Chemical Engineering, Hanyang University, <sup>2</sup> Battery Material TU, Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd., <sup>3</sup> NanoCamp Inc., <sup>4</sup> ALPES Co., Ltd. |
| TE3-P-4<br>15:00–15:15         | <b>Atomic Scale Tracking of Li Ion Migration in Epitaxial T-Nb<sub>2</sub>O<sub>5</sub> Using In situ STEM</b><br>Sol-I Sung <sup>1</sup> , Yaolong Xing <sup>1,2</sup> , Jinho Byun <sup>1</sup> , Hyun Han <sup>3,4</sup> , and Sang Ho Oh <sup>1</sup><br><sup>1</sup> Department of Energy Engineering, KENTECH, <sup>2</sup> Max Planck Institute for Sustainable Materials, <sup>3</sup> Department of Materials Science and Engineering, POSTECH, <sup>4</sup> Max Planck Institute of Microstructure Physics                                                                                                                  |
| TE3-P-5<br>15:15–15:30         | <b>Thin Film Ion-selective Hydrogel Separator for Sodium Resource Utilization and Adaptive Energy Storage</b><br>Hyunlee Kim <sup>1</sup> , Hyewon Song <sup>2</sup> , Do Hyeon Jung <sup>2</sup> , Chuong Van Ho <sup>2</sup> , Hui Hun Cho <sup>2</sup> , Jun Hyuk Heo <sup>2</sup> , and Jung Heon Lee <sup>1,2</sup><br><sup>1</sup> Department of MetaBioHealth, Sungkyunkwan University, <sup>2</sup> School of Advanced Materials Science and Engineering, Sungkyunkwan University                                                                                                                                             |
| TE3-P-6<br>15:30–15:45         | <b>Enhancing Interfacial Stability of Li Metal Anodes via In-situ H<sub>2</sub> Plasma Surface Treatment and a Low-Temperature Lithicone Passivation Layer</b><br>Ha Yeon Kwon <sup>1</sup> , Kyu Moon Kwon <sup>1</sup> , Min Jung Choi <sup>1</sup> , Syed Jazib Abbas Zaidi <sup>1</sup> , Seung Jeong Oh <sup>2</sup> , Hyo Rang Kang <sup>1,3</sup> , and Tae Joo Park <sup>1</sup><br><sup>1</sup> Department of Materials Science & Chemical Engineering, Hanyang University, <sup>2</sup> R&D Division, Hyundai Motors Co., Ltd., <sup>3</sup> NanoCamp Inc.                                                                  |

C. Material Growth & Characterization 분과

O52\_[TF3-C] 2D vdW Semiconductors and Heterostructures

좌장: 이정우 교수(홍익대학교), 백승협 책임박사(KIST)

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| TF3-C-1<br>14:00–14:15         | <b>Geometrically Induced Boundary Layer Propel Wafer-Scale Monolayer Tungsten Disulfide Synthesis</b><br>Dongho Lee <sup>1</sup> , Seowoo Son <sup>2</sup> , Hyunho Seok <sup>3</sup> , Hyunbin Choi <sup>4</sup> , Geon Wook Kim <sup>1</sup> , and Taesung Kim <sup>1,2,4</sup><br><sup>1</sup> School of Mechanical Engineering, Sungkyunkwan University, <sup>2</sup> SKKU Advanced Institute of Nano Technology, Sungkyunkwan University, <sup>3</sup> Research Laboratory of Electronics, MIT, <sup>4</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University                                                                                                                                                                                          |
| TF3-C-2<br>14:15–14:30         | <b>Hidden Ferroelectricity Unlocked in Centrosymmetric WS<sub>2</sub> Bilayers</b><br>Seowoo Son <sup>1</sup> , Dongho Lee <sup>2</sup> , Hyunho Seok <sup>3</sup> , Jinhyoung Lee <sup>2</sup> , Gunhyeong Kim <sup>4</sup> , Sihoon Son <sup>1</sup> , Hyunbin Choi <sup>4</sup> , Geonwook Kim <sup>2</sup> , and Taesung Kim <sup>1,2,4</sup><br><sup>1</sup> SKKU Advanced Institute of Nano Technology, Sungkyunkwan University, <sup>2</sup> School of Mechanical Engineering, Sungkyunkwan University, <sup>3</sup> Research Laboratory of Electronics, MIT, <sup>4</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University                                                                                                                          |
| 초청발표<br>TF3-C-3<br>14:30–15:00 | <b>Phase-Tunable Growth of van der Waals Semiconductors: 2D MoTe<sub>2</sub> and InSe Systems for Logic and Reconfigurable Nanoelectronics</b><br>Seunguk Song <sup>1,2</sup><br><sup>1</sup> Department of Energy Science, Sungkyunkwan University, <sup>2</sup> Center for 2D Quantum Heterostructures, IBS, Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                                                                                                  |
| 초청발표<br>TF3-C-4<br>15:00–15:30 | <b>Epitaxially Assembled van der Waals Heterostructures for In-sensor Computing</b><br>서준기<br>KAIST                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| TF3-C-5<br>15:30–15:45         | <b>Atomic-Level Conformal-Growth-Enabled Monolithic Integration of Vertical Monolayer MoS<sub>2</sub> Field-Effect Transistor</b><br>Seonguk Yang <sup>1</sup> , Huimin Lee <sup>2</sup> , Hanbin Cho <sup>1</sup> , Ki Han Kim <sup>3</sup> , Saeyoung Oh <sup>2</sup> , Hoyeon Cho <sup>4</sup> , Kyungmin Ko <sup>4</sup> , Namwook Hur <sup>4</sup> , Hu Young Jeong <sup>2</sup> , Byung Chul Jang <sup>3</sup> , and Joonki Suh <sup>1</sup><br><sup>1</sup> Department of Chemical and Biomolecular Engineering, KAIST, <sup>2</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>3</sup> School of Electronic and Electrical Engineering, Kyungpook National University, <sup>4</sup> Department of Materials Science and Engineering, UNIST |

N. VLSI CAD 분과

O53\_[TG3-N] Advanced CAD for VLSI

좌장: 현대준 교수(세종대학교), 박희천 교수(UNIST)

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| 초청발표<br>TG3-N-1<br>14:00-14:30 | Design Methodologies for Memory: Design Implementation Perspective<br>안세용<br>삼성전자 메모리사업부                                                                                                                                                                             |
| TG3-N-2<br>14:30-14:45         | Logic Partitioning Methodology for Utilizing Active Backside Layers<br>Minhong Kim, Ikkyum Kim, and Heechun Park<br>Department of Electrical Engineering, UNIST                                                                                                      |
| TG3-N-3<br>14:45-15:00         | Dataflow-aware Placement Optimization for Digital Compute-in-Memory (DCIM) Using H-Tree-Like Adder Tree Organization<br>Mingyeom Kim <sup>1</sup> , Gangmin Jeon <sup>2</sup> , and Heechun Park <sup>2</sup><br><sup>1</sup> Kookmin University, <sup>2</sup> UNIST |
| TG3-N-4<br>15:00-15:15         | PPA-Driven Multi-Bit Flip-Flop Clustering based on Minimum-Cost Maximum-Flow Algorithm<br>Jiyun Ham, Sojung Park, and Heechun Park<br>UNIST                                                                                                                          |
| TG3-N-5<br>15:15-15:30         | Monte Carlo Tree Search with LLM for Design Space Optimization<br>Jongho Yoon, Jeonghyun Choi, and Seokhyeong Kang<br>Department of Electrical Engineering, POSTECH                                                                                                  |
| TG3-N-6<br>15:30-15:45         | ILP-Based Pad Assignment for Signal and Power Integrity<br>Hyuk Ko and Daijoon Hyun<br>Department of Semiconductor Systems Engineering, Sejong University                                                                                                            |

G. Device & Process Modeling, Simulation and Reliability 분과

O54\_[TH3-G] Device & Process Modeling, Simulation and Reliability V

좌장: 이영훈 교수(인천대학교), 백록현 교수(POSTECH)

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| TH3-G-1<br>14:00–14:15 | <p><b>Quantum Transport Simulation for a-IGZO Channel Devices Considering Structural Disorder Effect</b><br/>Jooseok Kim<sup>1</sup>, Ilhan Yu<sup>1</sup>, Gyeongwon Roh<sup>1</sup>, Yeongjun Lim<sup>1</sup>, Seonghyun Kim<sup>2</sup>, Hyejung Choi<sup>2</sup>, Soogil Kim<sup>2</sup>, and Mincheol Shin<sup>1</sup><br/><sup>1</sup>School of Electrical Engineering, KAIST, <sup>2</sup>Component Research, R&amp;D Division, SK hynix Inc.</p>                                                                                                                                                        |
| TH3-G-2<br>14:15–14:30 | <p><b>Numerically Stable Compact Model of a Bistable Resistor (Biristor) for Circuit and Array-Level Applications</b><br/>Hanbin Lee<sup>1</sup>, Ji Won Park<sup>1</sup>, Seonghyeon Jeong<sup>1</sup>, Jeong Yeon Im<sup>1</sup>, So-Jeong Park<sup>1</sup>, Youngmin Kim<sup>1</sup>, Yoon Jung Lee<sup>1</sup>, Dae Hwan Kim<sup>1</sup>, Jihoon Han<sup>2</sup>, Seheon Oh<sup>2</sup>, Youngchul Kim<sup>2</sup>, and Sung-Jin Choi<sup>1</sup><br/><sup>1</sup>School of Electronics and Electrical Engineering, Kookmin University, <sup>2</sup>ESD/TCAD Team, Technology Enabling Center, DB HiTek</p> |
| TH3-G-3<br>14:30–14:45 | <p><b>Exploring Layer Number-Dependent Hole Transport in W- and Mo-Based Two-Dimensional Materials via Full-Band Semi-Classical Monte Carlo Simulation</b><br/>Donghyeok Lee<sup>1</sup>, Sukhyeong Youn<sup>1</sup>, and Jiwon Chang<sup>1,2</sup><br/><sup>1</sup>Department of Materials Science and Engineering, Yonsei University, <sup>2</sup>Department of System Semiconductor Engineering, Yonsei University</p>                                                                                                                                                                                       |
| TH3-G-4<br>14:45–15:00 | <p><b>TCAD Fast 3D Calibration Method to Analysis Edge Terminal in LDMOS</b><br/>Jihye Park, Jieen Lee, Jong Min Kim, Young Chul Kim, and Hyunchul Nah<br/>ESD/TCAD Team, Technology Enabling Center, DB HiTek</p>                                                                                                                                                                                                                                                                                                                                                                                              |
| TH3-G-5<br>15:00–15:15 | <p><b>Impact of Post-Channel-Release SiGe Residue in Forksheet FETs</b><br/>Sunmin Yeou, Sanguk Lee, Jongseo Park, Yonghwan Ahn, Minchan Kim, Gunryeol Cho, and Rock-Hyun Baek<br/>Department of Electrical Engineering, POSTECH</p>                                                                                                                                                                                                                                                                                                                                                                            |
| TH3-G-6<br>15:15–15:30 | <p><b>TCAD-Guided Calibration of Compact Models for IGZO TFTs in 6T1C Synaptic Memory Applications</b><br/>Ye-Han Kwon, Seung-Woo Jung, and Sung-Min Hong<br/>Department of Electrical Engineering and Computer Science, GIST</p>                                                                                                                                                                                                                                                                                                                                                                               |
| TH3-G-7<br>15:30–15:45 | <p><b>Degradation Behavior of NPN BJTs under On/Off Collector Stress Conditions</b><br/>Ju-Yong Shin, Yu-Bin Kim, Ju-Han Lee, and Hi-Deok Lee<br/>Department of Electronics Engineering, Chungnam National University</p>                                                                                                                                                                                                                                                                                                                                                                                       |

F. Silicon and Group-IV Devices and Integration Technology 분과

O55\_[TI3-F] GAA/CFET Device Technology and Design

좌장: 김명수 교수(UNIST), 황현준 교수(목포대학교)

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| TI3-F-1<br>14:00-14:15 | <b>Design Technology Co-Optimization (DTCO): Performance Analysis of Gate Extension Scaling on Nanosheet FET Considering Gate Metal Work-Function Non-Uniformity</b><br>Jung Su Kim and Changhwan Shin<br>School of Electrical Engineering, Korea University                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| TI3-F-2<br>14:15-14:30 | <b>Uniaxially Compressively Strained Ge (100)-OI p-MOSFET for High-Performance 3D Stacked FET (3DSFET) Applications</b><br>Hyeongrak Lim <sup>1</sup> , Seong Kwang Kim <sup>1</sup> , Hojin Jeong <sup>1</sup> , Jinha Lim <sup>1</sup> , Songhyeon Kuk <sup>1</sup> , Dae-Myeong Geum <sup>2</sup> , Jinho Bae <sup>3</sup> , Jaehyun Park <sup>3</sup> , Daewon Ha <sup>3</sup> , Jaehoon Han <sup>4</sup> , Younghyun Kim <sup>5</sup> , Jaeyong Jeong <sup>1</sup> , and Sanghyeon Kim <sup>1</sup><br><sup>1</sup> KAIST, <sup>2</sup> Inha University, <sup>3</sup> Semiconductor R&D Center, Samsung Electronics Co., Ltd., <sup>4</sup> KIST, <sup>5</sup> Hanyang University                   |
| TI3-F-3<br>14:30-14:45 | <b>그린 레이저 열처리 공정 도입을 통한 상부 Ge PMOS 기반 이중 3차원 순차적 CFET 성능 개선</b><br>박영근, 임형락, 정재중, 김준표, 김성광, 김상현, 조병진<br>한국과학기술원 전기 및 전자공학부                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                               |
| TI3-F-4<br>14:45-15:00 | <b>Comparative Analysis of Rare-Earth Elements (La, Y, Gd) Oxides Based Dipole-First Gate Stack for Multi-Vt Design Integration Targeting Low Thermal Budget CFET Device</b><br>Sangkuk Han <sup>1</sup> , Wonjae Choi <sup>2</sup> , Jaewon Chung <sup>2</sup> , Haesoo Jang <sup>2</sup> , Kyungwook Park <sup>1</sup> , Sangmyun Lim <sup>2</sup> , Soyoung Park <sup>2</sup> , Sangwoo Jeong <sup>1</sup> , Hanbyul Kim <sup>3</sup> , Yong Joo Park <sup>3</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University, <sup>3</sup> SK Trichem Co., Ltd. |
| TI3-F-5<br>15:00-15:15 | <b>Process Emulation and Device Simulation of Three-Dimensional Complementary Transistor Architecture, Flip FET</b><br>Min-Seo Jang and Sung-Min Hong<br>Department of Electrical Engineering and Computer Science, GIST                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| TI3-F-6<br>15:15-15:30 | <b>고품질 헤테로 에피 기반으로 구현된 GAA-FET 소자 특성</b><br>이성현, 김진하, 김상훈, 박민아, 정순규, 손민균, 김지은, 허수빈, 박재성, 최석원, 송한찬, 이왕주, 구스타보 파나마, 임종필, 박소영, 박정우, 서동우<br>한국전자통신연구원 인공지능창의연구소 소재부품연구본부                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| TI3-F-7<br>15:30-15:45 | <b>Lattice Kinetic Monte Carlo (LKMC) Simulation to Investigate the Impact of Growth Size of Epitaxial-Source/Drain on the Drive Current of NSFET</b><br>Hyunwoo Lee and Changhwan Shin<br>School of Electrical Engineering, College of Engineering, Korea University                                                                                                                                                                                                                                                                                                                                                                                                                                    |

H. Display and Imaging Technologies 분과

O56\_[TJ3-H] Emerging Displays and Image Sensors

좌장: 정예환 교수(한양대학교), 백근우 교수(한밭대학교)

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| 초청발표<br>TJ3-H-1<br>14:00–14:30 | <b>Strategy for Simultaneous Strain-Engineering and Chip Bonding for Stretchable Display and Electronics Applications</b><br>Yongtaek Hong <sup>1,2</sup><br><sup>1</sup> Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University                                           |
| 초청발표<br>TJ3-H-2<br>14:30–15:00 | <b>Natural Strategies for Vision: Inspiring Advanced Robotic Imaging Systems</b><br>Young Min Song<br>School of Electrical Engineering, KAIST                                                                                                                                                                                                                                            |
| TJ3-H-3<br>15:00–15:15         | <b>Stretchable Display with Cellulose Nanocrystal-Based Optical Diffuser for Strain-Invariant Image Quality</b><br>Kyung Jun Lee <sup>1</sup> , Hyeon Ho Shin <sup>2</sup> , and Yei Hwan Jung <sup>1,2</sup><br><sup>1</sup> Department of Artificial Intelligence Semiconductor Engineering, Hanyang University, <sup>2</sup> Department of Electronic Engineering, Hanyang University |
| TJ3-H-4<br>15:15–15:30         | <b>Enhanced Thermal and Optical Performance in Vertically Stacked <math>\mu</math>LEDs via Oxide-Based Wafer Bonding</b><br>Hyun Soo Kim, Juhyuk Park, Woo Jin Baek, and SangHyeon Kim<br>School of Electrical Engineering, KAIST                                                                                                                                                        |
| TJ3-H-5<br>15:30–15:45         | <b>Low-Voltage Resonant Reflective Display via MOSFET-Assisted Selective Pixel Deposition</b><br>Jun Seo Lee <sup>1</sup> , Jae Min Jeon <sup>1</sup> , Hyo Eun Jeong <sup>2</sup> , and Young Min Song <sup>2</sup><br><sup>1</sup> School of Electrical Engineering and Computer Science, GIST, <sup>2</sup> School of Electrical Engineering, KAIST                                   |

D. Thin Film Process Technology 분과

O57\_[TA4-D] Emerging Devices III

좌장: 손준우 교수(서울대학교), 백인환 교수(인하대학교)

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| TA4-D-1<br>15:55-16:10 | <b>Reversible Gap State Saturation of MoS<sub>2</sub>-Semimetal Interface for Uninterrupted Synaptic Weight</b><br>손시훈 <sup>1,2</sup> , 최현빈 <sup>3</sup> , 김건욱 <sup>4</sup> , 김태성 <sup>1,2,3,4</sup><br><sup>1</sup> 성균관대학교 나노과학기술학과, <sup>2</sup> 성균관대학교 SKKU Advanced Institute of Nano Technology, <sup>3</sup> 성균관대학교 반도체융합공학과, <sup>4</sup> 성균관대학교 기계공학과                                                                                                                                                                                                                                                                                                                                                                                                                                                                         |
| TA4-D-2<br>16:10-16:25 | <b>One-Shot Remote Integration of Polymer Synaptic Arrays for Flexible Neural Network System</b><br>Jaehoon Lee <sup>1</sup> , Jihun Noh <sup>2</sup> , Sungmo Kang <sup>1</sup> , and Bosoek Kang <sup>1,2</sup><br><sup>1</sup> Department of Nanoscience and Technology, Sungkyunkwan University, <sup>2</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                                                                                        |
| TA4-D-3<br>16:25-16:40 | <b>Ferroelectric Synaptic Transistors with Tunable Plasticity via Coupled Gate-Insulator and Active-Layer Engineering</b><br>Ji-Won Jang, Hyun-Sik Kim, Hong-Sub Lee, and Sung-Min Yoon<br>Kyung Hee University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                       |
| TA4-D-4<br>16:40-16:55 | <b>Reconfigurable Floating-Gate Memory based on van der Waals Heterostructures</b><br>Seongwook Yoon <sup>1</sup> and Woo Jong Yu <sup>2</sup><br><sup>1</sup> Department of Semiconductor Convergence Engineering, Sunkyunkwan University, <sup>2</sup> Department of Electrical and Computer Engineering, Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                   |
| TA4-D-5<br>16:55-17:10 | <b>Gate Insulator Stack Engineering for Simultaneous Enhancement of On-Current and Reliability in a-IGZO TFT-Based Synaptic Circuits</b><br>Youngchae Roh <sup>1,2,3</sup> , Narae Han <sup>1,4</sup> , Ha-jun Sung <sup>4</sup> , Sangbum Kim <sup>1,2,3</sup> , Sangwook Kim <sup>4</sup> , Minseung Kang <sup>1,2,3</sup> , Jongun Won <sup>1,2,3</sup> , Joo-Hun Han <sup>4</sup> , Younjin Jang <sup>4</sup> , and Jee-Eun Yang <sup>4</sup><br><sup>1</sup> Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup> Research Institute of Advanced Materials, Seoul National University, <sup>4</sup> Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd.                                                                           |
| TA4-D-6<br>17:10-17:25 | <b>Impact of Neutron Irradiation on <math>\alpha</math>-In<sub>2</sub>Se<sub>3</sub> Ferroelectric Memory under Harsh Environments</b><br>Sieun Lee <sup>1</sup> , Jaewook Yoo <sup>2</sup> , Hongseung Lee <sup>2</sup> , Seongbin Lim <sup>2</sup> , Minah Park <sup>2</sup> , Seohyeon Park <sup>2</sup> , Sojin Jung <sup>2</sup> , Donghyeon Lee <sup>2</sup> , Soohyun Lim <sup>2</sup> , Dongsun Shin <sup>2</sup> , Junhui Park <sup>2</sup> , Bong-ki Jung <sup>3</sup> , Taewan Kim <sup>4</sup> , and Hagyoul Bae <sup>2</sup><br><sup>1</sup> Department of Electrical Engineering, Jeonbuk National University, <sup>2</sup> Department of Electronic Engineering, Jeonbuk National University, <sup>3</sup> Q-beam solution Inc., <sup>4</sup> Department of Intelligent Semiconductor Engineering, University of Seoul |
| TA4-D-7<br>17:25-17:40 | <b>Bi-Heterojunction Noise-Enhanced Transistors for Multi-Bit Stochasticity and Secure Image Generation</b><br>Youngmin Han <sup>1</sup> , Jaechan Song <sup>2</sup> , and Hocheon Yoo <sup>1</sup><br><sup>1</sup> Department of Electronic Engineering, Hanyang University, <sup>2</sup> Department of Artificial Intelligence Semiconductor Engineering, Hanyang University                                                                                                                                                                                                                                                                                                                                                                                                                                                        |

B. Patterning (Lithography & Etch Technology) 분과

O58\_[TB4-B] Advanced Etch

좌장: 김규현 전문교수(SK hynix), 김재호 교수(성균관대학교)

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| 초청발표<br>TB4-B-1<br>15:55-16:25 | Dry Etching 장비의 발전 맥락과 차세대 Etching 기술 개발<br>Jong Chul Park<br>Semiconductor R&D Center, Samsung Electronics Co., Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                   |
| TB4-B-2<br>16:25-16:40         | Low Temperature Etch of Silicon Oxide Using Ar/CF <sub>4</sub> /H <sub>2</sub> O Plasma<br>Hakseung Lee <sup>1,2</sup> , Haegeon Jung <sup>1,2</sup> , Kangwoo Lee <sup>3</sup> , Daeun Hong <sup>3</sup> , Minsung Jeon <sup>4</sup> , and Heeyeop Chae <sup>3,4</sup><br><sup>1</sup> Department of Semiconductor Display Engineering, Sungkyunkwan University, <sup>2</sup> Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd., <sup>3</sup> School of Chemical Engineering, Sungkyunkwan University, <sup>4</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University |
| TB4-B-3<br>16:40-16:55         | Optimized hBN Spacer Thickness in Plasmonic WSe <sub>2</sub> /AuNPs Photodetectors: An Experimental and Computational Study<br>이수빈, 김지현<br>서울대학교 화학생명공학부                                                                                                                                                                                                                                                                                                                                                                                                                                                                |
| TB4-B-4<br>16:55-17:10         | Investigation of Area-Selective Ru Deposition via Substrate-dependent ALD-Etch Supercycles<br>Youngseo Na <sup>1</sup> , Hyunjin Lim <sup>2</sup> , Seungchae Lee <sup>2</sup> , Yehbeen Im <sup>2</sup> , Donguk Kim <sup>1</sup> , Kangbaek Seo <sup>1</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University                                                                                                                                                          |
| TB4-B-5<br>17:10-17:25         | C=C 결합이 포함된 C <sub>3</sub> HF <sub>5</sub> 와 C <sub>3</sub> F <sub>6</sub> 플라즈마의 SiO <sub>2</sub> 식각<br>조인경 <sup>1,2</sup> , 김창구 <sup>1,2</sup><br><sup>1</sup> Department of Chemical Engineering, Ajou University, <sup>2</sup> Department of Energy Systems Research, Ajou University                                                                                                                                                                                                                                                                                                                                |
| TB4-B-6<br>17:25-17:40         | Influence of Oxygen and HBr on the Etching Characteristics of Molybdenum Thin Films in Cl <sub>2</sub> /O <sub>2</sub> /HBr/Ar Gas Mixture<br>Hong Ju Yang <sup>1,2</sup> , Jae Min Jung <sup>1,2</sup> , Ho Jin Jung <sup>1,2</sup> , In-Hwan Baek <sup>1,2</sup> , and Chee Won Chung <sup>1,2</sup><br><sup>1</sup> Department of Chemical Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University                                                                                                                                                                          |

D. Thin Film Process Technology 분과

O59\_[TC4-D] Thin Film Transistors II

좌장: 최창환 교수(한양대학교), 오일권 교수(아주대학교)

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| TC4-D-1<br>15:55-16:10 | <b>Vertically Integrated Stacking InGaZnO Vertical Thin-Film Transistors with Shared Channel for Scalable Monolithic 3D Integration</b><br>Young-Jae Kim <sup>1</sup> , Ji-Won Kang <sup>1</sup> , Chi-Sun Hwang <sup>2</sup> , and Sung-Min Yoon <sup>1</sup><br><sup>1</sup> Kyung Hee University, <sup>2</sup> ETRI                                                                                                                                                                                                            |
| TC4-D-2<br>16:10-16:25 | <b>Gate-Stack Engineering of Vertical-Channel Charge-Trap Memory Transistors with ALD-IGZO Channel for High-Density Nonvolatile Storage</b><br>Yu-jin Jung <sup>1</sup> , Kyung-Min Kim <sup>1</sup> , Chi-Sun Hwang <sup>2</sup> , and Sung-Min Yoon <sup>1</sup><br><sup>1</sup> Kyung Hee University, <sup>2</sup> ETRI                                                                                                                                                                                                        |
| TC4-D-3<br>16:25-16:40 | <b>Material-Driven Formation of Two-Dimensional Electron Gas at In<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub> Interfaces with Atomic Layer Deposition</b><br>Kyunghun Lyu, Jiyoung Park, Jiwon Ahn, and Woongkyu Lee<br>Department of Materials Science and Engineering, Soongsil University                                                                                                                                                                                                                            |
| TC4-D-4<br>16:40-16:55 | <b>Analysis of Hysteresis in MoS<sub>2</sub> Field Effect Transistor via Surface Engineering Using Low-Frequency O<sub>2</sub> Plasma Treatment</b><br>Seung Ri Jeong, Ha Yeon Choi, Joon Soo Byeon, Ju Yong Shin, Jong Mun Park, Shivam Kumar Gautam, and Hi Deok Lee<br>Department of Electronics Engineering, Chungnam National University                                                                                                                                                                                     |
| TC4-D-5<br>16:55-17:10 | <b>Low-Temperature Process Strategies for High-Performance BEOL-Compatible p-Type SnO Thin-Film Transistors</b><br>Jaemin Jeong <sup>1,2</sup> , Jaeyoon Shim <sup>1,2</sup> , Dahui Jeon <sup>1,2</sup> , Sung Kwang Lee <sup>3</sup> , Taek-mo Chung <sup>3</sup> , and In-Hwan Baek <sup>1,2</sup><br><sup>1</sup> Department of Chemical Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University, <sup>3</sup> Division of Advanced Materials, KRICT                                 |
| TC4-D-6<br>17:10-17:25 | <b>Scavenging-Driven Interface Engineering for High-Performance Te-Based p-Type TFTs via ALD Al<sub>2</sub>O<sub>3</sub> Passivation</b><br>Jaeyoon Shim <sup>1,2</sup> , Jaemin Jung <sup>1,2</sup> , Dahui Jeon <sup>1,2</sup> , and In-Hwan Baek <sup>1,2</sup><br><sup>1</sup> Department of Chemical Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University                                                                                                                        |
| TC4-D-7<br>17:25-17:40 | <b>P-Type Tellurium Thin Film Transistor with Sacrificial Atomic Layer Deposition</b><br>Wonho Choi <sup>1,2</sup> , Byongwoo Park <sup>1,2</sup> , Seungjae Yoon <sup>1,2</sup> , Gwangsik Jeon <sup>1,2</sup> , Sangmin Jeon <sup>1,2</sup> , Sungjin Kim <sup>1,2</sup> , Junwoo Park <sup>1,2</sup> , and Cheol Seong Hwang <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University |

K. Memory (Design & Process Technology) 분과

O60\_[TD4-K] Advanced Memory

좌장: 김태현 교수(서울과학기술대학교), 정연주 책임(KIST)

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| 초청발표<br>TD4-K-1<br>15:55-16:25 | <b>RRAM and Flash AND Array Platform for Energy-Efficient Spiking Neural Network Computation</b><br>Sungjun Kim<br>Division of Electronics and Electrical Engineering, Dongguk University                                                                                                                                                                                                                                                                                         |
| TD4-K-2<br>16:25-16:40         | <b>Experimental Demonstration of Configurable Kernel Mapping in Memristor Crossbar for Convolutional Neural Networks</b><br>Sangwook Youn <sup>1,2</sup> , Jinwoo Park <sup>1,2</sup> , and Hyungjin Kim <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University                                                                                               |
| TD4-K-3<br>16:40-16:55         | <b>Advances and Perspectives of Selector-Only Memory (SOM) for Future Memory Applications</b><br>연정호, 반상현, 최혜정, 김명섭, 김수길, 이재연, 차선용<br>SK hynix Inc.                                                                                                                                                                                                                                                                                                                               |
| TD4-K-4<br>16:55-17:10         | <b>Bi-Based Selector Only Memory for High-Density 3D Stacked Memory</b><br>Chang Deok Han, Su Yong Chae, and Seung Hwan Lee<br>Department of Semiconductor Engineering, Kyung Hee University                                                                                                                                                                                                                                                                                      |
| TD4-K-5<br>17:10-17:25         | <b>Identical Pulse Based Compensation Resistors for Linear Potentiation and Depression of Synaptic Device</b><br>Minsu Kang <sup>1</sup> , Sion Kim <sup>1</sup> , Yuna Kim <sup>1</sup> , Eungcheol Kim <sup>2</sup> , Sarah Yoon <sup>2</sup> , Songye Lim <sup>2</sup> , and Daeseok Lee <sup>1</sup><br><sup>1</sup> School of Semiconductor System Engineering, Kwangwoon University, <sup>2</sup> Department of Electronic Materials Engineering, Kwangwoon University      |
| TD4-K-6<br>17:25-17:40         | <b>Electrical Properties Between Chalcogenide Ovonic Threshold Switch and Metal Electrodes</b><br>MiRiNae Lee <sup>1,2</sup> , Junghoon Han <sup>1,3</sup> , ChaHwan Yang <sup>1,2</sup> , Kyunghee Choi <sup>1</sup> , and Sooji Nam, <sup>1,2</sup><br><sup>1</sup> Department of Electric Engineering, ETRI, <sup>2</sup> Semiconductor and Advanced Device Engineering, University of Science and Technology, <sup>3</sup> Department of Micro/Nano Systems, Korea University |

P. Device for Energy (Solar Cell, Power Device, Battery, etc.) 분과

O61\_[TE4-P] 전력반도체 소자

좌장: 홍영준 교수(성균관대학교), 김형탁 교수(홍익대학교)

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| 초청발표<br>TE4-P-1<br>15:55-16:25 | 질화갈륨 전력반도체소자의 다양한 열화현상과 메커니즘<br>김형탁<br>홍익대학교 전자전기공학부                                                                                                                                                                                                                                                                                                                                                                                                                                                        |
| TE4-P-2<br>16:25-16:40         | Monolithic Growth of AlGaAs/Si Tandem Solar Cells with a High Bandgap 1.7 eV n-AlGaAs Buffer on GaP/Si<br>Yeonhwa Kim <sup>1,2</sup> , Tsimafei Laryn <sup>1,3</sup> , In-Hwan Lee <sup>2</sup> , Won Jun Choi <sup>1</sup> , and Daehwan Jung <sup>1,3</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Department of Materials Science and Engineering, Korea University, <sup>3</sup> Division of Nanoscience and Technology, KIST School at University of Science and Technology |
| TE4-P-3<br>16:40-16:55         | 반도체 패키지 방열 품질 관리를 위한 확률론적 열 구조 함수<br>송원빈 <sup>1</sup> , 이규석 <sup>2</sup> , 윤병동 <sup>1,3</sup><br><sup>1</sup> 서울대학교 기계공학과, <sup>2</sup> 한국전자기술연구원 신뢰성연구센터, <sup>3</sup> 원프레딕트                                                                                                                                                                                                                                                                                                                               |
| TE4-P-4<br>16:55-17:10         | Flexible InGaP/GaAs/InGaAs 3J Solar Cell for Unassisted Photocatalysis and Space Applications<br>Sukkyu Hong <sup>1,2</sup> , Seungwan Woo <sup>1</sup> , Hyun-Beom Shin <sup>3</sup> , Ho Kwan Kang <sup>3</sup> , Jeongeun Mo <sup>1</sup> , Sung-Min Lee <sup>2</sup> , and Won Jun Choi <sup>1</sup><br><sup>1</sup> Center for Quantum Technology, KIST, <sup>2</sup> Department of Electrical Engineering, Hanyang University, <sup>3</sup> KANC                                                      |

A. Interconnect & Package 분과

O62\_[TF4-A] Advanced Package III

좌장: 박아영 교수(서울시립대학교), 김명준 교수(성균관대학교)

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| 초청발표<br>TF4-A-1<br>15:55-16:25 | <b>Packaging-Driven Reliability Divergence in Power MOSFETs: Insights from Single-Die and Cascode Stack-Die Devices</b><br>You-Cheol Jang<br>Global R&D Center, HL Mando                                                                                                                                                                                                                                                                                                                                                                                    |
| TF4-A-2<br>16:25-16:40         | <b>Study of Substrate-Dependent Signal Integrity in Chiplet Systems</b><br>Yurim Choi <sup>1</sup> , Yongwoo Lee <sup>1</sup> , Haksoon Jung <sup>2</sup> , and Jimin Kwon <sup>1,2</sup><br><sup>1</sup> Department of Electrical Engineering, UNIST, <sup>2</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST                                                                                                                                                                                                               |
| TF4-A-3<br>16:40-16:55         | <b>3D-Printed 28-GHz Antenna-in-Package Lid Substrate Featuring 50-Ohm Quasi-Coaxial Through-Vias</b><br>Nahyeon Kim <sup>1</sup> , Kyungsun Kim <sup>1</sup> , Haksoon Jung <sup>2</sup> , and Jimin Kwon <sup>1,2</sup><br><sup>1</sup> Graduate school of Semiconductor Materials and Devices Engineering, UNIST, <sup>2</sup> Department of Electrical Engineering, UNIST                                                                                                                                                                               |
| TF4-A-4<br>16:55-17:10         | <b>Heat Transfer Modeling for High-Performance Semiconductor Package Using Finite Element Analysis: Experimental Validation and Deep Learning-Based Approach for Acceleration</b><br>Min-Jun Cheon <sup>1</sup> , Seongjin Kim <sup>2</sup> , Jung-Won Lee <sup>3</sup> , Lewis Kang <sup>3</sup> , Sungmo Kang <sup>4</sup> , Inhak Han <sup>5</sup> , Jae Yong Song <sup>2</sup> , and Hoon-Hwe Cho <sup>1</sup><br><sup>1</sup> Hanbat National University, <sup>2</sup> POSTECH, <sup>3</sup> Nepes, <sup>4</sup> Asicland Co., Ltd., <sup>5</sup> Baum |
| TF4-A-5<br>17:10-17:25         | <b>A Validated Multi-Scale Framework for Predicting the Effective Thermal Conductivity of Cu-BAs Composites for Advanced Packaging Applications</b><br>Hyunwoo Jung <sup>1</sup> , Ki-Han Lee <sup>1</sup> , Sung-Jun Kang <sup>1</sup> , Seolim Yoon <sup>1</sup> , Jongchan Park <sup>1</sup> , Jaehoon Kim <sup>2</sup> , Minjeong Sohn <sup>3</sup> , Tae-Ik Lee <sup>3</sup> , Joon Sang Kang <sup>2</sup> , Myung Jun Kim <sup>1</sup> , and Eun-Ho Lee <sup>1</sup><br><sup>1</sup> Sungkyunkwan University, <sup>2</sup> KAIST, <sup>3</sup> KITECH |
| TF4-A-6<br>17:25-17:40         | <b>Characterization of AlN Powder Thermal Conductivity for Thermal Interface Material</b><br>Jinwook Lee <sup>1,2</sup> , Jaewoo Lee <sup>1,2</sup> , Taeheun Lim <sup>1,2</sup> , Jungyoon Hur <sup>1,2</sup> , Heesoo Lee <sup>1,2</sup> , and Woo Jin Kim <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Pusan National University, <sup>2</sup> Institute of Materials Technology, Pusan National University                                                                                                           |

N. VLSI CAD 분과

O63\_[TG4-N] Machine Learning for Electronic Design Automation

좌장: 현대준 교수(세종대학교), 박희천 교수(UNIST)

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| TG4-N-1<br>15:55-16:10 | <b>Multi-Objective Logic Optimization with Diffusion Model</b><br>Jiwon Kang <sup>1</sup> , Dhoui Lim <sup>2</sup> , and Heechun Park <sup>2</sup><br><sup>1</sup> School of Electronics and Electrical Engineering, Hongik University, <sup>2</sup> Department of Electrical Engineering, UNIST |
| TG4-N-2<br>16:10-16:25 | <b>Enhancing Timing Closure via Spatially Embedded Graph Transformer with Low Power/Area Overhead</b><br>Hyunjung Cho, Joonyoung Seo, and Seokhyeong Kang<br>Department of Electrical Engineering, POSTECH                                                                                       |
| TG4-N-3<br>16:25-16:40 | <b>Timing-Driven Hierarchical Gate Sizing with Reinforcement Learning</b><br>Kijung Kong, Geonhyeong Park, and Heechun Park<br>Department of Electrical Engineering, UNIST                                                                                                                       |
| TG4-N-4<br>16:40-16:55 | <b>Physical-Aware Diffusion Model for Macro Placement</b><br>Jongho Yoon, Yunjun Nam, and Seokhyeong Kang<br>Department of Electrical Engineering, POSTECH                                                                                                                                       |
| TG4-N-5<br>16:55-17:10 | <b>A Heterogeneous Graph and Transformer-Based Approach to Gate Sizing for PPA Improvement</b><br>Mungyu Choi, Jinmo Ahn, and Seokhyeong Kang<br>Department of Electrical Engr., POSTECH                                                                                                         |
| TG4-N-6<br>17:10-17:25 | <b>LLM-Based RTL Generation and PPA Improvement Using Evolutionary Computation</b><br>Hayoung Shin, Kyungjun Min, Kyumin Cho, and Seokhyeong Kang<br>Graduate School of Semiconductor Technology, POSTECH                                                                                        |
| TG4-N-7<br>17:25-17:40 | <b>Post-Route Timing Prediction from Synthesis-Level Netlists Using a Graph Neural Network</b><br>Hyeon Jeong Lee and Suwan Kim<br>Department of Electronic Engineering, Kyung Hee University                                                                                                    |

E. Compound Semiconductors 분과

O64\_[TH4-E] Reliability and Radiation Hardness

좌장: 차호영 교수(홍익대학교), 석오균 교수(부산대학교)

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| 초청발표<br>TH4-E-1<br>15:55-16:25 | <b>Charge Trapping as a Design Opportunity and a Reliability Challenge in GaN HEMTs</b><br>Junseok Heo <sup>1,2</sup><br><sup>1</sup> Department of Intelligence Semiconductor Engineering, Ajou University, <sup>2</sup> Department of Electrical and Computer Engineering, Ajou University                                                                                                                                                                                                                                                                                                            |
| TH4-E-2<br>16:25-16:40         | <b>E-mode GaN 트랜지스터에서 게이트 전압에 의한 문턱전압 양의 변화의 게이트 누설 전류 영향 분석</b><br>채명수, 김형탁<br>홍익대학교 전자전기공학부                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                           |
| TH4-E-3<br>16:40-16:55         | <b>Radiation Tolerance Improvement in GaN-Based HEMTs Using Extremely Thin h-BN Passivation Layer and Air Spacer</b><br>Sung-Jae Chang <sup>1</sup> , Seokho Moon <sup>2</sup> , Junhyung Jeong <sup>1</sup> , Hyun-Wook Jung <sup>1</sup> , Ho-Kyun Ahn <sup>1</sup> , Dong-Min Kang <sup>1</sup> , Jong Kyu Kim <sup>2</sup> , Jong-Won Lim <sup>1</sup> , and Dong-Seok Kim <sup>3</sup><br><sup>1</sup> Photonic/Wireless Convergence Research Department, ETRI, <sup>2</sup> Department of Materials Science and Engineering, POSTECH, <sup>3</sup> Korea Multi-purpose Accelerator Complex, KAERI |
| TH4-E-4<br>16:55-17:10         | <b>High-Temperature and Radiation Effects on Al-Rich AlGaIn Channel HEMTs with Various Gate Metals</b><br>Mingoo Jo <sup>1,2</sup> , Joocheol Jeong <sup>1,2</sup> , Shyam Mohan <sup>1,2</sup> , Jaejin Heo <sup>1,2</sup> , Hyogeun Cho <sup>1,2</sup> , Minyeong Kim <sup>1,2</sup> , Dongseok Kim <sup>3</sup> , and Okhyun Nam <sup>1,2</sup><br><sup>1</sup> Convergence Center for Advanced Nano Semiconductor, Tech University of Korea, <sup>2</sup> Department of Semiconductor Engineering, Tech University of Korea, <sup>3</sup> Korea Multi-purpose Accelerator Complex, KAERI            |
| TH4-E-5<br>17:10-17:25         | <b>Electrical Characteristics of H-Diamond FETs with Al/Al<sub>2</sub>O<sub>3</sub>/Al Gate under Proton Irradiation</b><br>Hyunsu Ma <sup>1</sup> , Taemyung Kyak <sup>1</sup> , Yoonseok Nam <sup>1</sup> , Geunho Yoo <sup>1</sup> , Dongseok Kim <sup>2</sup> , Seong-woo Kim <sup>3</sup> , and Okhyun Nam <sup>1</sup><br><sup>1</sup> Convergence Center for Advanced Nano Semiconductor, Department of Nano-Semiconductor Engineering, Tech University of Korea, <sup>2</sup> KAERI, <sup>3</sup> Obray Co., Ltd.                                                                               |
| TH4-E-6<br>17:25-17:40         | <b>Effect of Gamma(<math>\gamma</math>)-Ray Radiation on Tin Oxide Field-Effect Transistors</b><br>Seonchang Kim <sup>1</sup> , Huiseung Kim <sup>2</sup> , Jeongtae Kim <sup>1</sup> , Roy Byung Kyu Chung <sup>2</sup> , and Dong-Seok Kim <sup>1</sup><br><sup>1</sup> Korea Multi-purpose Accelerator Complex, KAERI, <sup>2</sup> Department of Electronic Science and Engineering, Kyungpook National University                                                                                                                                                                                  |

Q. Metrology, Inspection, Analysis, and Yield Enhancement 분과

O65\_[TI4-Q] Metrology, Inspection, Analysis, and Yield Enhancement II

좌장: 김경태 책임연구원(나노종합기술원), 박인용 박사(한국표준과학연구원)

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| 초청발표<br>TI4-Q-1<br>15:55-16:25 | Next-Generation Digital 3D X-ray CT Metrology for Advanced Semiconductor Structures<br>Jehwang Ryu<br>CAT Beam Tech Co., Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| 초청발표<br>TI4-Q-2<br>16:25-16:55 | HBM Stacking Process 발전과 Stacking Misalignment Metrology<br>Hyunjin Chang<br>AUROS Technology Inc.                                                                                                                                                                                                                                                                                                                                                                                                                                                                        |
| TI4-Q-3<br>16:55-17:10         | OCD Spectrum-Based Anomaly Index for Process Evaluation of High-Aspect-Ratio Structures in V-NAND Devices<br>Hoyeon Kim <sup>1</sup> , Sohee Han <sup>1</sup> , Seong Yun <sup>1</sup> , Eonho Park <sup>1</sup> , JunWoong Hur <sup>1</sup> , Eunseo Choi <sup>2</sup> , Heejin Ahn <sup>2</sup> , Jaewon Lee <sup>1</sup> , Taeyong Jo <sup>1</sup> , and Myungjun Lee <sup>1</sup><br><sup>1</sup> Advanced Process Development Team, Samsung Electronics Co., Ltd., <sup>2</sup> School of Electrical Engineering, KAIST                                              |
| TI4-Q-4<br>17:10-17:25         | A Compact Actinic EUV Exposure Platform for Quantitative Photoresist Evaluation Using Femtosecond HHG EUV Source<br>Hyuk Jin Kim <sup>1</sup> , Geonhwa Kim <sup>1</sup> , Namhyeon Kim <sup>1</sup> , Boknam Chae <sup>1</sup> , Yejin Ku <sup>3</sup> , Gayoung Kim <sup>3</sup> , JinKyun Lee <sup>3</sup> , Jiho Kim <sup>1</sup> , and Sangsul Lee <sup>1,2</sup><br><sup>1</sup> Pohang Accelerator Laboratory, POSTECH, <sup>2</sup> Department of Semiconductor Engineering, POSTECH, <sup>3</sup> Department of Polymer Science and Engineering, Inha University |
| TI4-Q-5<br>17:25-17:40         | Flare-Integrated Evaluation Methodology for High-NA EUV Pellicle with Precise Transmission-Reflection Measurements<br>Geonhwa Kim <sup>1</sup> , Jiho Kim <sup>1</sup> , Namhyeon Kim <sup>1</sup> , Hyuk Jin Kim <sup>1</sup> , Byeong-Gyu Park <sup>1</sup> , Jeong Kyu Kim <sup>1</sup> , and Sangsul Lee <sup>1,2</sup><br><sup>1</sup> Pohang Accelerator Laboratory, POSTECH, <sup>2</sup> Department of Semiconductor Engineering, POSTECH                                                                                                                         |

H. Display and Imaging Technologies 분과

O66\_[TJ4-H] Thin Film Transistors for Displays II

좌장: 정예환 교수(한양대학교), 노정균 교수(부산대학교)

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| 초청발표<br>TJ4-H-1<br>15:55-16:25 | Submicron Channel Length Oxide Semiconductor Thin-Film Transistors with Top-Gate and Self-Aligned Process Architecture and Their Monolithic Integration on Si CMOS Wafer<br>Sung Haeng Cho, Chihun Sung, and Jeho Na<br>Flexible Electronics Research Section, ETRI                                                                                                         |
| TJ4-H-2<br>16:25-16:40         | Extremely Flexible MOSFETs with Micrometer-Scale Radius of Curvature in Flexible Display Backplanes<br>Chang Hyeon Park and Yei Hwan Jung<br>Department of Artificial Intelligence Semiconductor Engineering, Hanyang University                                                                                                                                            |
| TJ4-H-3<br>16:40-16:55         | Swing-Tunable Thin-Film Transistors for Improved Low-Gray-Scale OLED Operation<br>Jae Won Na<br>ETRI                                                                                                                                                                                                                                                                        |
| TJ4-H-4<br>16:55-17:10         | Engineering SiNx Gate Insulators via Precursor Ligand Chemistry for High-Performance IGZO TFTs<br>YuJin Yang <sup>1</sup> , Sang-Hyun Kim <sup>2</sup> , and Jin-Seong Park <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Department of Display Science and Engineering, Hanyang University                      |
| TJ4-H-5<br>17:10-17:25         | A Novel AMOLED Display Pixel Circuit for Reducing Leakage Current Induced by Kickback Voltage<br>Dae Cheol Ha <sup>1</sup> , Kook Chul Moon <sup>2</sup> , and Yong-Sang Kim <sup>1,2</sup><br><sup>1</sup> Department of Display Convergence Engineering, Sungkyunkwan University, <sup>2</sup> Department of Electrical and Computer Engineering, Sungkyunkwan University |

D. Thin Film Process Technology 분과

O67\_[FA1-D] Advanced Thin Films and Growth Processes

좌장: 한정환 교수(서울과학기술대학교), 엄태용 교수(세종대학교)

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| FA1-D-1<br>09:00-09:15 | <b>Atomic Layer Annealing of High-Quality Wide-Bandgap BeO for Advanced 3D IC Applications</b><br>Byung Jun Yu <sup>1,2</sup> , Jong Hyun Bae <sup>1,2</sup> , Dohwan Jung <sup>1</sup> , Haekyun Bong <sup>1,2</sup> , Jongha Lim <sup>1,2</sup> , Siwon Lee <sup>1,2</sup> , and Jungwoo Oh <sup>1,2</sup><br><sup>1</sup> School of Integrated Technology, Yonsei University, <sup>2</sup> BK21 Graduate Program in Intelligent Semiconductor Technology, Yonsei University                                                                                                                                                                                                                                                                                                                                                                                                                         |
| FA1-D-2<br>09:15-09:30 | <b>증착 방법에 따른 Poly-Si의 결정립 구조 및 전기적 특성 연구</b><br>김성준 <sup>1,4</sup> , 박준형 <sup>2,4</sup> , 정화윤 <sup>2,4</sup> , 변병훈 <sup>2,4</sup> , 박인성 <sup>3</sup> , 이태호 <sup>4</sup> , 신왕철 <sup>4</sup> , 박영욱 <sup>4</sup> , 안진호 <sup>1,2,4</sup><br><sup>1</sup> 한양대학교 나노반도체공학과, <sup>2</sup> 한양대학교 신소재공학과, <sup>3</sup> 한양대학교 나노과학기술연구소, <sup>4</sup> 극한스케일·극한물성-이종 집적 한계극복 반도체 기술 연구센터                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                           |
| FA1-D-3<br>09:30-09:45 | <b>PECVD SiCO Thin Films Deposition: Compositional Control Using Hollow Cathode Plasma</b><br>Jun Seok Moon <sup>1</sup> , So Yeong Park <sup>2</sup> , Sang Hyun Lee <sup>2</sup> , Dong Kyun Lee <sup>2</sup> , and Tae Joo Park <sup>1</sup><br><sup>1</sup> Department of Materials Science & Chemical Engineering, Hanyang University, <sup>2</sup> SK hynix Inc.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| FA1-D-4<br>09:45-10:00 | <b>Epitaxial Growth of Single-Phase NiCo Thin Films for Resistivity Size Effect Suppression in Advanced Interconnects</b><br>Ju Young Sung <sup>1,2</sup> , Chae Hyun Lee <sup>1,2</sup> , Ye Bin Lim <sup>1,2</sup> , In Su Oh <sup>1,2</sup> , Sang Hyeok Lee <sup>1,2</sup> , Min Seo Kim <sup>1,2</sup> , Yun Won Song <sup>1,2</sup> , and Sang Woon Lee <sup>1,2</sup><br><sup>1</sup> Department of Energy Systems Research, Ajou University, <sup>2</sup> Department of Physics, Ajou University                                                                                                                                                                                                                                                                                                                                                                                               |
| FA1-D-5<br>10:00-10:15 | <b>Epitaxial Growth and Reduced Resistivity Size Effect of Single-Phase Body-Centered Cubic Co-Mo Alloy Thin Films</b><br>Ye Bin Lim <sup>1,2</sup> , Ju Young Sung <sup>1,2</sup> , Chae Hyun Lee <sup>1,2</sup> , In Su Oh <sup>1,2</sup> , Sang Hyeok Lee <sup>1,2</sup> , and Sang Woon Lee <sup>1,2</sup><br><sup>1</sup> Department of Energy Systems Research, Ajou University, <sup>2</sup> Department of Physics, Ajou University                                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| FA1-D-6<br>10:15-10:30 | <b>Carrier Concentration Control and Thermoelectric Enhancement of n-Type Bi<sub>2</sub>Te<sub>3</sub>-Based Materials via Atomic-Layer-Deposited In<sub>2</sub>O<sub>3</sub> Interfacial Layers</b><br>Gwang Min Park <sup>1,2</sup> , Ji Ho Jeon <sup>3</sup> , Jaebaek Ju <sup>1,4</sup> , Jin-Sang Kim <sup>1</sup> , Seung-Hyub Baek <sup>1,5</sup> , Jeong Hwan Han <sup>3</sup> , and Seong Keun Kim <sup>1,2</sup><br><sup>1</sup> Electronic and Hybrid Materials Research Center, KIST, <sup>2</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University, <sup>3</sup> Department of Materials Science and Engineering, Seoul National University of Science & Technology, <sup>4</sup> Department of Materials Science and Engineering, Korea University, <sup>5</sup> Division of Nanoscience and Technology, KIST School, University of Science and Technology |
| FA1-D-7<br>10:30-10:45 | <b>Compositional Engineering of Oxygen Contents in TiO<sub>2-x</sub> to Enhance Temperature Sensitivity for High-Temperature Microbolometer Applications</b><br>Jeongeun Mo <sup>1,2</sup> , Dongrye Choi <sup>1</sup> , Daesan Han <sup>1,2</sup> , Jeong Min Baik <sup>2</sup> , Donghee Park <sup>1</sup> , and Won Jun Choi <sup>1</sup><br><sup>1</sup> KIST, <sup>2</sup> Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                |

B. Patterning (Lithography & Etch Technology) 분과

O68\_[FB1-B] Wet & Dry Etch Processes

좌장: 이원준 교수(세종대학교), 채희엽 교수(성균관대학교)

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| 초청발표<br>FB1-B-1<br>09:00-09:30 | Advances in Atomic Layer Surface Preparation for Next-Generation Memory Nodes<br>Gyu Hyun Kim<br>SK hynix University, SK hynix                                                                                                                                                                                                                                                                                                                                                                                  |
| FB1-B-2<br>09:30-09:45         | 결정 방향성 기반 습식 식각을 통한 다층 WSe <sub>2</sub> 의 전하 수송 이방성 규명<br>김정민, 김지현<br>서울대학교 화학생물공학부                                                                                                                                                                                                                                                                                                                                                                                                                             |
| FB1-B-3<br>09:45-10:00         | Isotropic Atomic Layer Etching of Amorphous and Crystalline Hafnium Oxide Films Using NF <sub>3</sub> Remote Plasma<br>Jehwan Hong <sup>1</sup> , Hye-Lee Kim <sup>1,2</sup> , Byungchul Cho <sup>3</sup> , Changkyu Lee <sup>3</sup> , Juhwan Park <sup>3</sup> , and Won-Jun Lee <sup>1,2</sup><br><sup>1</sup> Department of Nanotechnology and Advanced Materials Engineering, Sejong University, <sup>2</sup> Metal-organic Compounds Materials Research Center, Sejong University, <sup>3</sup> Wonik IPS |
| FB1-B-4<br>10:00-10:15         | Energy-Efficient Plasma-Assisted Atomic Layer Etching of Ruthenium via Gas Activation<br>Jeongmin Oh <sup>1</sup> , Hyung-Gu Kang <sup>2</sup> , Gunsu Yun <sup>2</sup> , and Jihwan An <sup>1</sup><br><sup>1</sup> Graduate School of Semiconductor Technology, POSTECH, <sup>2</sup> Division of Advanced Nuclear Engineering, POSTECH                                                                                                                                                                       |
| FB1-B-5<br>10:15-10:30         | Acetic Acid-Assisted Plasma-Enhanced Atomic Layer Etching for Redeposition-Free Anisotropic Cobalt Profiles<br>Harin Song <sup>1,2</sup> , Daehan Won <sup>1,2</sup> , Dahui Jeon <sup>1,2</sup> , Hongju Yang <sup>1,2</sup> , Chee Won Chung <sup>1,2</sup> , and In-Hwan Baek <sup>1,2</sup><br><sup>1</sup> Department of Chemical Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University                                                                         |

D. Thin Film Process Technology 분과

O69\_[FC1-D] Atomic Layer Deposition I

좌장: 송봉근 교수(홍익대학교), 오일권 교수(아주대학교)

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| FC1-D-1<br>09:00–09:15 | <b>Initial Growth Study of Pt Atomic Layer Deposition for Continuous and Low-Resistivity Ultrathin Films</b><br>Seon Gu Choi, Eun Ji Joo, Jeong Min Han, Jae Hyeon Lee, and Jeong Hwan Han<br>Department of Materials Science and Engineering, Seoul National University of Science & Technology                                                                                                                                                                                                                                                                                                                                                       |
| FC1-D-2<br>09:15–09:30 | <b>Theoretical Analysis of Temperature-Dependent Behavior in Area-Selective Atomic Layer Deposition of Ruthenium Using a Novel Precursor</b><br>Iaan Cho <sup>1,2</sup> , Hideaki Nakatsubo <sup>3,4</sup> , Jeongha Kim <sup>3</sup> , Hyungjun Kim <sup>2</sup> , Soo-Hyun Kim <sup>3</sup> , and Bonggeun Shong <sup>1</sup><br><sup>1</sup> Hongik University, <sup>2</sup> Yonsei University, <sup>3</sup> UNIST, <sup>4</sup> Tanaka Precious Metal Technologies Co., Ltd.                                                                                                                                                                       |
| FC1-D-3<br>09:30–09:45 | <b>Theoretical Insights into Factors Determining Deposition Selectivity During Area-Selective ALD of Ru Using Small-Molecule Inhibitors</b><br>Myeong Kyun Nam <sup>1</sup> , Jiwon Kim <sup>1</sup> , Iaan Cho <sup>1,2</sup> , Young Min Lee <sup>3</sup> , Gi-Young Jo <sup>3</sup> , Jeong Yub Lee <sup>3</sup> , Eun-Hyoung Cho <sup>3</sup> , and Bonggeun Shong <sup>1</sup><br><sup>1</sup> Hongik University, <sup>2</sup> Yonsei University, <sup>3</sup> Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd.                                                                                                            |
| FC1-D-4<br>09:45–10:00 | <b>Metal-on-Metal Area-Selective Atomic Layer Deposition of Ruthenium with Infinite Selectivity for Advanced BEOL Interconnects</b><br>Dahui Jeon <sup>1,2</sup> , Tien Anh Nguyen <sup>3</sup> , Sieun Chae <sup>3</sup> , and In-Hwan Baek <sup>1,2</sup><br><sup>1</sup> Department of Chemical Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University, <sup>3</sup> School of Electrical Engineering and Computer Science, Oregon State University                                                                                                                                                       |
| FC1-D-5<br>10:00–10:15 | <b>Advanced Atomic Layer Deposition: Titanium Nitride Thin Films Growth Using Discrete Feeding Method with Brute Hydrazine</b><br>Jae Woo Jang, Ji Won Han, In Chan Jeong, and Tae Joo Park<br>Department of Materials Science & Chemical Engineering, Hanyang University                                                                                                                                                                                                                                                                                                                                                                              |
| FC1-D-6<br>10:15–10:30 | <b>Alternative Reaction Pathways to Reduce the Resistivity of Low-Temperature Atomic Layer Deposition of TiN Electrode Films</b><br>Kyeong Hyeon Choi <sup>1,2</sup> , Byeong Jun Jeon <sup>1,2</sup> , Se Eun Kim <sup>1,2</sup> , Kyung Jun Lee <sup>1,2</sup> , Tae Hyun Kim <sup>1,2</sup> , Se Eun Park <sup>1,2</sup> , Seung Min Noh <sup>3</sup> , Jae Min Jang <sup>3</sup> , Bong Geun Shong <sup>3</sup> , and Sang Woon Lee <sup>1,2</sup><br><sup>1</sup> Department of Physics, Ajou University, <sup>2</sup> Department of Energy Systems Research, Ajou University, <sup>3</sup> Department of Chemical Engineering, Hongik University |
| FC1-D-7<br>10:30–10:45 | <b>Low-Resistivity Thin Vanadium Nitride (VN) Films Using Plasma-Enhanced Atomic Layer Deposition for Advanced Cu Diffusion Barrier</b><br>Kangbaek Seo <sup>1</sup> , Hyunjin Lim <sup>2</sup> , Seungchae Lee <sup>2</sup> , Youngseo Na <sup>1</sup> , Yehbeen Im <sup>2</sup> , Dounguk Kim <sup>1</sup> , Hyunseok Oh <sup>3</sup> , Donghun Shin <sup>3</sup> , Yongjoo Park <sup>3</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University, <sup>3</sup> SK Trichem Co., Ltd.                     |

K. Memory (Design & Process Technology) 분과

O70\_[FD1-K] Advanced Memory

좌장: 김시준 교수(강원대학교), 김성준 교수(동국대학교)

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| 초청발표<br>FD1-K-1<br>09:00-09:30 | CMOS-compatible Gate Insulator Stack Engineering for Hardware-Based Spiking Neural Networks<br>Min-Kyu Park<br>Department of Semiconductor Engineering, Gachon University                                                                                                                                                                                                      |
| FD1-K-2<br>09:30-09:45         | Threshold Voltage and Saturation Current Programmable Charge-trap Oxide Transistor and Its Utilization for Time-Based Cryptography<br>Huisu Noh and Kyung Min Kim<br>Graduate School of Semiconductor Technology, KAIST                                                                                                                                                        |
| FD1-K-3<br>09:45-10:00         | Enhanced Polarization Switching in InGaAs MFIS Tunnel FET<br>Kyul Ko, Dae-Hwan Ahn, and Jae-Hoon Han<br>KIST                                                                                                                                                                                                                                                                   |
| FD1-K-4<br>10:00-10:15         | Carbon-Doped GST PCRAM: Correlating Chemical Bonding with Thermal Stability and Retention<br>Jisu Park <sup>1</sup> , Seung Min Kang <sup>1</sup> , Woo Seong Son <sup>1</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Engineering, Hanyang University, <sup>2</sup> Division of Materials Science and Engineering, Hanyang University |
| FD1-K-5<br>10:15-10:30         | Sidewall-Structured Memristor for High Density Arrays<br>Sooyeon Narie Kay, Dong Hwi Hwang, and Kyung Min Kim<br>Department of Materials Science and Engineering, KAIST                                                                                                                                                                                                        |

J. Nano-Science & Technology 분과

O71\_[FE1-J] 3D 집적·회로 기술 및 나노소자

좌장: 조경준 선임(KIST), 최상현 교수(DGIST)

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| 초청발표<br>FE1-J-1<br>09:00-09:30 | <b>Improving Transistor Performance through New Material Research</b><br>Yongsung Kim, Kyung-Eun Byun, Minsu Seol, Eun-Kyu Lee, Changhyun Kim, Min Seok Yoo, Junyoung Kwon, Huije Ryu, Sang Won Kim, and Luhing Hu<br>Device Research Center, Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                             |
| 초청발표<br>FE1-J-2<br>09:30-10:00 | <b>Radiation-Hardened Electronics based on Low-Dimensional Materials</b><br>Yeonhoo Kim<br>KRISS                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                  |
| FE1-J-3<br>10:00-10:15         | <b>Modular Approach for Monolithic 3D Integration of CFETs through Inter-module Vias</b><br>Hyokwang Park <sup>1,2</sup> , Won Jong Yoo <sup>1,2</sup> , and Boseok Kang <sup>1,2,3,4</sup><br><sup>1</sup> SKKU Advanced Institute of Nano Technology, Sungkyunkwan University, <sup>2</sup> Department of Nano Science and Technology, Sungkyunkwan University, <sup>3</sup> Department of Nano Engineering, Sungkyunkwan University, <sup>4</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University                                                                                                                                                                                                                                                                                                 |
| FE1-J-4<br>10:15-10:30         | <b>CMOS-Integrable Ambipolar Tellurene Nanofilm-Based Negative Differential Transconductance Transistor for Multi-Valued Logic Computing</b><br>Jihoon Huh <sup>1,2</sup> , Bolim You <sup>1,2</sup> , Yuna Kim <sup>1</sup> , Mino Yang <sup>3</sup> , Unjeong Kim <sup>4</sup> , Min-Kyu Joo <sup>5,6</sup> , Myung Gwan Hahm <sup>1,7</sup> , and Moonsang Lee <sup>1,2</sup><br><sup>1</sup> Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University, <sup>3</sup> KBSI, <sup>4</sup> Department of Physics, Dongguk University, <sup>5</sup> Department of Applied Physics, Sookmyung Women's University, <sup>6</sup> Institute of Advanced Materials and Systems, Sookmyung Women's University, <sup>7</sup> Institute for Bio-Medical and Translational Health Care, Inha University Hospital |
| FE1-J-5<br>10:30-10:45         | <b>EMI Shielding Through Engineering 2D Materials Based Nanomatrix</b><br>Jong Sung Kim <sup>1,2</sup> , Eunjung Lee <sup>1,3</sup> , and Kyungjune Cho <sup>2</sup><br><sup>1</sup> Convergence Research Center for Solutions to Electromagnetic Interference in Future-mobility, KIST, <sup>2</sup> Department of Materials Science and Engineering, Korea University, <sup>3</sup> Department of Chemical and Biological Engineering, Korea University                                                                                                                                                                                                                                                                                                                                                                         |

K. Memory (Design & Process Technology) 분과

O72\_[FF1-K] Advanced Memory

좌장: 권민우 교수(서울과학기술대학교), 권동석 교수(GIST)

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| FF1-K-1<br>09:00–09:15 | <b>Low-Frequency Noise Characteristics of Hafnia Ferroelectric FETs with Ultra-Thin Interface Layer</b><br>Youngchan Cho <sup>1</sup> , Changhyeon Han <sup>2</sup> , Daewoong Kwon <sup>2</sup> , and Wonjun Shin <sup>1</sup><br><sup>1</sup> Department of Semiconductor Convergence Engineering, Sungkyunkwan University, <sup>2</sup> Department of Electrical Engineering, Hanyang University |
| FF1-K-2<br>09:15–09:30 | <b>A Tripartite Synapse-Inspired Ferroelectric-Gated Phototransistors for In-Sensor Image Processing</b><br>Yubin Lee <sup>1</sup> , Dong Hyun Seo <sup>1</sup> , June Seo Lee <sup>2</sup> , Jae Min Jeon <sup>2</sup> , and Young Min Song <sup>1</sup><br><sup>1</sup> School of Electrical Engineering, KAIST, <sup>2</sup> School of Electrical Engineering and Computer Science, GIST         |
| FF1-K-3<br>09:30–09:45 | <b>Variation Tolerant Probabilistic Computing Using a Probabilistic Von Neumann (p-VN) Extraction Algorithm</b><br>Seoeun Jang and Kyung Min Kim<br>KAIST                                                                                                                                                                                                                                           |
| FF1-K-4<br>09:45–10:00 | <b>Reconfigurable Mott Oscillators for Hardware Security and Computing</b><br>Daehee Kim <sup>1</sup> , Gwangmin Kim <sup>2</sup> , and Kyung Min Kim <sup>1</sup><br><sup>1</sup> Department of Materials Science and Engineering, KAIST, <sup>2</sup> Peter-Grünberg-Institut 7 (PGI-7), Forschungszentrum Jülich GmbH                                                                            |
| FF1-K-5<br>10:00–10:15 | <b>Hardware Security Enhancement via Self-Differential Pair PUF in 3D-Stacked Memristor Crossbar Array</b><br>Jinwoo Park and Hyungjin Kim<br>Division of Materials Science and Engineering, Hanyang University                                                                                                                                                                                     |
| FF1-K-6<br>10:15–10:30 | <b>Variation Tolerant Co-Design of Selector-Memory Pairs for Cross-Point Array</b><br>Moon Gyu Choi, Su Yong Chae, and Seung Hwan Lee<br>Department of Semiconductor Engineering, Kyung Hee University                                                                                                                                                                                              |
| FF1-K-7<br>10:30–10:45 | <b>Physical Unclonable Function based on Wordline-Controlled String Current Variation in 3D NAND Flash for Enhanced Reliability</b><br>Dayeon Yu <sup>1,2</sup> , Hwiho Hwang <sup>1,2</sup> , and Hyungjin Kim <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University          |

A. Interconnect & Package 분과

O73\_[FG1-A] Advanced Package IV

좌장: 남태욱 교수(세종대학교), 김명준 교수(성균관대학교)

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| 초청발표<br>FG1-A-1<br>09:00-09:30 | DIC 측정 기반 패키지 인터커넥트 열기계 변형 거동 규명<br>이태익<br>한국생산기술연구원 첨단반도체패키징집적센터                                                                                                                                                                                                                                                                      |
| FG1-A-2<br>09:30-09:45         | Effect of Substrate Thickness and Material Properties on Package Warpage Reduction<br>Jong Won Lee <sup>1,2</sup> , Jae Bum Choi <sup>1,2</sup> , and Jae Woo LEE <sup>2</sup><br><sup>1</sup> Package Development, SK hynix, <sup>2</sup> Department of Electronics and Information Engineering, Korea University                     |
| FG1-A-3<br>09:45-10:00         | Projection Moiré 기술을 활용한 Advanced PKG Warpage 평가<br>정두진, 김제민, 이규석<br>한국전자기술연구원 신뢰성연구센터                                                                                                                                                                                                                                                 |
| FG1-A-4<br>10:00-10:15         | Development of Next-generation Spiral Scan Based High-throughput Inline SAT Machine for Future HBM Core Inspection Technology<br>Han Nu Ri Park, Young Hoon Lee, Gwangmin Yoon, Jongwook Kwon, and Kyungmin Lee<br>SK hynix Co., Ltd.                                                                                                  |
| FG1-A-5<br>10:15-10:30         | Probabilistic Fracture of Glass Interposer for TGV Semiconductor Applications<br>박민혁 <sup>1</sup> , 김해탄 <sup>1</sup> , 박수현 <sup>1</sup> , 김동오 <sup>1</sup> , 박창규 <sup>1</sup> , 좌성훈 <sup>1</sup> , 오정원 <sup>2</sup> , 신현록 <sup>2</sup> , 박지웅 <sup>2</sup> , 변재원 <sup>1</sup><br><sup>1</sup> 서울과학기술대학교 신소재공학과, <sup>2</sup> (주)제이더블유엠티 |
| FG1-A-6<br>10:30-10:45         | Vacancy Assisted Metal-Oxide Redox Bonding for Low Temperature Integration<br>이지윤, 성동윤, 최서연, 홍슬기<br>서울과학기술대학교 지능형반도체공학과                                                                                                                                                                                                                |

G. Device & Process Modeling, Simulation and Reliability 분과

O74\_[FH1-G] Device & Process Modeling, Simulation and Reliability VI

좌장: 장지원 교수(연세대학교), 최성진 교수(국민대학교)

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| <div>FH1-G-1</div> <div>09:00-09:15</div> | <div>Analysis of Retention Characteristics Considering Floating Body Effects in Double-Gate, Gate-All-Around and Channel-All-Around MOSFETs Used as Cell Transistors for 3-Dimensional DRAM</div> <div>Ga-Min Gwon and Ji-Woon Yang</div> <div>Department of Electronics and Information Engineering, Korea University</div>                                                                                                                      |
| <div>FH1-G-2</div> <div>09:15-09:30</div> | <div>Asymmetry-Based Identification of Grain-Boundary Position and Its Impact on Device Variability in 3-D NAND Flash Memory</div> <div>Daehan Won<sup>1</sup>, Donghyun Go<sup>2</sup>, Donghwi Kim<sup>2</sup>, Seungjae Kim<sup>1</sup>, Hyunjun Kim<sup>1</sup>, and Jeong-Soo Lee<sup>1,2</sup></div> <div><sup>1</sup>Graduate School of Semiconductor Technology, POSTECH, <sup>2</sup>Department of Electrical Engineering, POSTECH</div> |
| <div>FH1-G-3</div> <div>09:30-09:45</div> | <div>Short-Channel Effects Model of Double-Gate MOSFET with a-IGZO Channel for Cell Array Transistor in 3-Dimensional DRAM</div> <div>Tae-Hyun Park and Ji-Woon Yang</div> <div>Department of Electronics and Information Engineering, Korea University</div>                                                                                                                                                                                     |
| <div>FH1-G-4</div> <div>09:45-10:00</div> | <div>An Approach for BSIM-CMG Parameter Extraction Using a Quasi-1D Model</div> <div>Kwang-Woon Lee and Sung-Min Hong</div> <div>Department of Electrical Engineering and Computer Science, GIST</div>                                                                                                                                                                                                                                            |
| <div>FH1-G-5</div> <div>10:00-10:15</div> | <div>Investigation of a Methodology for Adjusting the Ron of ESD Devices through Experiments</div> <div>Jihoon Lee and Youngchul Kim</div> <div>Technology Development Department, DB HiTek</div>                                                                                                                                                                                                                                                 |
| <div>FH1-G-6</div> <div>10:15-10:30</div> | <div>Top-gate Self-aligned IGZO TFT의 축방향 수소 확산 매커니즘 규명 및 제어를 통한 수소 열처리 내성 향상</div> <div>김희태<sup>1</sup>, 이호석<sup>1</sup>, 김희수<sup>1</sup>, 조성행<sup>2</sup>, 조병진<sup>1</sup></div> <div><sup>1</sup>한국과학기술원 전기 및 전자공학부, <sup>2</sup>한국전자통신연구원 플렉시블 전자소자연구실</div>                                                                                                                                                                                   |
| <div>FH1-G-7</div> <div>10:30-10:45</div> | <div>Mechanism Analysis of High-Voltage ESD BJT Protection Circuit with High Current Characteristic</div> <div>Bo-Bae Song and Young-chul Kim</div> <div>ESD/TCAD Team, DB HiTek</div>                                                                                                                                                                                                                                                            |

Q. Metrology, Inspection, Analysis, and Yield Enhancement 분과

O75\_[F11-Q] Metrology, Inspection, Analysis, and Yield Enhancement III

좌장: 손영훈 마스터(삼성전자), 제갈원 박사(한국표준과학연구원)

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| 초청발표<br>F11-Q-1<br>09:00-09:30 | <b>A Study on Prediction of Electrical Characteristics Using In-Line Measurement Values in GAA FET</b><br>Hyung Keun Yoo, Kyunghoon Lee, Inhee Jung, Yeonjeong Kim, Mingyu Kim, Mira Park, Younghoon Sohn, and Yongdeok Jeong<br>Metrology & Inspection Technology Team, Common Technology Center, Samsung Electronics Co., Ltd.                                                                         |
| 초청발표<br>F11-Q-2<br>09:30-10:00 | <b>Patent Big Data Analytics of Gas and Chemical Systems for Semiconductor Infrastructure: Implications for Metrology and Process Control</b><br>Jongmin Lee<br>Global Manufacturing & Infra Technology, Samsung Electronics Co., Ltd.                                                                                                                                                                   |
| F11-Q-3<br>10:00-10:15         | <b>Improvement of CD-SEM Image Quality with High Depth of Focus (DOF) Beam</b><br>Ra Seong Ki <sup>1</sup> , Jong Hoi Cho <sup>1</sup> , Kyung Su Byun <sup>1</sup> , Jin Hee Han <sup>1</sup> , Jun Ho Lee <sup>1</sup> , Su Jin Lim <sup>2</sup> , Woo Sung Jung <sup>2</sup> , and Eun Hyuk Choi <sup>1</sup><br><sup>1</sup> SK hynix Inc., <sup>2</sup> PDC Business Group, Applied Materials, Inc. |
| F11-Q-4<br>10:15-10:30         | <b>HBM Hybrid Bonding향 CMP 공정 품질 모니터링 고속화 기술 연구 (High Speed CMP Process Quality Monitoring Technology for HBM Hybrid Bonding Process)</b><br>박품성, 조한샘, 조선기, 변정훈, 김종관<br>SK hynix Inc. ADV PKG MI개발                                                                                                                                                                                                       |
| F11-Q-5<br>10:30-10:45         | <b>Anomaly Monitoring Framework Using AI-Based Chart Image Classifier and Initial Analysis Assistant</b><br>Bumsuk Chung, Jinsik Kim, Haeyong Joung, Sungjoon Hong, Yunhee Kim, Hyunjin Wang, Hyunsoo Kim, Taehwa Oh, Inkap Chang, and Chiyong An<br>Memory Quality & Reliability, Memory Business, Samsung Electronics Co., Ltd                                                                         |

I. MEMS & Sensors Systems 분과

O76\_[FJ1-I] MEMS and Sensor System III

좌장: 박윤석 교수(경희대학교), 윤홍준 교수(가천대학교)

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| 초청발표<br>FJ1-I-1<br>09:00-09:30 | <b>Closed-loop Functionalities in Optical Materials and Devices</b><br>Sang Min Won<br>Department of Electrical and Computer Engineering, Sungkyunkwan University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                |
| FJ1-I-2<br>09:30-09:45         | <b>Orientation-Tunable Liquid-Crystalline Organic Semiconductors for Reconfigurable PUF and OFET Applications</b><br>Moon Jong Han<br>Department of Semiconductor Engineering, Gachon University                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| FJ1-I-3<br>09:45-10:00         | <b>Synaptic Nanowire Phototransistor for Biosignal Classification</b><br>Wangmyung Choi <sup>1</sup> , Jin Seok Yoon <sup>2</sup> , Won Woo Lee <sup>3</sup> , Gun Ho Hong <sup>4</sup> , Hyeonjung Kim <sup>4</sup> , Seyong Oh <sup>4</sup> , Young Tea Chun <sup>2</sup> , and Hocheon Yoo <sup>1</sup><br><sup>1</sup> Department of Electronic Engineering, Hanyang University, <sup>2</sup> Division of Electronics and Electrical Information Engineering, Korea Maritime & Ocean University, <sup>3</sup> Department of Artificial Intelligence Semiconductor Engineering, Hanyang University, <sup>4</sup> Division of Electrical Engineering, Hanyang University ERICA |
| FJ1-I-4<br>10:00-10:15         | <b>LSPR-Driven Photodetector Enabled by Ag Mesh-Si Schottky Nanodiodes</b><br>Jongyeol Park <sup>1,2</sup> , Jihoon Huh <sup>1,2</sup> , Yohan Lee <sup>1,2</sup> , Seung Ji Lo <sup>1,2</sup> , Jae Hyun Kim <sup>1,2</sup> , Narea Lee <sup>1,2</sup> , Jaehyeong Park <sup>1</sup> , and Moonsang Lee <sup>1,2</sup><br><sup>1</sup> Department of Materials Science and Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University                                                                                                                                                                                                     |
| FJ1-I-5<br>10:15-10:30         | <b>On-Chip Gas Leak Source Estimation Using Filament Events</b><br>Wooseong Roh <sup>1,2</sup> , Hunhee Shin <sup>1,2</sup> , Jonghyun Ko <sup>1,2</sup> , Jeseung Jeong <sup>1,2</sup> , Jong-Ho Lee <sup>1,2</sup> , and Gyuweon Jung <sup>1,2,3</sup><br><sup>1</sup> Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup> School of Transdisciplinary Innovations, Seoul National University                                                                                                                                                   |
| FJ1-I-6<br>10:30-10:45         | <b>Grain-Boundary-Driven Stochastic Oxide Junction in 2D SnSe Enables Dual Electrical-Optical PUFs</b><br>Jaechan Song <sup>1</sup> , Taehyun Park <sup>2</sup> , Youngmin Han <sup>2</sup> , Junhyung Cho <sup>1</sup> , and Hocheon Yoo <sup>2</sup><br><sup>1</sup> Department of Artificial Intelligence Semiconductor Engineering, Hanyang University, <sup>2</sup> Department of Electronic Engineering, Hanyang University                                                                                                                                                                                                                                                |

D. Thin Film Process Technology 분과

O77\_[FC2-D] Atomic Layer Deposition II

좌장: 한정환 교수(서울과학기술대학교), 유찬영 교수(홍익대학교)

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| FC2-D-1<br>10:55-11:10 | <p>High-Temperature Atomic Layer Deposition of High-Quality SiO<sub>2</sub> Films Using a Novel Silylamine-Type Precursor</p> <p>Okhyeon Kim<sup>1</sup>, Changgyu Kim<sup>1</sup>, Tanzia Chowdhury<sup>1</sup>, Mi-Soo Kim<sup>1</sup>, Taeyoon Kwon<sup>1</sup>, Hye-Lee Kim<sup>1</sup>, Seunggyun Hong<sup>2</sup>, Byung-Kwan Kim<sup>2</sup>, Jin Sik Kim<sup>2</sup>, Wonyong Koh<sup>2</sup>, and Won-Jun Lee<sup>1</sup></p> <p><sup>1</sup>Department of Nano Technology and Advanced Materials Engineering, Sejong University, <sup>2</sup>UP Chemical Co., Ltd.</p> |
| FC2-D-2<br>11:10-11:25 | <p>Oxygen Vacancy Suppression in ALD TiO<sub>2</sub> Thin Films Using a Modified Ti-Precursor</p> <p>Juan Hong, Seokho Cho, Hyeongjun Kim, Taehyun Kim, Soonbin Kwon, and Woongkyu Lee</p> <p>Department of Materials Science and Engineering, Soongsil University</p>                                                                                                                                                                                                                                                                                                           |
| FC2-D-3<br>11:25-11:40 | <p>Temperature-Driven Phase Formation with Novel Cyclopentadienyl-Based Precursors for BEOL-Compatible Hf<sub>1-x</sub>Zr<sub>x</sub>O<sub>2</sub> Ferroelectric Capacitors</p> <p>Hye-Won Cho<sup>1</sup>, Hyo-Bae Kim<sup>1</sup>, Jin Sik Kim<sup>2</sup>, Byung-Kwan Kim<sup>2</sup>, and Ji-Hoon Ahn<sup>1</sup></p> <p><sup>1</sup>Department of Materials Science &amp; Chemical Engineering, Hanyang University, <sup>2</sup>Material Process Development Division, UP Chemical Co., Ltd.</p>                                                                            |
| FC2-D-4<br>11:40-11:55 | <p>A Composition Tuning Strategy via Analysis of Underlayer-Dependent Initial Growth Behavior in IGZO Supercycle ALD</p> <p>Jae-Hak Choung<sup>1</sup>, Ae-Rim Choi<sup>1</sup>, Eun-Hu Hwang<sup>1</sup>, Seung-Wook Ryu<sup>2</sup>, and Il-Kwon Oh<sup>1,3</sup></p> <p><sup>1</sup>Department of Intelligence Semiconductor Engineering, Ajou University, <sup>2</sup>Revolutionary Technology Center, R&amp;D Process, R&amp;D Division, SK hynix Inc., <sup>3</sup>Department of Electrical and Computer Engineering, Ajou University</p>                                  |
| FC2-D-5<br>11:55-12:10 | <p>ALD-Grown Amorphous InGaO<sub>x</sub> Channels for Thermally Stable Thin-Film Transistors</p> <p>Joonyong Kim, Dong Hee Han, Hyun Woo Jeong, Hyeong Seok Choi, Jaejoon Kim, Suyong Lee, and Min Hyuk Park</p> <p>Department of Materials Science and Engineering, Seoul National University</p>                                                                                                                                                                                                                                                                               |
| FC2-D-6<br>12:10-12:25 | <p>Low-Damage IGZO/HfO<sub>2</sub> Charge-Trap Memory Devices Fabricated by a Customized 2600W Remote Plasma ALD Process</p> <p>In Kook Hwang, Ji Won Kim, Byung Wook Kim, Young Woon Jang, Hyeon Wu Nam, Min Kyun Kang, and Chang Bun Yoon</p> <p>Department of Advanced Materials Engineering, Tech University of Korea</p>                                                                                                                                                                                                                                                    |
| FC2-D-7<br>12:25-12:40 | <p>Transparent Resistive Memory Devices Utilizing Ga-Doped ZnO Thin Films Prepared by Atomic Layer Deposition</p> <p>Wonnyeon Kim, Gyeongil Son, Satish B. Jadhav, and Minjae Kim</p> <p>School of Materials Science &amp; Engineering, Yeungnam University</p>                                                                                                                                                                                                                                                                                                                  |

O. System LSI Design 분과

O78\_[FD2-O] R & O 분과 통합 세션 (부제: System LSI Design)

좌장: 유호영 교수(충남대학교), 김재호 교수(경상국립대학교)

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| 초청발표<br>FD2-O-1<br>10:55-11:25 | Device/Circuit Design for Emerging eDRAM Technologies<br>Munhyeon Kim<br>Department of Electrical and Information Engineering, Seoul National University of Science and Technology                                                                                                                                                                                                 |
| FD2-O-2<br>11:25-11:40         | 하드웨어 효율적인 GPS L1C 인터리버 구현<br>송재오, 황용택, 구교덕, 김도훈, 유호영<br>충남대학교 전자공학과                                                                                                                                                                                                                                                                                                                |
| FD2-O-3<br>11:40-11:55         | A 512-Point STFT Hardware Architecture Using Low-Precision Floating-Point for High Accuracy and Area Efficiency<br>Seung Pyo Hong <sup>1</sup> , Hana Kim <sup>2</sup> , and Ji-Hoon Kim <sup>1,2</sup><br><sup>1</sup> Department of Artificial Intelligence Semiconductor Engineering, Hanyang University, <sup>2</sup> Department of Electronic Engineering, Hanyang University |
| FD2-O-4<br>11:55-12:10         | An Efficient Multi-Mode SHA-3 Architecture<br>Jisoo Lee, Sojeong Ok, and Woong Choi<br>School of Electronic Engineering, Sookmyung Women's University                                                                                                                                                                                                                              |
| FD2-O-5<br>12:10-12:25         | FTL 개발자를 위한 Cosmos OpenSSD 시뮬레이터 상 개발환경<br>이제연, 최종무<br>단국대학교                                                                                                                                                                                                                                                                                                                       |
| FD2-O-6<br>12:25-12:40         | Fast and Efficient Transformer-Based Architecture for SSD Failure Prediction in Multi-Horizon Forecasting<br>Jobeda Khanam Ria and Jaeho Kim<br>Department of AI Convergence Engineering, Gyeongsang National University                                                                                                                                                           |

J. Nano-Science & Technology 분과

O79\_[FE2-J] 뉴로모픽·메모리 소재 및 시냅스 소자 기술

좌장: 김연후 책임연구원(한국표준과학연구원), 정용진 교수(국립한국교통대학교)

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| 초청발표<br>FE2-J-1<br>10:55-11:25 | <b>Wafer-scale Passive Crossbar Integration of Metal-oxide Memristors for Computing</b><br>Sanghyeon Choi <sup>1,2</sup><br><sup>1</sup> Department of Electrical Engineering & Computer Science, DGIST, <sup>2</sup> Department of Semiconductor Engineering, DGIST                                                                                                                                                                                                                                                            |
| FE2-J-2<br>11:25-11:40         | <b>나노결정질 MoS<sub>2</sub>/HfO<sub>2</sub> 기반 전하 포획 시냅스 소자의 공정 변수 최적화 및 전기적 특성 분석</b><br>이정빈 <sup>1</sup> , 황윤아 <sup>1</sup> , 명재민 <sup>2,3</sup> , 김태현 <sup>2,3</sup> , 손시훈 <sup>3</sup> , 최현빈 <sup>3</sup> , 김근석 <sup>3</sup> , 김태성 <sup>3</sup> , 문지훈 <sup>2</sup> , 최민섭 <sup>1</sup><br><sup>1</sup> 충남대학교, <sup>2</sup> 한국표준과학연구원, <sup>3</sup> 성균관대학교                                                                                                                                                                       |
| FE2-J-3<br>11:40-11:55         | <b>Reconfigurable Artificial Multipolar Neuronal Device Realized by Nanoporous VO<sub>2</sub> Memristive Array</b><br>Gwanyeong Park <sup>1</sup> , Young Ran Park <sup>1</sup> , Mingyu Kim <sup>1</sup> , Sanghyeon Choi <sup>3</sup> , and Gunuk Wang <sup>1,2</sup><br><sup>1</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University, <sup>2</sup> Department of Integrated Energy Engineering, Korea University, <sup>3</sup> Department of Electrical Engineering & Computer Science, DGIST |
| FE2-J-4<br>11:55-12:10         | <b>Energy-efficient Uncertainty Quantification via Gate-tunable 1A1M Synaptic Device for Bayesian Neural Network</b><br>Hyeon Bin Kim <sup>1</sup> , Yejin Kim <sup>1</sup> , Yeon Seo An <sup>1</sup> , Sanghyeon Choi <sup>3</sup> , and Gunuk Wang <sup>1,2</sup><br><sup>1</sup> KU-KIST Graduate School of Converging Science and Technology, Korea University, <sup>2</sup> Department of Integrative Energy Engineering, Korea University, <sup>3</sup> Department of Electrical Engineering & Computer Science, DGIST   |
| FE2-J-5<br>12:10-12:25         | <b>Improving Synaptic Properties in Ionic Gated Transistors by Controlling Ion Migration Pathways</b><br>Woongki Lee <sup>1</sup> , Youngkyoo Kim <sup>2</sup> , and Kyungjune Cho <sup>1</sup><br><sup>1</sup> Electronic and Hybrid Materials Research Center, KIST, <sup>2</sup> Department of Chemical Engineering, Kyungpook National University                                                                                                                                                                           |
| FE2-J-6<br>12:25-12:40         | <b>A Van der Waals Optoelectronic Synapse with Tunable Positive and Negative Post-Synaptic Current for Highly Accurate Spiking Neural Networks</b><br>Dong-Ho Kang<br>Department of Semiconductor Engineering, GIST                                                                                                                                                                                                                                                                                                             |

K. Memory (Design & Process Technology) 분과

O80\_[FF2-K] Advanced Memory

좌장: 김성준 교수(동국대학교), 권용우 교수(홍익대학교)

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| 초청발표<br>FF2-K-1<br>10:55-11:25 | <b>In-Memory Computing for Solving Combinatorial Optimization Problems</b><br>Dongseok Kwon<br>Department of Semiconductor Engineering, GIST                                                                                                                                                                                                                                                                                                                                                                                                                         |
| FF2-K-2<br>11:25-11:40         | <b>1T-1MFMIS FeFET CiM Cell with Enhanced Memory Window and Long-Term Multi-Bit Retention</b><br>Simin Chen <sup>1,2</sup> , Zewei Wang <sup>1,2</sup> , Gijun Ju <sup>1,2,3</sup> , Jaehoon Han <sup>3</sup> , and Younghyun Kim <sup>1,2</sup><br><sup>1</sup> Department of Photonics and Nanoelectronics, Hanyang University, <sup>2</sup> BK21 FOUR ERICA-ACE Center, Hanyang University, <sup>3</sup> KIST                                                                                                                                                     |
| FF2-K-3<br>11:40-11:55         | <b>Capacitive Time-Domain Ferroelectric Content-Addressable Memory for High-Density and Highly Robust In-Memory Nearest Neighbor Search</b><br>Minjeong Ryu <sup>1,2</sup> , Jae Seung Woo <sup>1,2</sup> , and Woo Young Choi <sup>1,2</sup><br><sup>1</sup> Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup> Inter-university Semiconductor Research Center, Seoul National University                                                                                                                                   |
| FF2-K-4<br>11:55-12:10         | <b>Reliable 28nm eFlash Process for UWB-Based Automotive Applications</b><br>Gyuhak Choi, Hyunik Park, Han-Hyeoung Choi, Junyoung Kim, Taemin Jang, Jeadong Jung, Kyungjun Oh, Sooyeoung Kim, Sumin Choi, Jongyeoun Hong, Juyeong Pyo, Youngcheon Jeong, Changmin Jeon, and OhKyum Kwon<br>Foundry Business, Samsung Electronics Co., Ltd.                                                                                                                                                                                                                           |
| FF2-K-5<br>12:10-12:25         | <b>3D Integrated Neural Networks with Ionic-Switch Neurons for Energy- and Area-Efficient Hardware Implementation</b><br>Yuna Kim <sup>1</sup> , Minsu Kang <sup>1</sup> , Sion Kim <sup>1</sup> , Sarah Yoon <sup>2</sup> , Eungcheol Kim <sup>2</sup> , Songye Lim <sup>2</sup> , and Daeseok Lee <sup>2</sup><br><sup>1</sup> School of Semiconductor Systems Engineering, Kwangwoon University, <sup>2</sup> Department of Electronic Materials Engineering, Kwangwoon University                                                                                |
| FF2-K-6<br>12:25-12:40         | <b>Implementation of a Leaky Integrate-and-Fire Neuron Using Volatile Memristors with Threshold Switching</b><br>Dae Kyu Lee <sup>1,2</sup> , Gichang Noh <sup>1</sup> , Yooyeon Jo <sup>1,3</sup> , Eunpyo Park <sup>1,2</sup> , Min Jee Kim <sup>1</sup> , Heerak Wi <sup>4</sup> , Ria Choi <sup>4</sup> , Hyun Jae Jang <sup>1</sup> , Suyoun Lee <sup>1</sup> , Sangbum Kim <sup>2</sup> , and Joon Young Kwak <sup>4</sup><br><sup>1</sup> KIST, <sup>2</sup> Seoul National University, <sup>3</sup> Sun Moon University, <sup>4</sup> Ewha Womans University |
| FF2-K-7<br>12:40-12:55         | <b>Polymer Insertion Effects on Self-Rectification Behaviors in CuI-RRAMs</b><br>Hyun Kyu Lee <sup>1</sup> , Dhananjay Mishra <sup>1</sup> , Hyeon Bin Jo <sup>1</sup> , Yun Sung Lee <sup>2</sup> , Han Min Kim <sup>2</sup> , and Sung Hun Jin <sup>1</sup><br><sup>1</sup> Department of Information Display, Kyung Hee University, <sup>2</sup> Department of Intelligent Semiconductor Engineering, Incheon National University                                                                                                                                 |

A. Interconnect & Package 분과

O81\_[FG2-A] Emerging Interconnects

좌장: 이소연 교수(인하대학교), 김명준 교수(성균관대학교)

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| 초청발표<br>FG2-A-1<br>10:55-11:25 | <b>Thermal Atomic Layer Etching of Molybdenum for the Next Generation Interconnect</b><br>Taewook Nam <sup>1,2</sup><br><sup>1</sup> Department of Semiconductor Systems Engineering, Sejong University, <sup>2</sup> Department of Artificial Intelligence and Information Technology, Sejong University                                                                                                                                                                                                                                                                                                                                                                                                   |
| FG2-A-2<br>11:25-11:40         | <b>A Distribution-Dependent Grain Size Measurement for the Accurate Property Prediction of Ruthenium Interconnects</b><br>Jun Hyeok Hyun <sup>1,2</sup> , Yoon-Gu Lee <sup>3</sup> , Hongik Kim <sup>3</sup> , Jaehee Sohn <sup>3</sup> , Jae-Min Lim <sup>3</sup> , Da-Young Lee <sup>3</sup> , So-Yeon Lee <sup>1,2</sup> , and Young-Chang Joo <sup>3</sup><br><sup>1</sup> Department of Materials Science and Engineering, Inha University, <sup>2</sup> Program in Semiconductor Convergence, Inha University, <sup>3</sup> Department of Materials Science and Engineering, Seoul National University                                                                                                |
| FG2-A-3<br>11:40-11:55         | <b>Plasma-Enhanced Atomic Layer Deposition of Molybdenum Carbide (MoC<sub>x</sub>) Thin Films Using an Amido-Imido Based Metal-Organic Precursor for Conductive Interconnects</b><br>Hyunjin Lim <sup>1</sup> , Seungchae Lee <sup>1</sup> , Yehbeen Im <sup>2</sup> , Youngseo Na <sup>2</sup> , Donguk Kim <sup>2</sup> , Kangbaek Seo <sup>2</sup> , Kanghyeok Lee <sup>2</sup> , Sangtae Park <sup>1</sup> , Yong Joo Park <sup>3</sup> , Dong Hun Shin <sup>3</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University, <sup>3</sup> SK Trichem Co., Ltd. |
| FG2-A-4<br>11:55-12:10         | <b>Reliability Evaluation of Cobalt Nitride (CoN) Diffusion Barrier for Advanced Cu and Co Interconnects</b><br>Yeh Been Im <sup>1</sup> , Young Seo Na <sup>2</sup> , Hyun Jin Lim <sup>1</sup> , Jeng A Heo <sup>3</sup> , So Yeon Lee <sup>3</sup> , and Changhwan Choi <sup>1,2</sup><br><sup>1</sup> Division of Materials Science and Engineering, Hanyang University, <sup>2</sup> Department of Semiconductor Engineering, Hanyang University, <sup>3</sup> Department of Materials Science and Engineering, Inha University                                                                                                                                                                        |
| FG2-A-5<br>12:10-12:25         | <b>Annealing Effect on the Interfacial and Dielectric Reliability of ALD Ru/ZnO Thin Films for Advanced Interconnects</b><br>Daeyoon Jeong <sup>1</sup> , Suyeon Lee <sup>1</sup> , Yeseul Son <sup>2</sup> , Minwoo Kim <sup>2</sup> , Soo-Hyun Kim <sup>2,3</sup> , and Young-Bae Park <sup>1</sup><br><sup>1</sup> School of Materials Science and Engineering, Gyeongbuk National University, <sup>2</sup> Graduate School of Semiconductor Materials and Devices Engineering, UNIST, <sup>3</sup> Department of Materials Science and Engineering, UNIST                                                                                                                                               |
| FG2-A-6<br>12:25-12:40         | <b>Benchmarking of Ag-Cu Amorphous Alloy for Interconnects Materials</b><br>SeongYun Hong <sup>1</sup> , Subeen Lim <sup>2</sup> , and YeongHun Lee <sup>2</sup><br><sup>1</sup> Department of Intelligent Semiconductor Engineering, Incheon National University, <sup>2</sup> Department of Electronics Engineering, Incheon National University                                                                                                                                                                                                                                                                                                                                                          |

V. Quantum Technology 분과

O82\_[FI2-V] Quantum Technology II

좌장: 문기원 박사(ETRI), 이문주 교수(POSTECH)

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| 초청발표<br>FI2-V-1<br>10:55-11:25 | <b>Squeezed Light Generation Using Optical Parametric Amplifier Module</b><br>Kiwon Moon, Byungkyu Jeong, Tetiana Slusar, Guhwan Kim, Hong-Seok Kim, Heesung Kim, Jaegyu Park, Jin Tae Kim, Min-su Kim, and Jung Jun Ju<br>Quantum Technology Research Division, ETRI                                                                                       |
| 초청발표<br>FI2-V-2<br>11:25-11:55 | <b>The Feasibility of a Silicon Quantum Dot Structure as a Sensing Unit</b><br>Hoon Ryu<br>School of Computer Engineering, Kumoh National Institute of Technology                                                                                                                                                                                           |
| 초청발표<br>FI2-V-3<br>11:55-12:25 | <b>Superconducting Scalable Quantum Computing</b><br>이용호<br>한국표준과학연구원 초전도양자컴퓨팅시스템연구단                                                                                                                                                                                                                                                                        |
| FI2-V-4<br>12:25-12:40         | <b>Realization of an Exceptional Point in a Fabry-Pérot Cavity Using a Birefringent Defect in a Supermirror</b><br>Juman Kim <sup>1,2</sup> , Jisung Seo <sup>1,2</sup> , and Kyungwon An <sup>1,2</sup><br><sup>1</sup> Department of Physics & Astronomy, Seoul National University, <sup>2</sup> Institute of Applied Physics, Seoul National University |

U. Bio-Medical 분과

O83\_[FJ2-U] Sensors and Circuits for Biomedical and Biochemical Applications

좌장: 송민영 교수(DGIST), 이경태 교수(DGIST)

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| <div>초청발표<br/>FJ2-U-1<br/>10:55-11:25</div> | <div>A High-Density, Scalable Capacitive Neural Interface System Using 2-D Code-Division Multiplexing<br/>Woojun Choi<br/>Department of Integrated Display Engineering, Yonsei University</div>                                                                                                                                                                                                                                                                            |
| <div>초청발표<br/>FJ2-U-2<br/>11:25-11:55</div> | <div>Scalable and Reproducible Fabrication of Single-CNT FETs for Single-Molecule Sensing<br/>Yoonhee Lee<br/>Division of Biomedical Technology, DGIST</div>                                                                                                                                                                                                                                                                                                               |
| <div>FJ2-U-3<br/>11:55-12:10</div>          | <div>High-Spatiotemporal-Resolution Thermoelectric Temperature Sensor Array for Photothermal Neuromodulation<br/>Junhee Lee<sup>1</sup>, Dongjo Yoon<sup>2</sup>, Yoonkey Nam<sup>2</sup>, and Hongki Kang<sup>3</sup><br/><sup>1</sup>Department of Electrical Engineering and Computer Science, DGIST, <sup>2</sup>Department of Bio and Brain Engineering, KAIST, <sup>3</sup>Department of Biomedical Engineering, Seoul National University College of Medicine</div> |
| <div>FJ2-U-4<br/>12:10-12:25</div>          | <div>A cDNA-Mediated Regenerable RF Biosensor based on Solution-Processed MoS<sub>2</sub> for Selective ss-cfDNA Detection<br/>Seungchan Lee<sup>1</sup>, Sung Moon Park<sup>2</sup>, Changwoo Pyo<sup>2</sup>, and Myungsoo Kim<sup>1,2</sup><br/><sup>1</sup>Department of Electrical Engineering, UNIST, <sup>2</sup>Graduate School of Semiconductor Materials and Devices Engineering, UNIST</div>                                                                    |